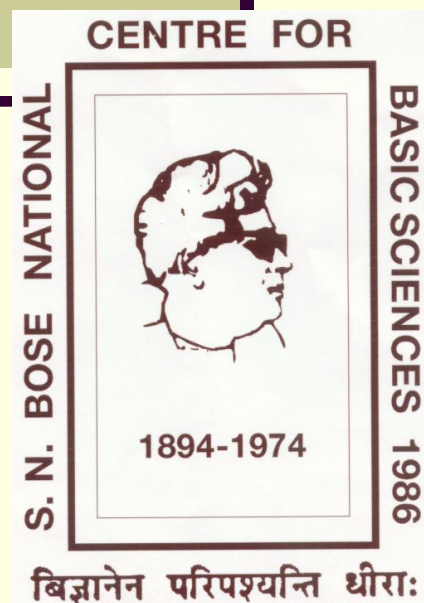


Why do we have unusual behavior in twisted bilayers of transition metal dichalcogenides?

Priya Mahadevan

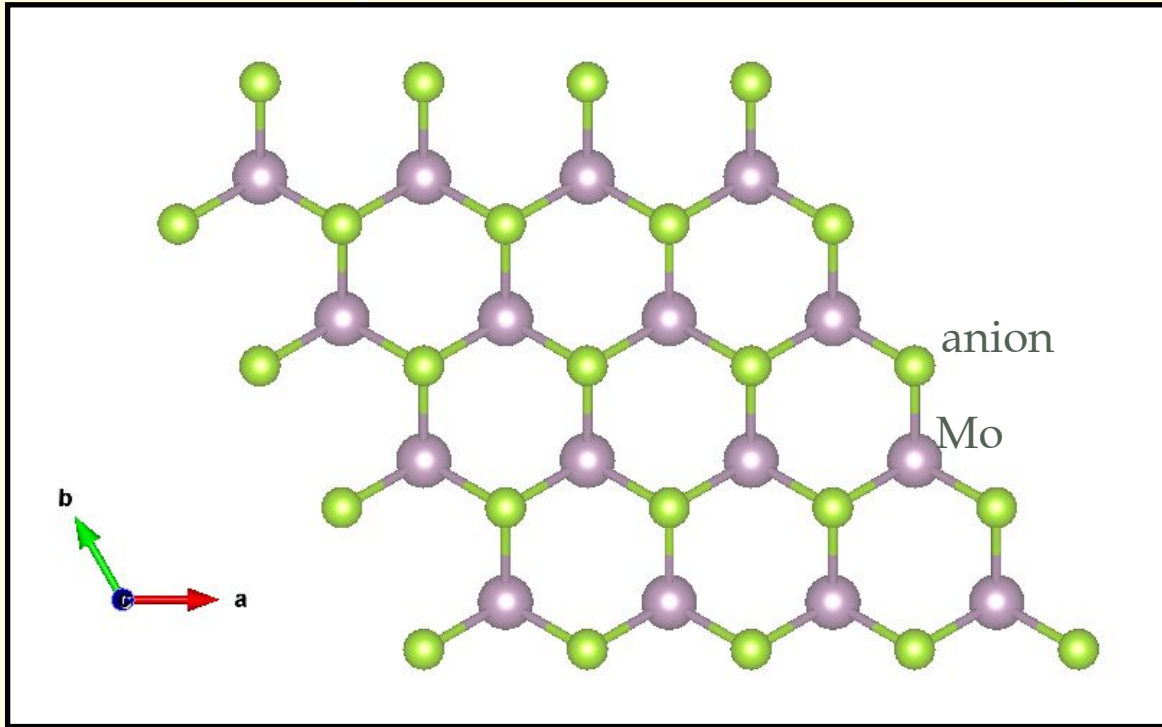
Department of Condensed Matter & Material  
Physics

S.N.Bose National Centre for Basic Sciences

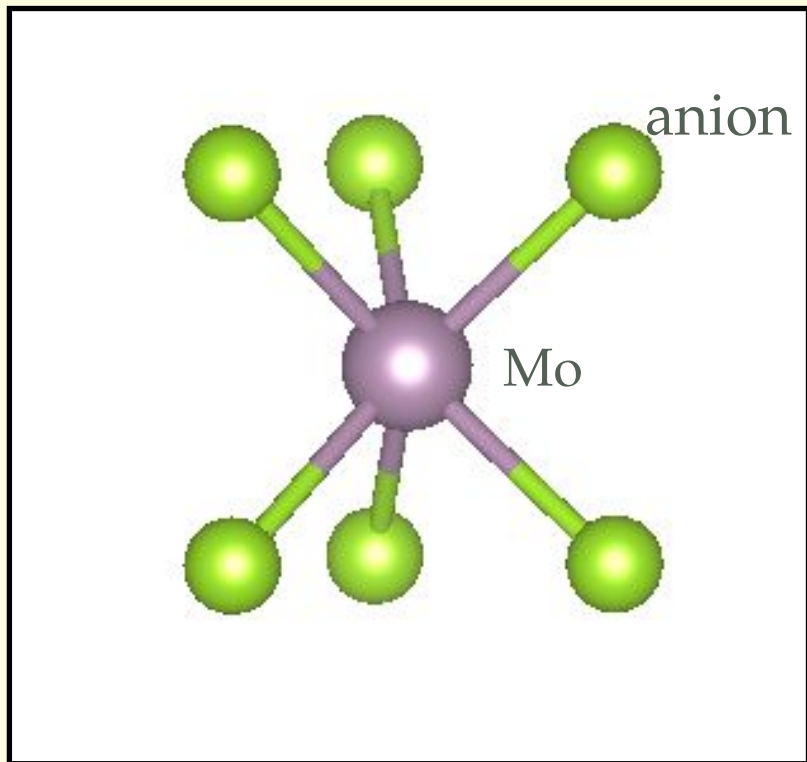
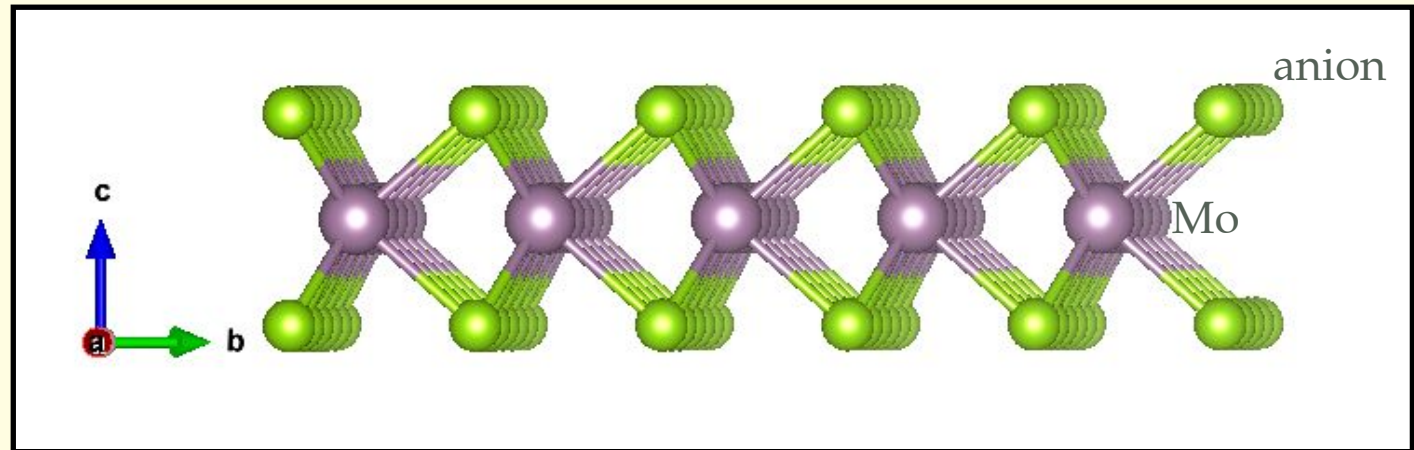


ICTS, July 2024.

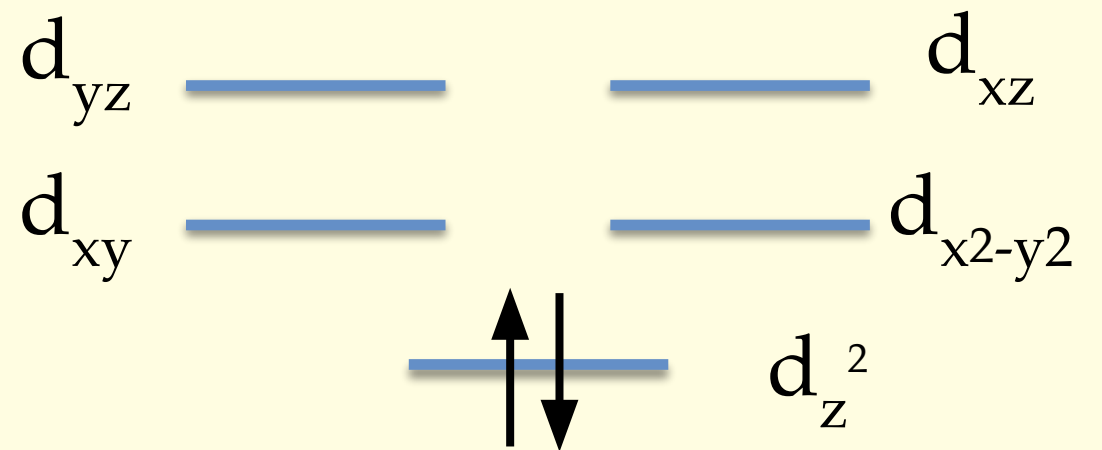
# The TMDCs (Mo, W based) : Why are they semiconducting?



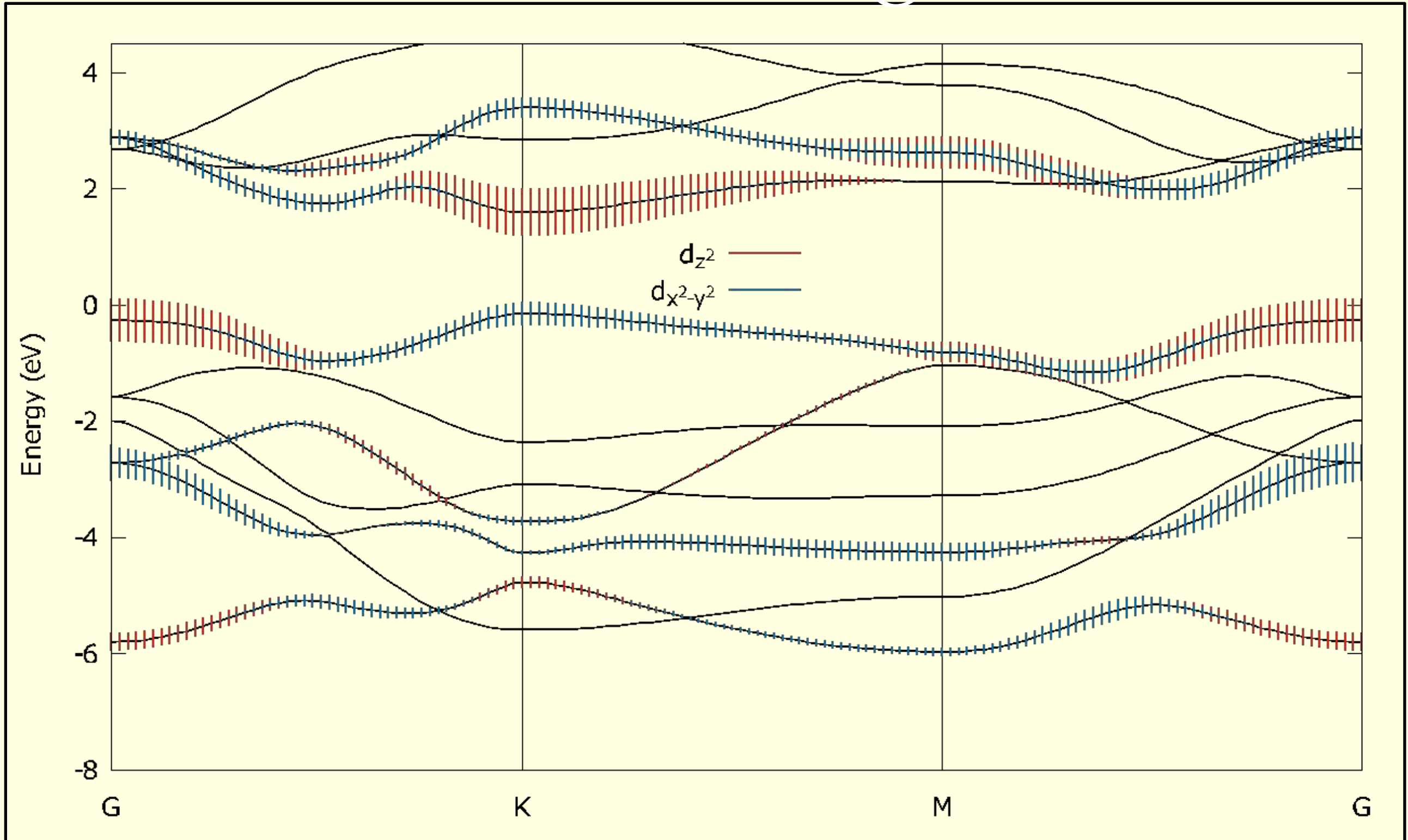
1H MoX<sub>2</sub>



d-orbitals of Mo

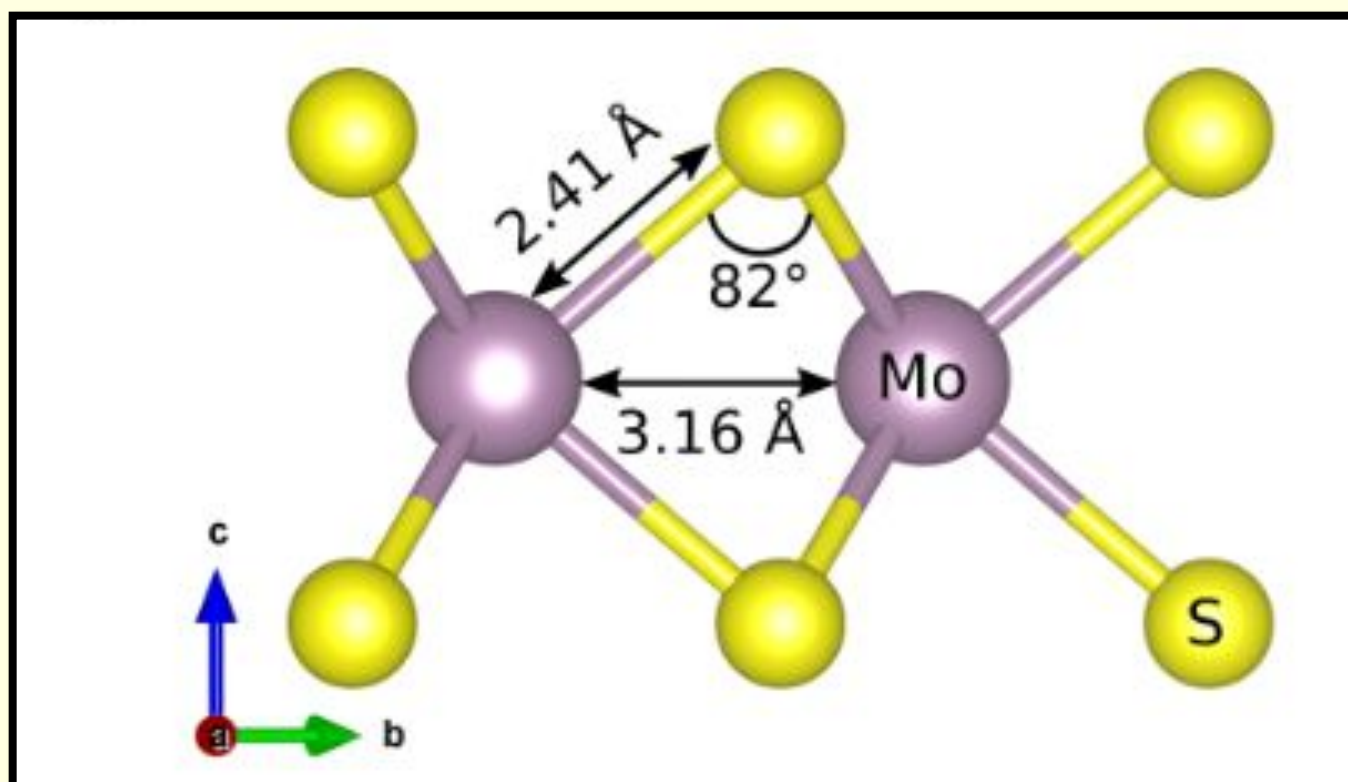


# Do we understand the semiconducting state?

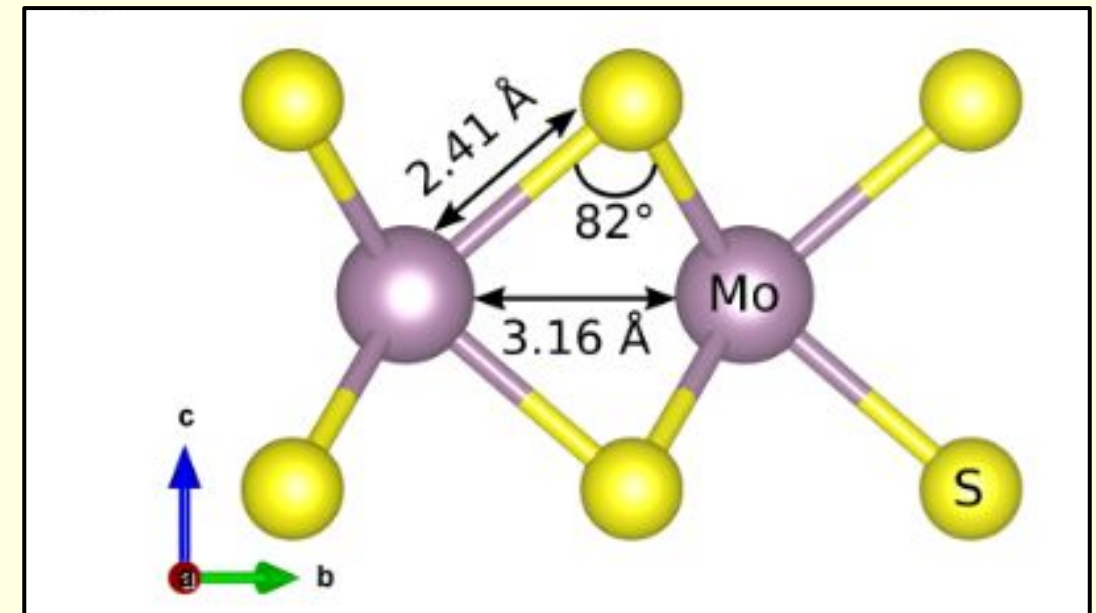
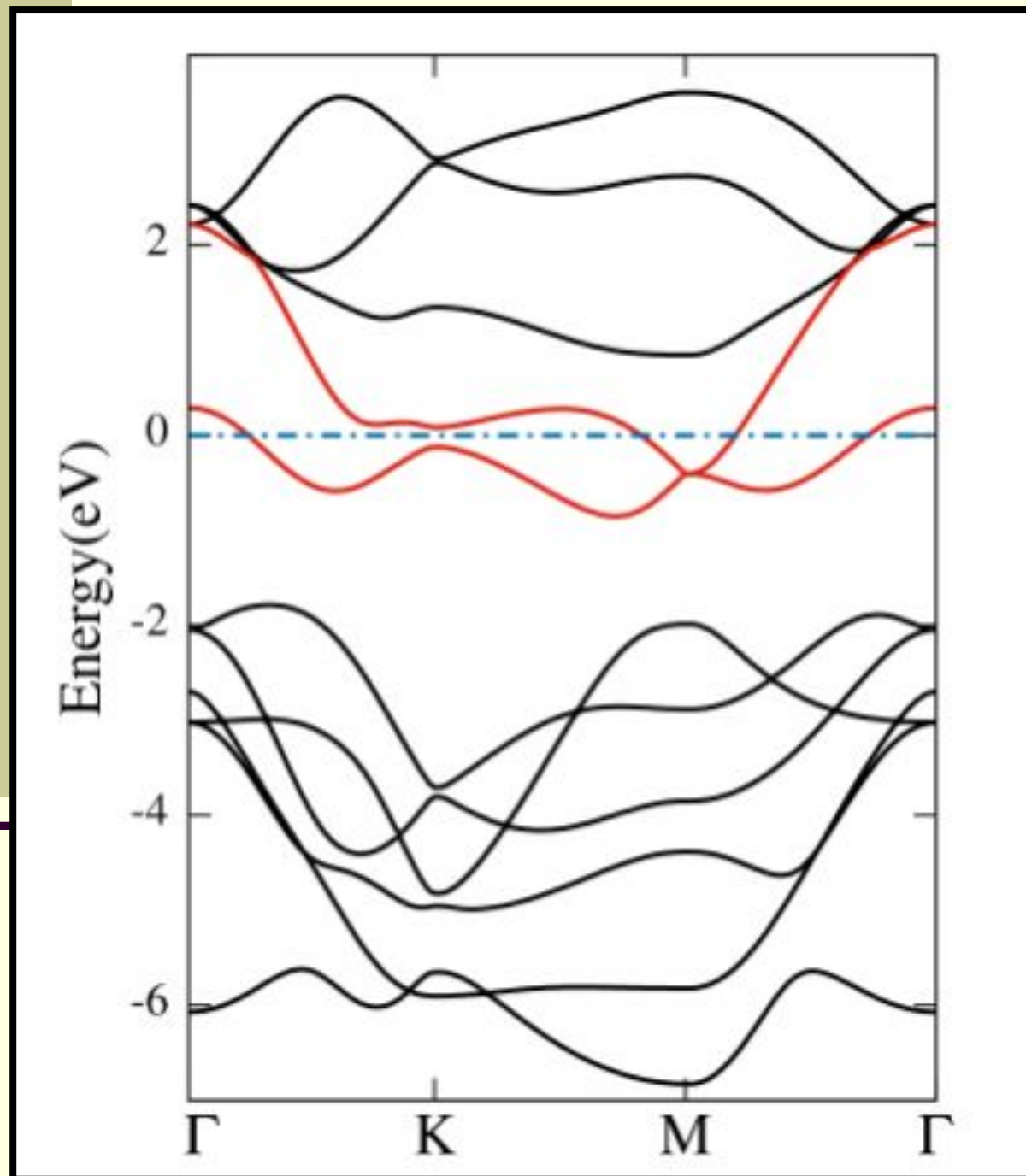


## A quick look at the structure

---



## Within a tight binding model



Switching off d-d interactions

**SYSTEM IS METALLIC**

What is the minimal model?



## But a d-only model fails

---

Interaction between in plane orbitals

$$h_{12} = \left( \frac{3\sqrt{3}}{4} V_{dd\sigma} - \sqrt{3} V_{dd\pi} + \frac{\sqrt{3}}{4} V_{dd\delta} \right) \sin \alpha \sin \beta$$

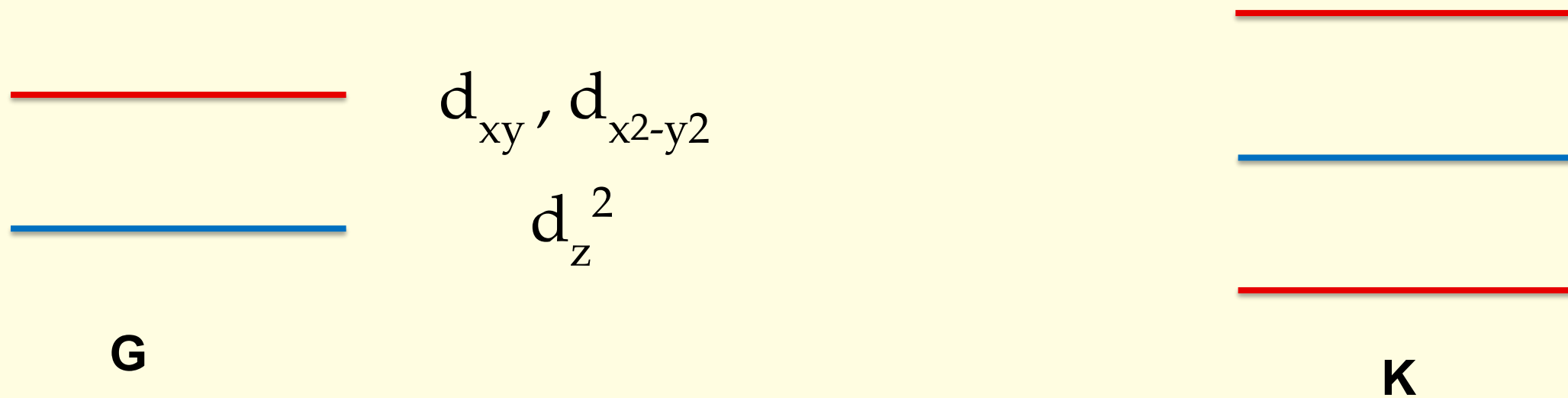
$$\alpha = ak_x \text{ and } \beta = a\sqrt{3}k_y$$

At  $\Gamma$  :  $\alpha = 0$  and  $\beta = 0$

At K :  $\alpha = (2\pi)/3$  and  $\beta = 2\pi$

**Both at  $\Gamma$  and K point, the in plane states remains degenerate!**

# reversal at G and K + the system remaining semiconducting?



Coupling between in-plane orbitals is through the p orbitals

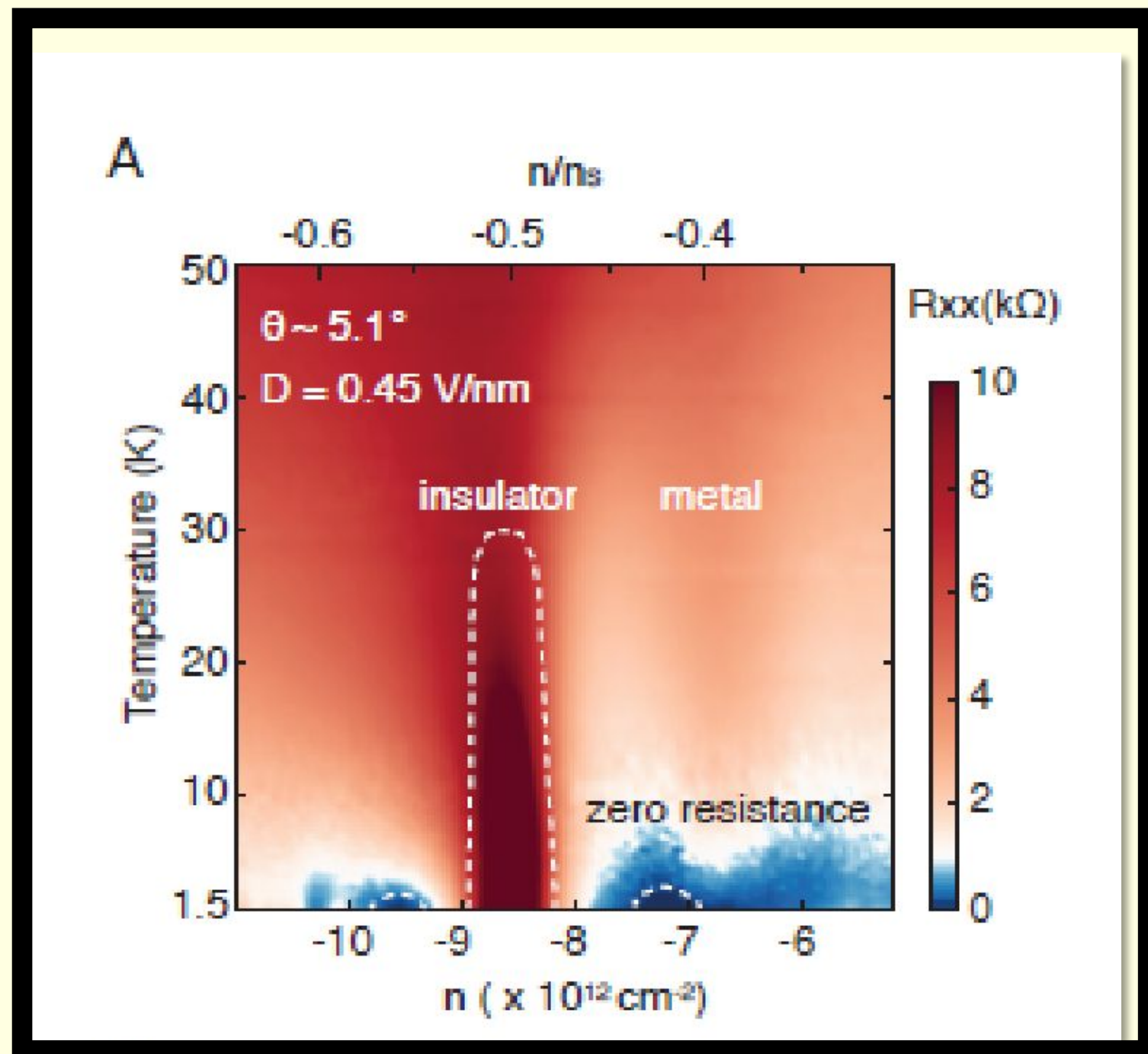
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Moving on to the twisted limit

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# For twisted $\text{WSe}_2$



L. Wang et al., Nat.

Materials 19, 861 (2020).

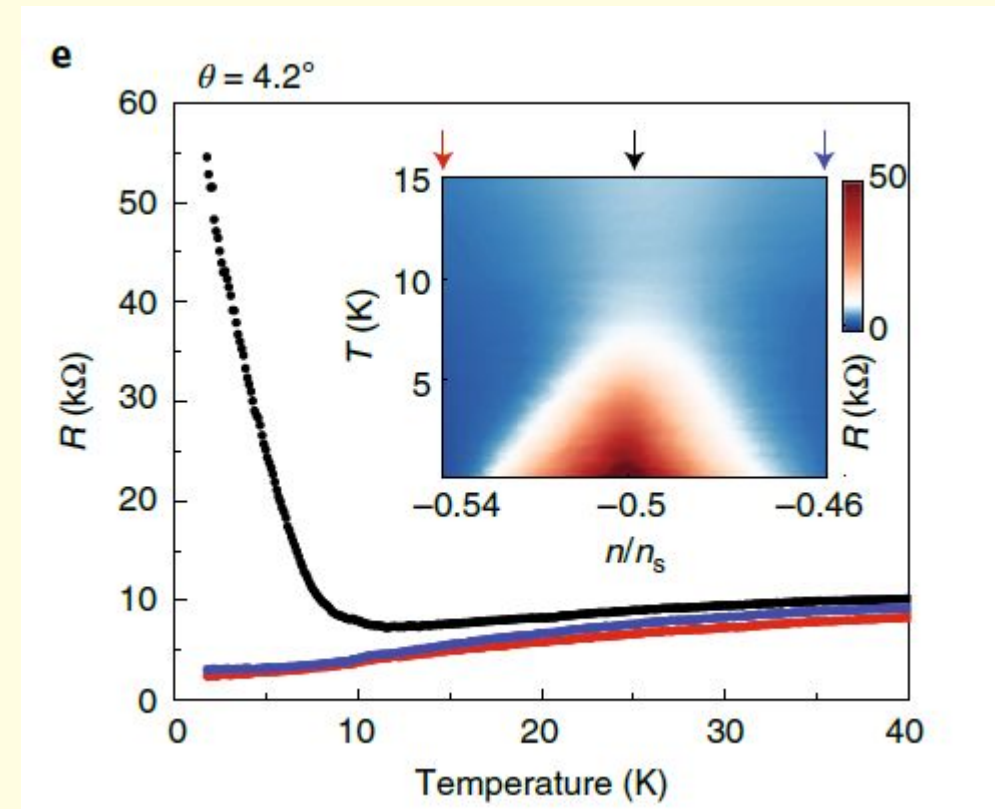
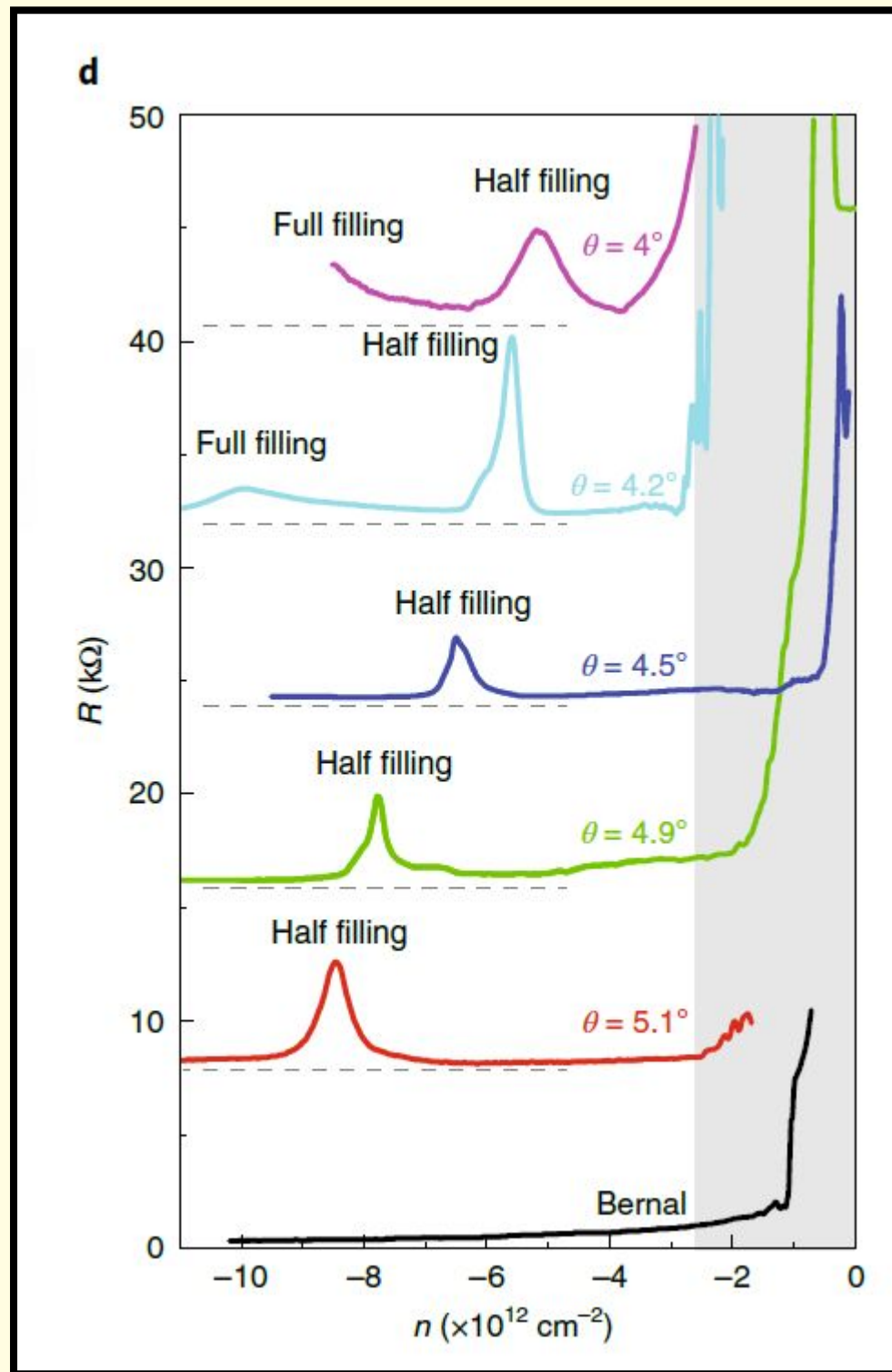
# What does one expect?

---

Conduction band

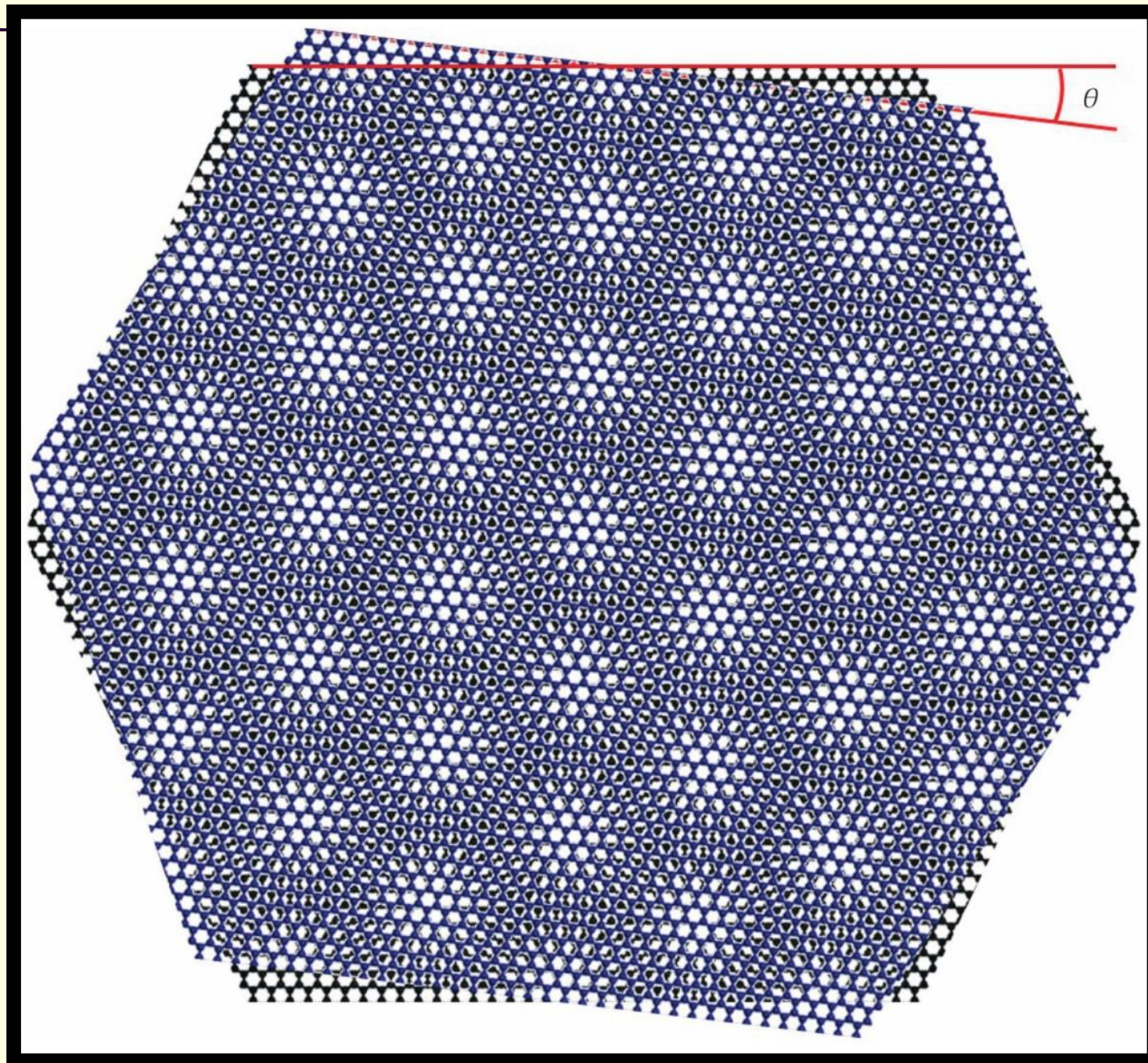
Valence band

For twisted  $\text{WSe}_2$





# The twisted bilayers :



Upper layer rotated slightly with respect to the lower layer.

This leads to

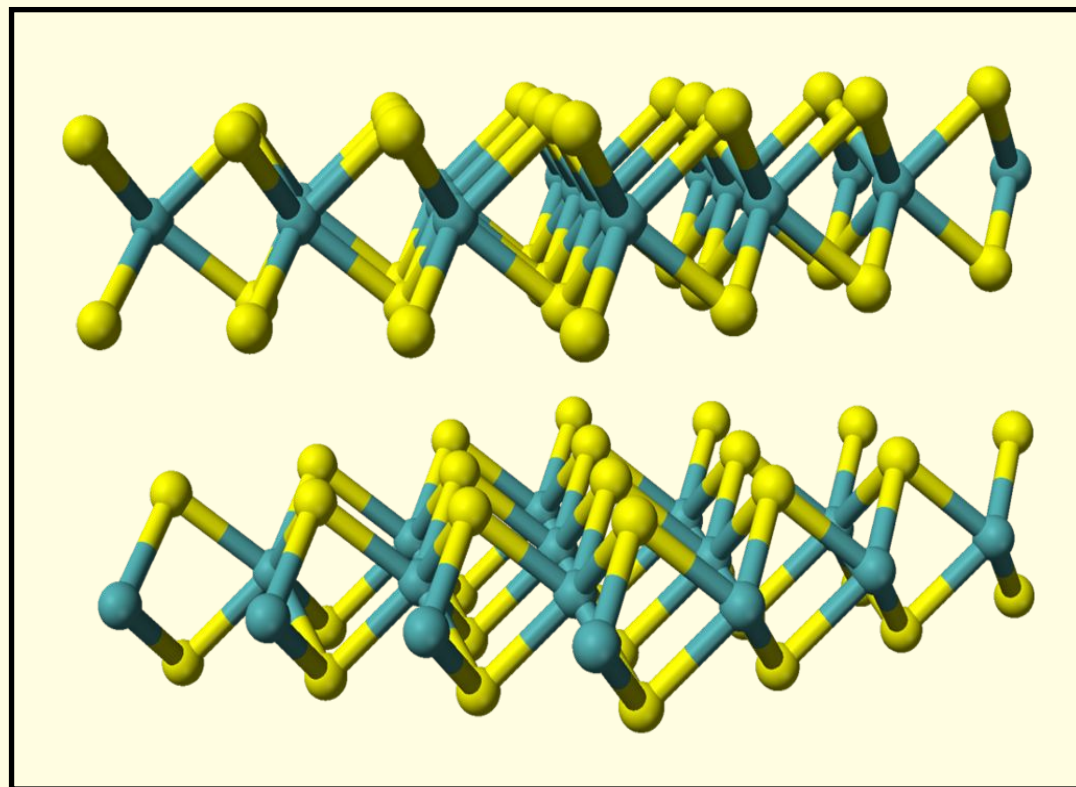
**large unit cells**

**small Brillouin zones**

Should we think of these as giant molecules with dispersionless levels?



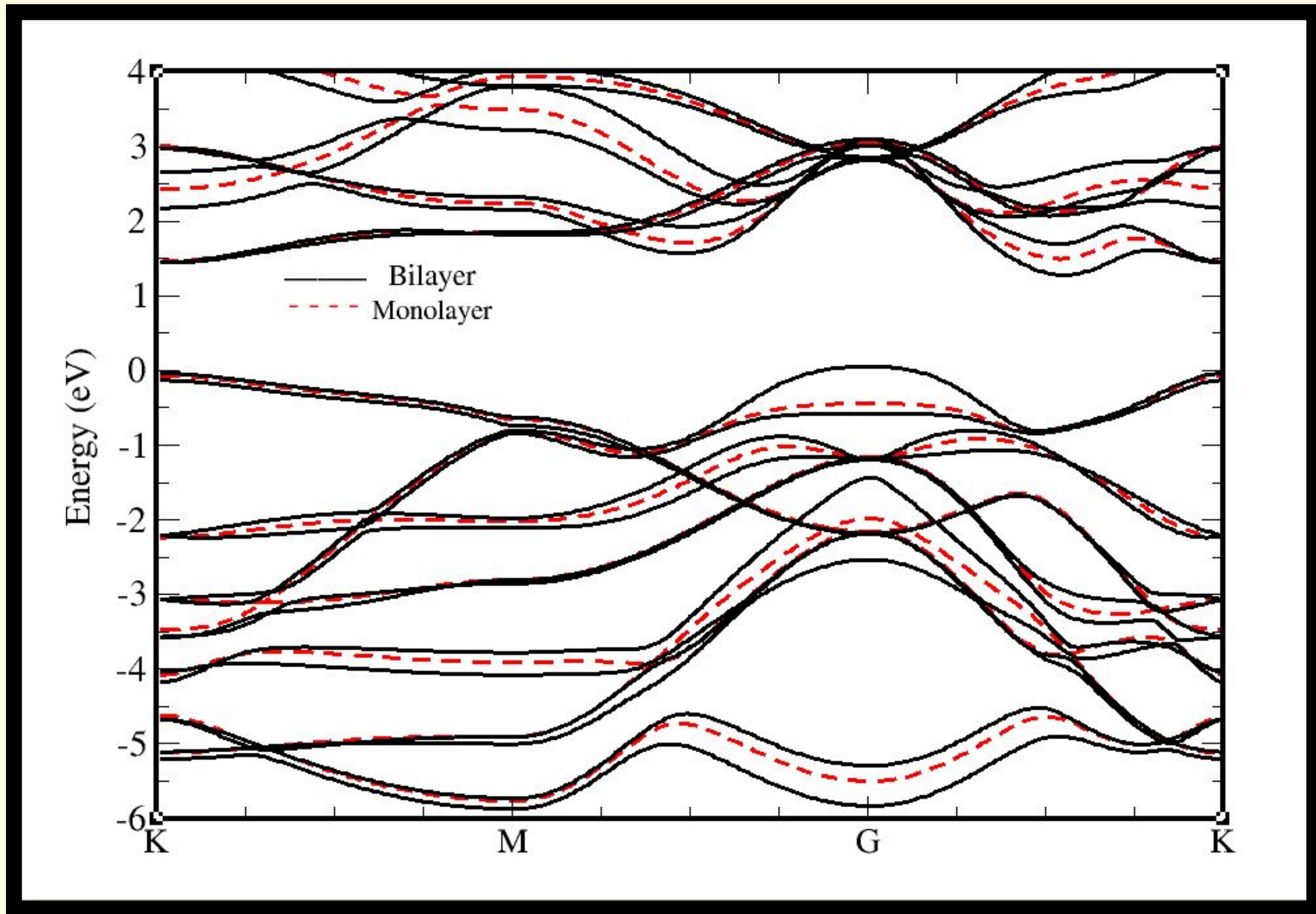
# What do we know about the untwisted bilayers?



Most popular technique to separate them is the “scotch-tape” technique.

Implying a weak interaction between the layers.

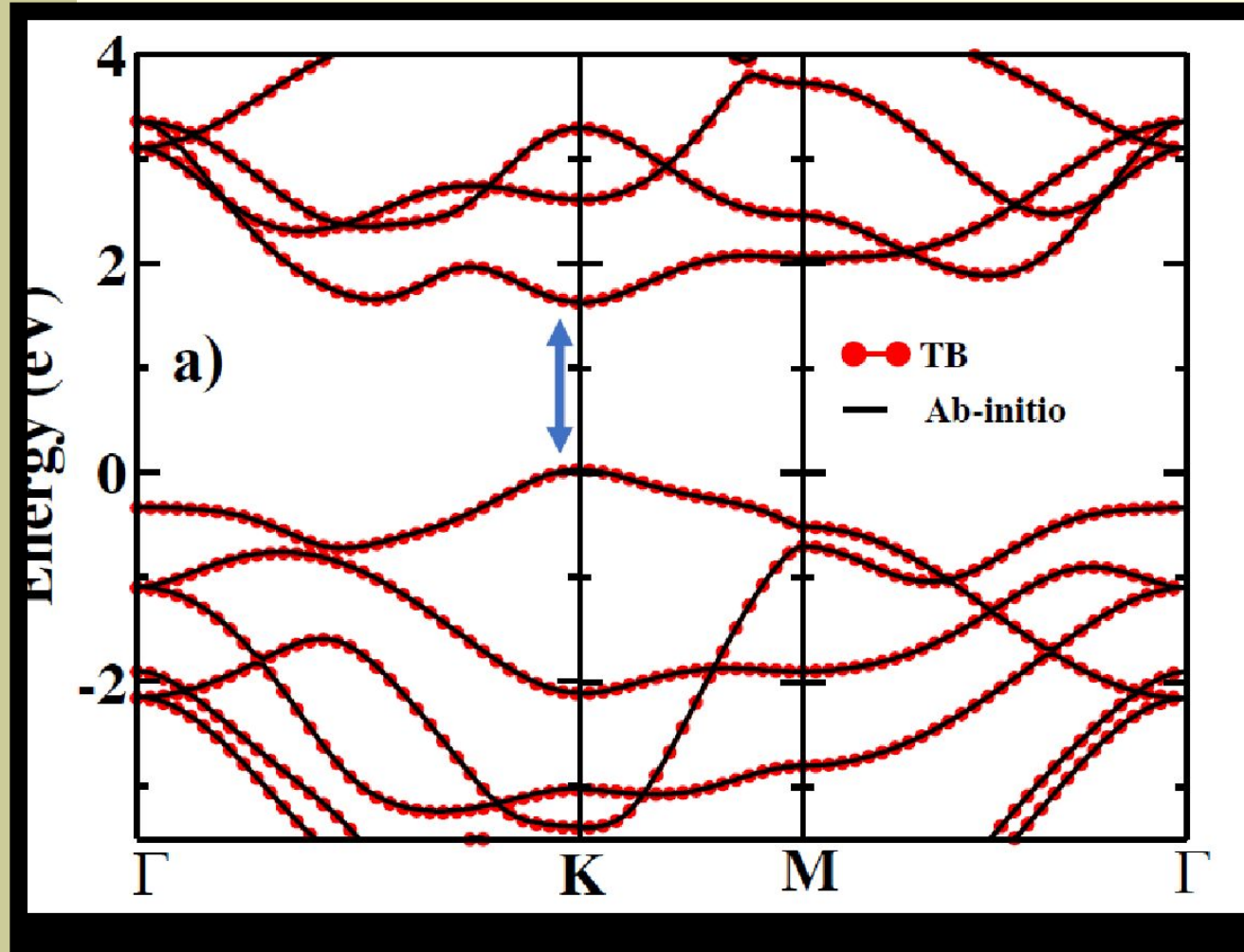
# Consequences of a weak coupling between the layers



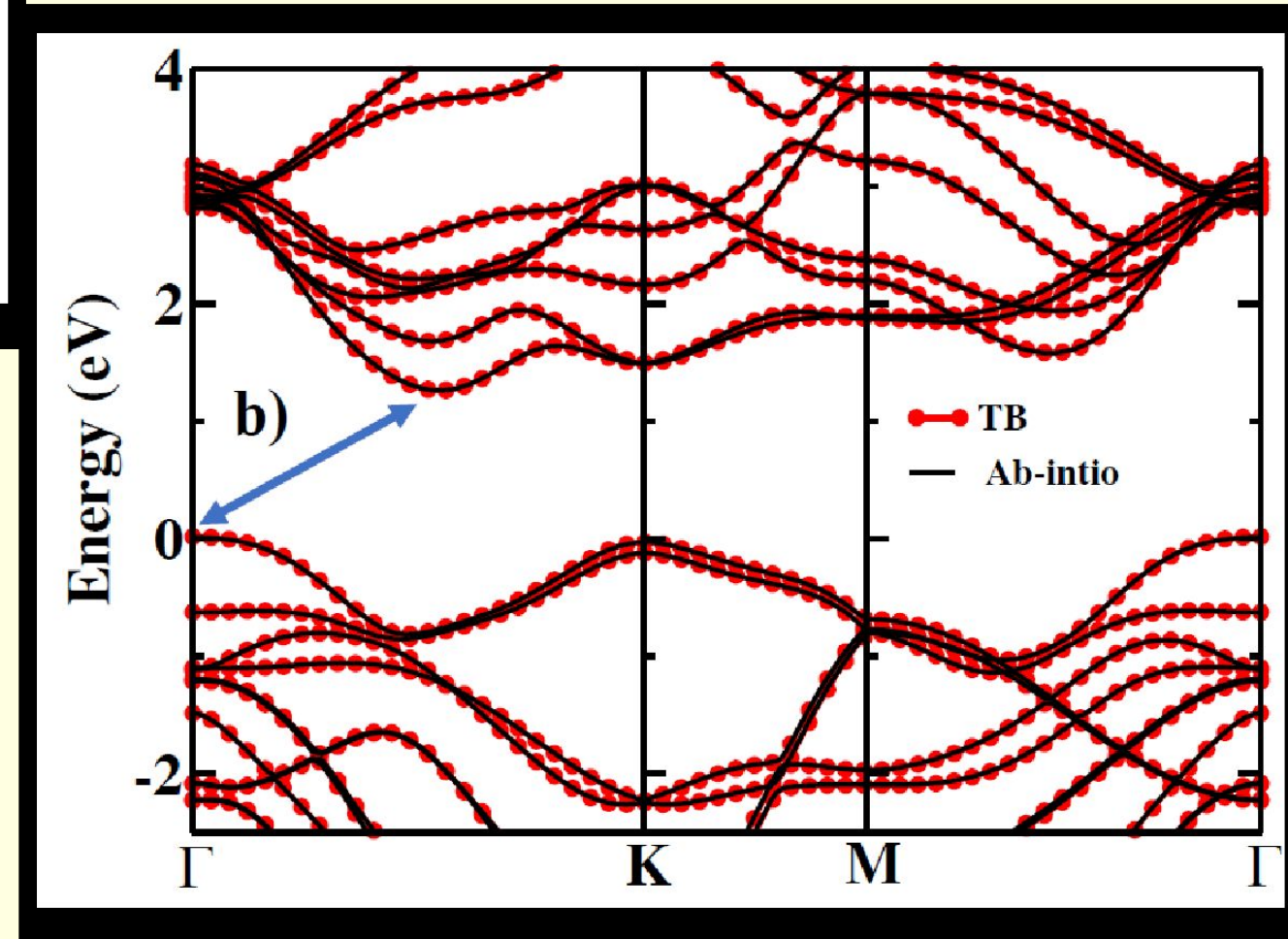
**Suggesting a weak perturbation of the monolayer band structure.**

# Why do we see changes?

## Monolayer

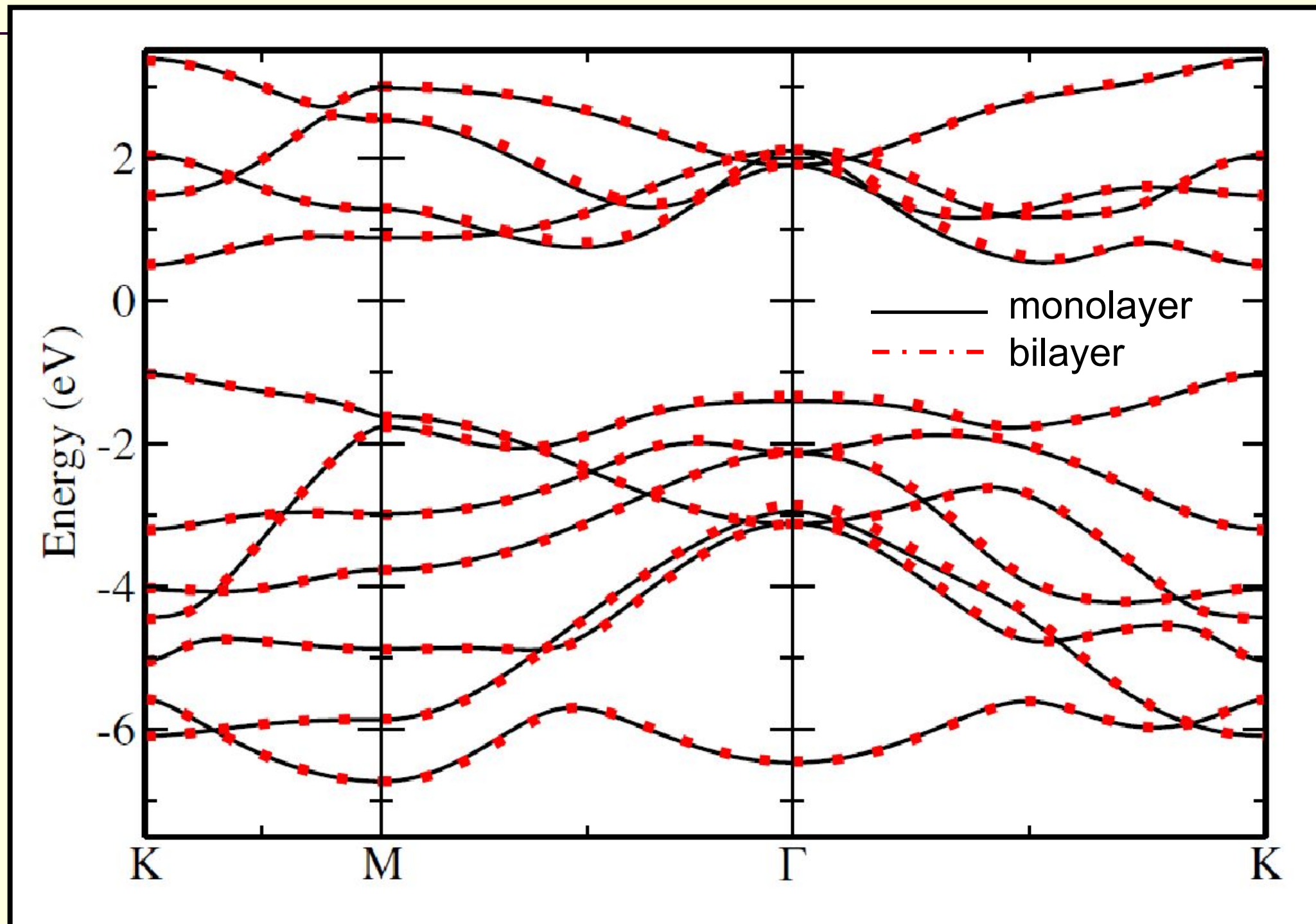


## Bilayer





# Bilayer band structure with interlayer interactions switched off, superposed on monolayer



So how should we view the Moire unit cells?

**Untwisted limit + a weak perturbation**

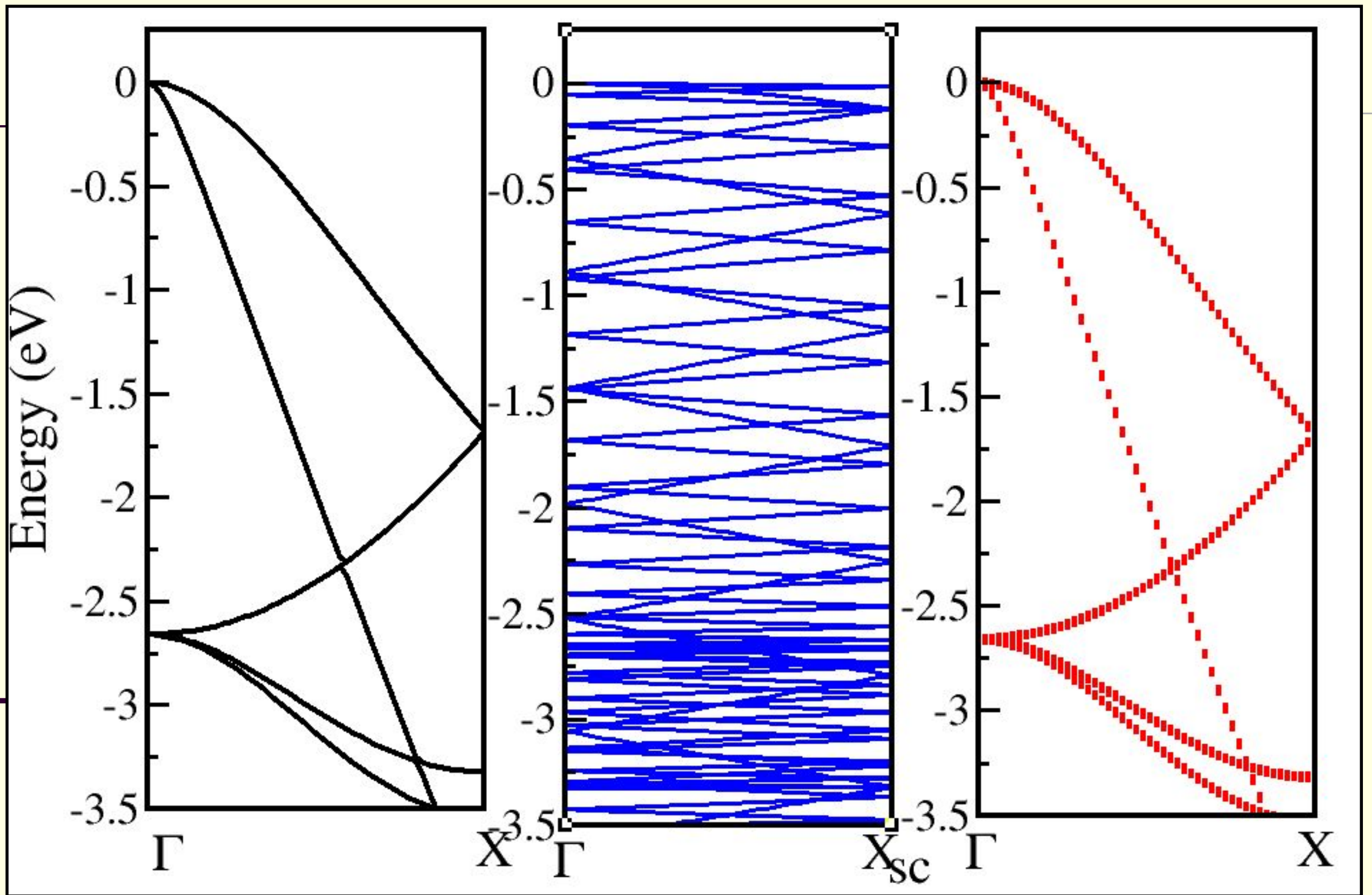
**First introduced by us in**

**P. Kumari, J. Chatterjee and P. Mahadevan, Phys. Rev. B 045432 (2020).**

How should we recover the primitive cell limit?

$$P_{\vec{K}m}(\vec{k}_i) = \sum_n |\langle \vec{K}m | \vec{k}_i n \rangle|^2$$

$$P_{\vec{K}m}(\vec{k}_i) = \sum_{\vec{g}} |C_{\vec{K}m}(\vec{g} + \vec{k}_i - \vec{K})|^2$$

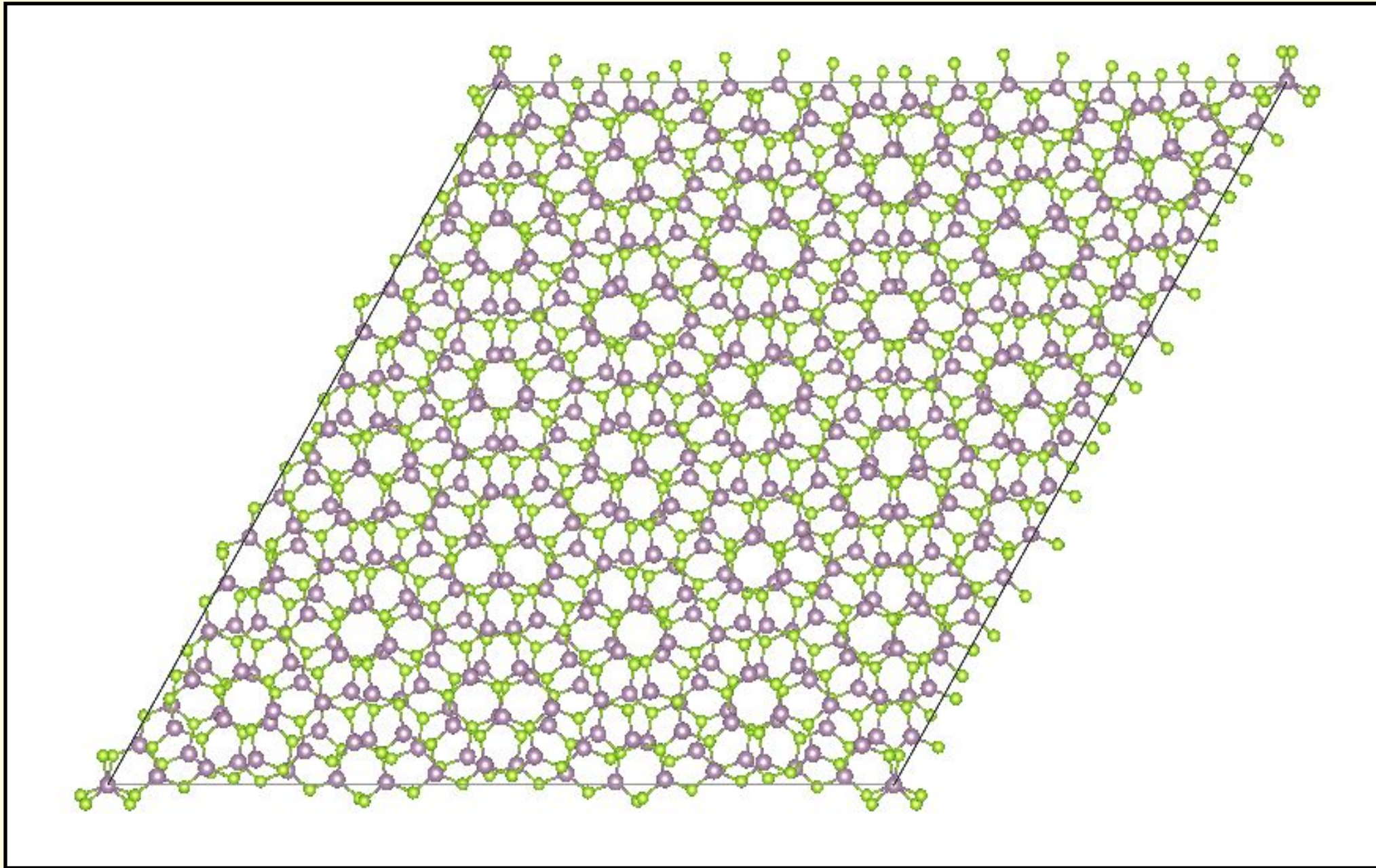


Primitive cell

Super cell

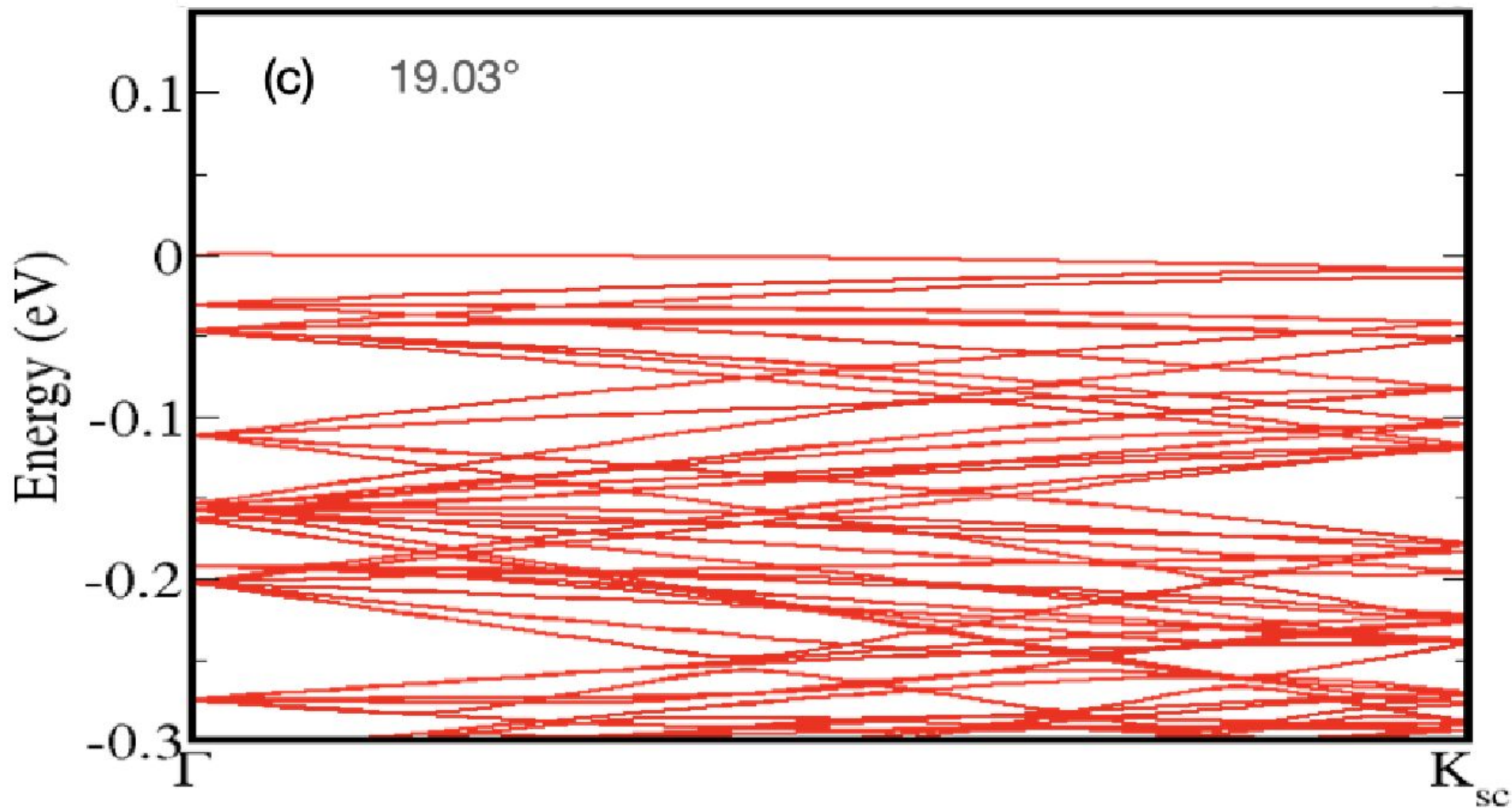


# Twisted bilayer of $\text{MoSe}_2$ at $19.03^\circ$



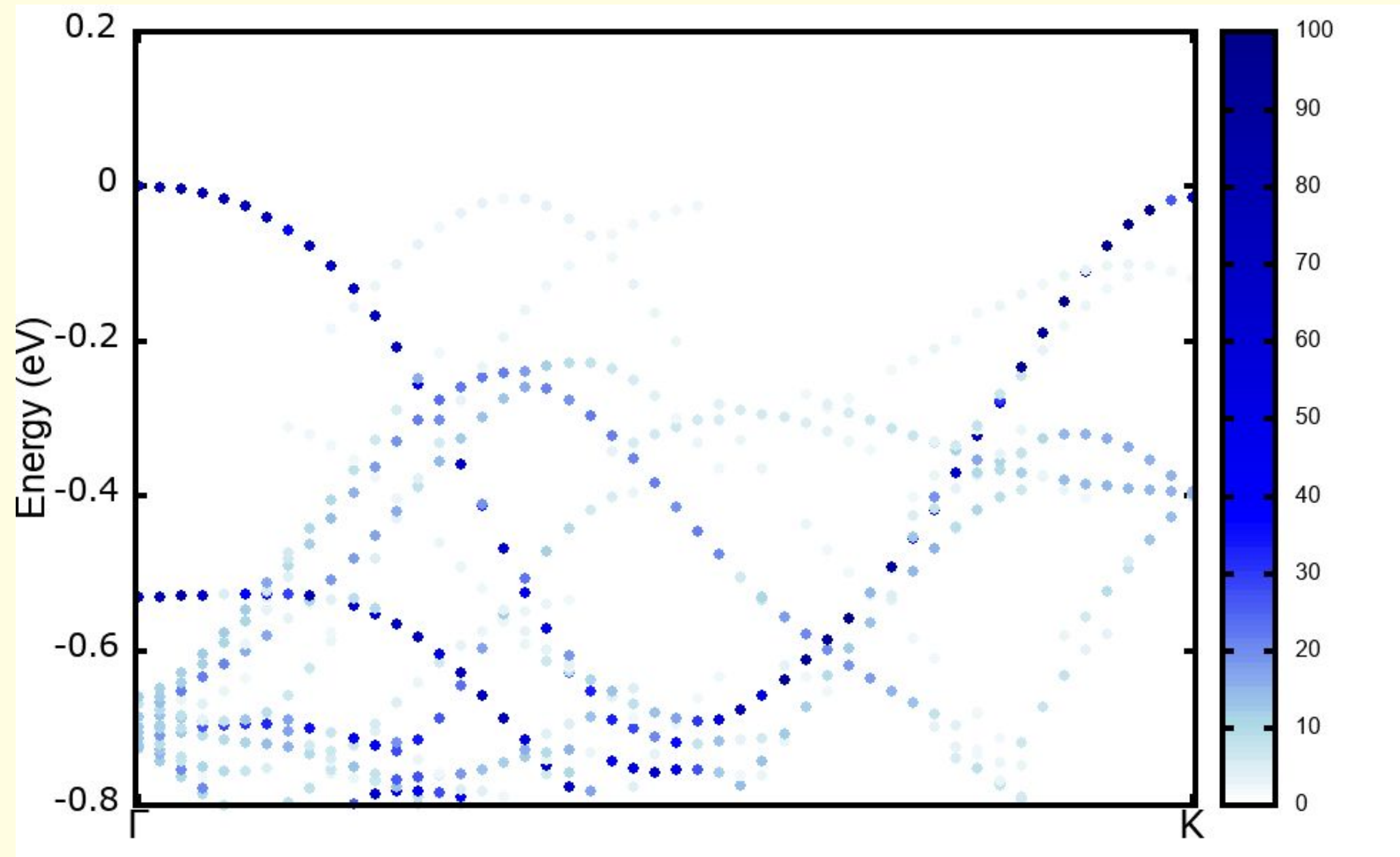
No of atoms=1482  
Unit cell dimensions ~ 51.69 Å 16 x primitive unit cell

## Along the Moire cell direction



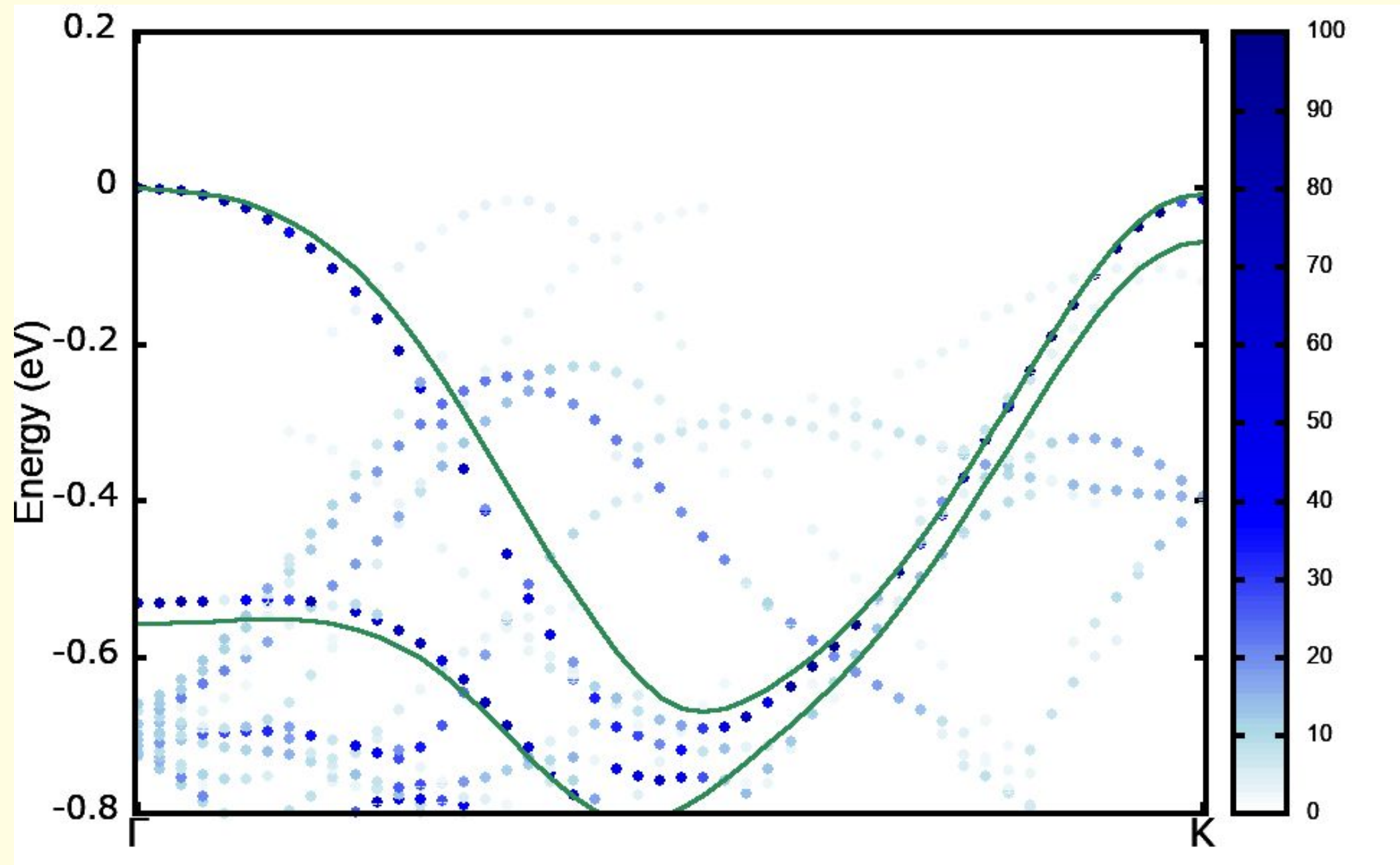


# Along the primitive cell directions





# Comparison with the unperturbed band structure

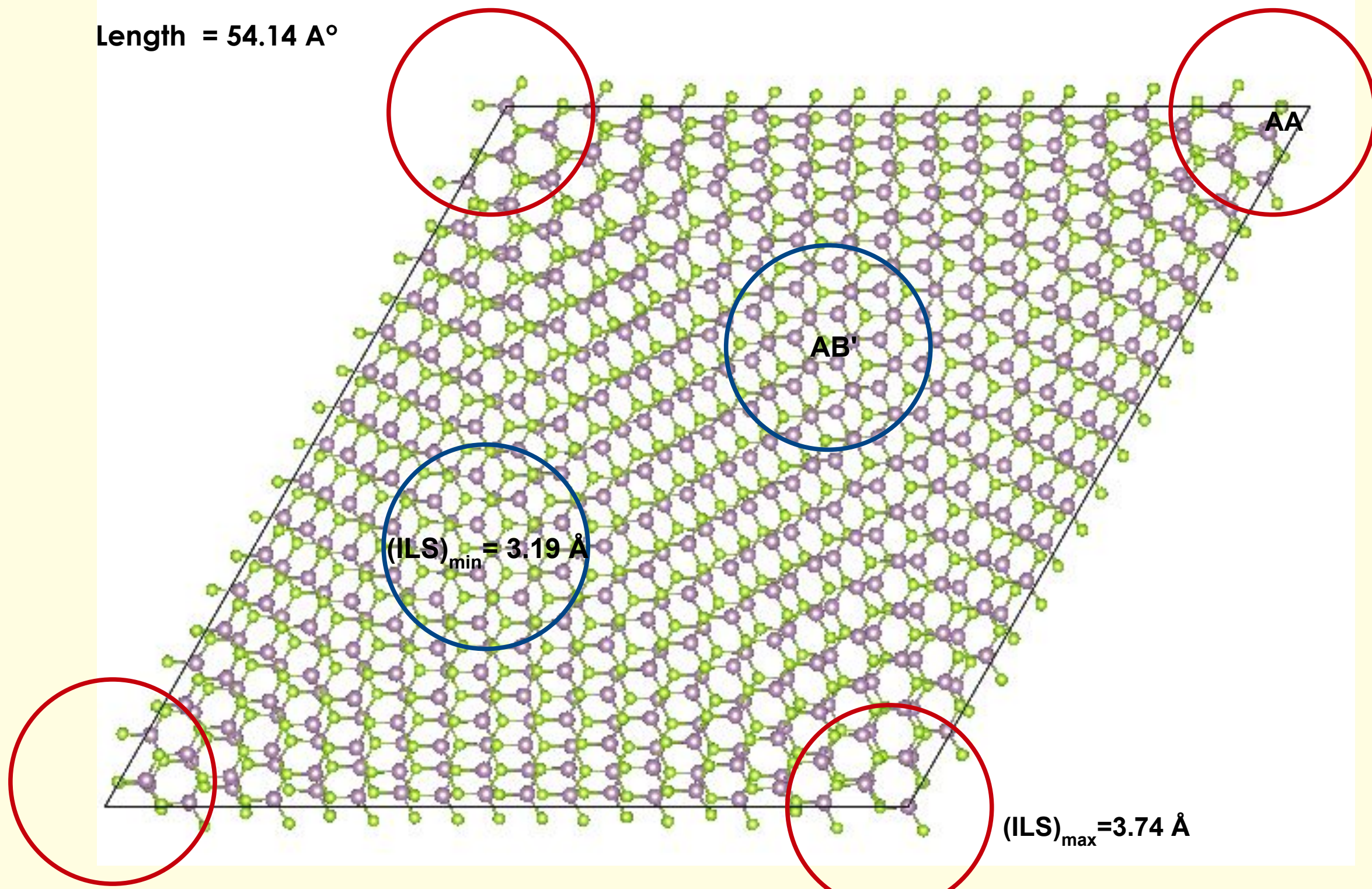


The low energy band structure is very weakly perturbed.

So is the low energy electronic structure always similar to the untwisted limit?

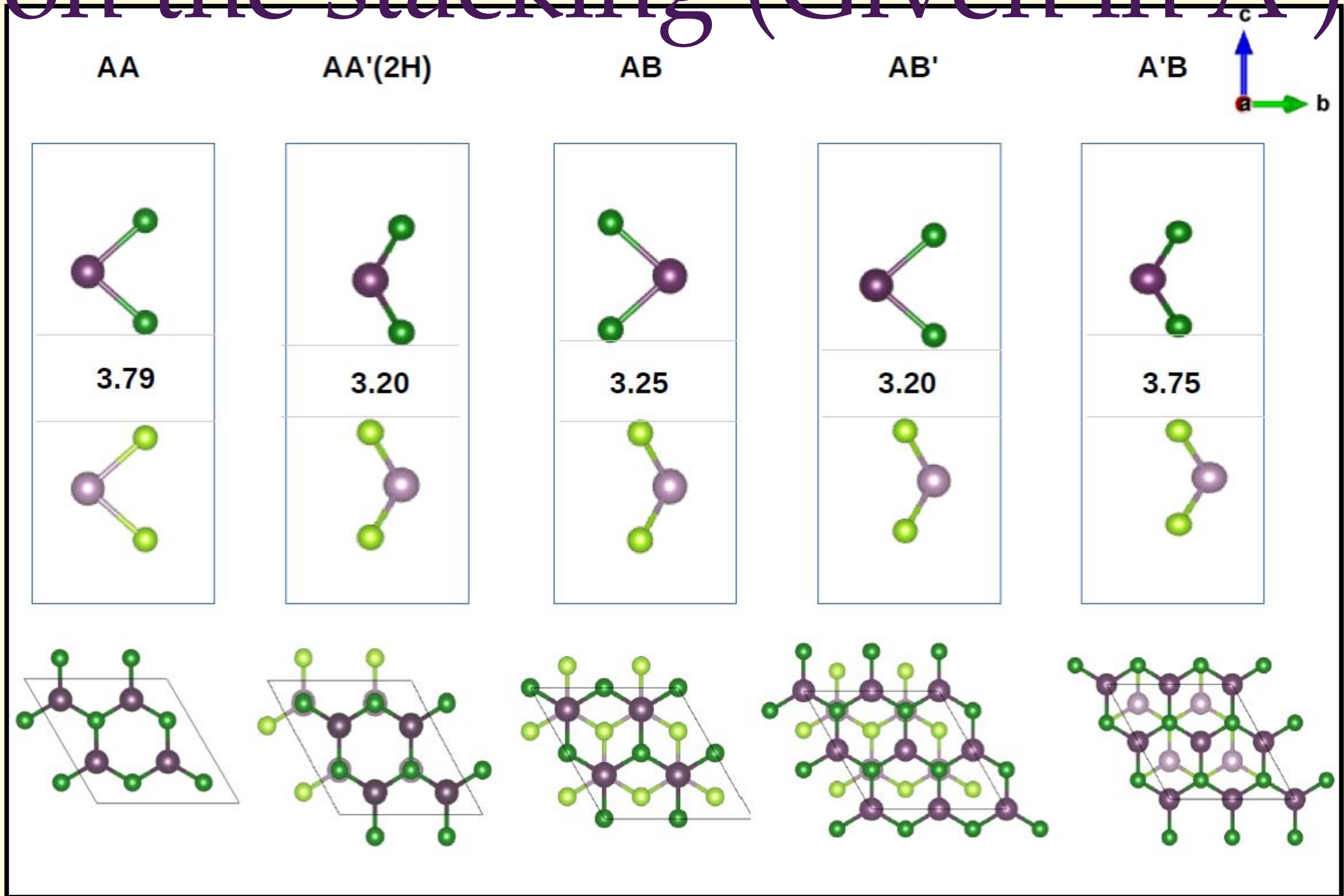
# Twisted bilayer of $\text{MoSe}_2$ at $3.48^\circ$

Length =  $54.14 \text{ \AA}$

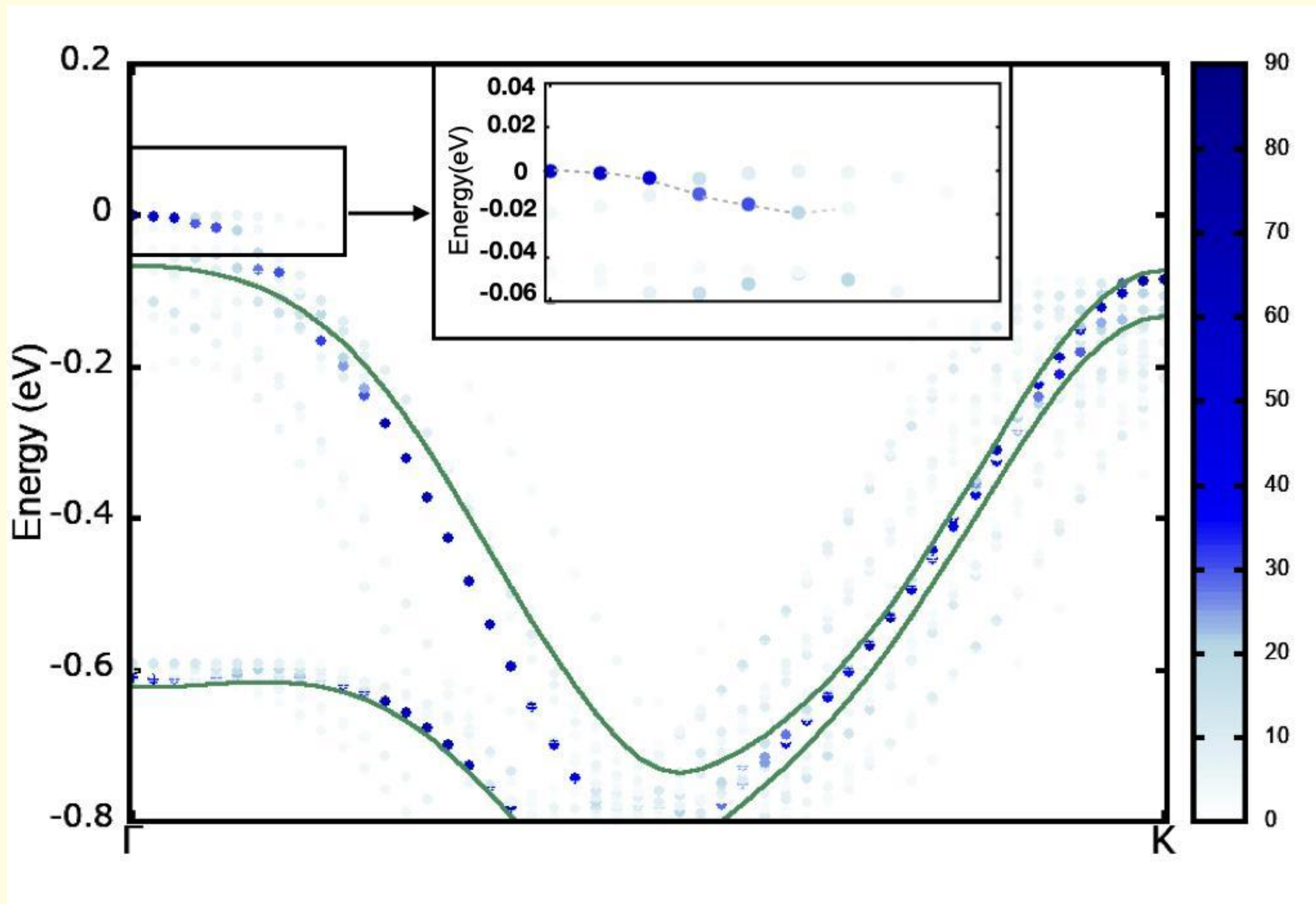




# Interlayer distance depends on the stacking (Given in Å)

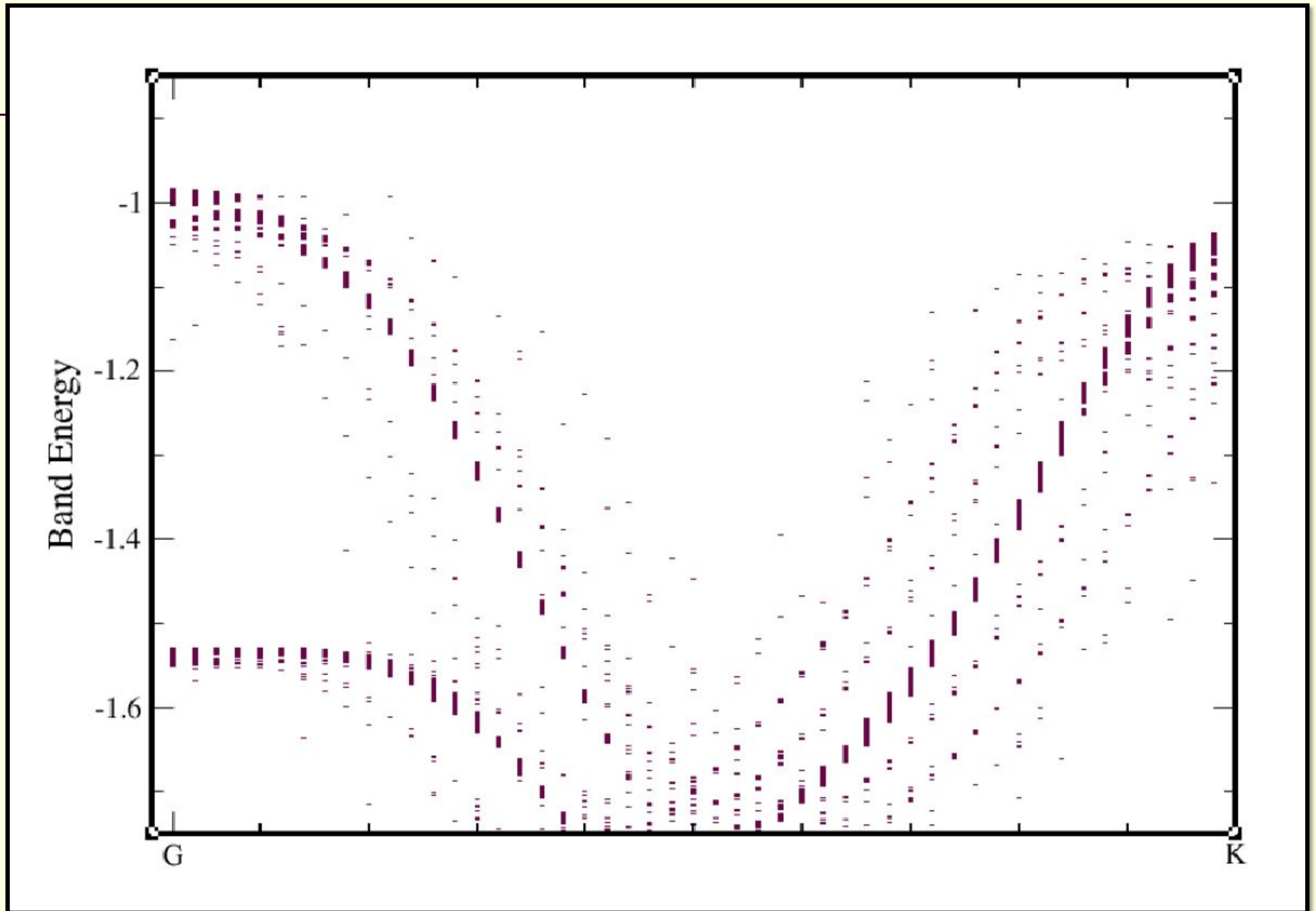


# Along the primitive cell directions

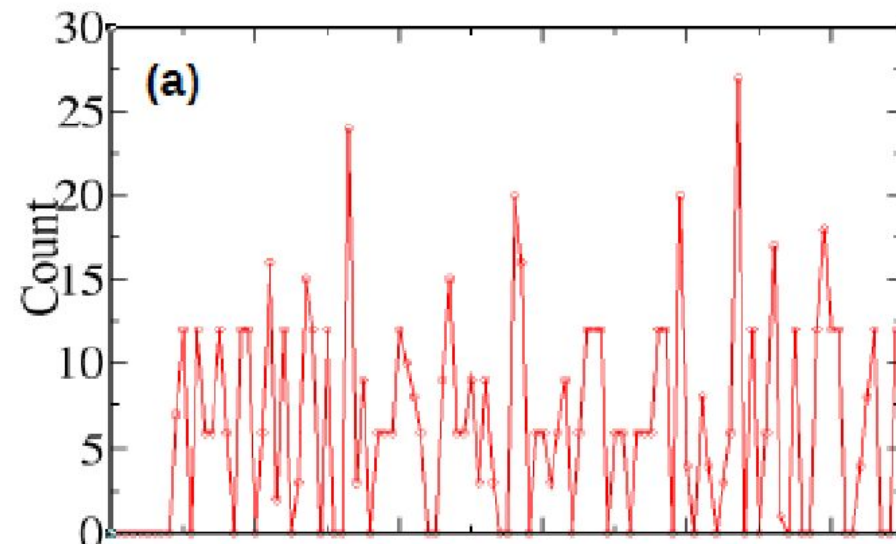


Split off band has a width of 19 meV

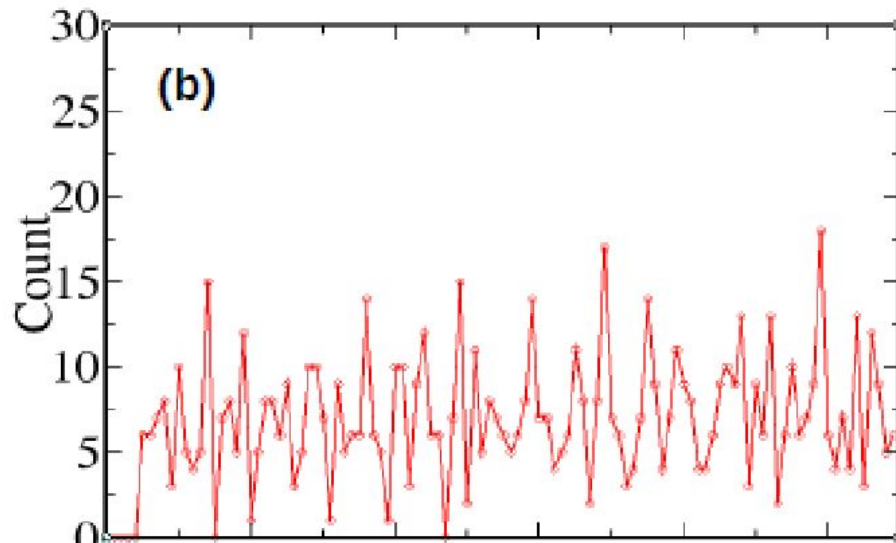
At a fixed interlayer separation of  $3.44 \text{ \AA}$



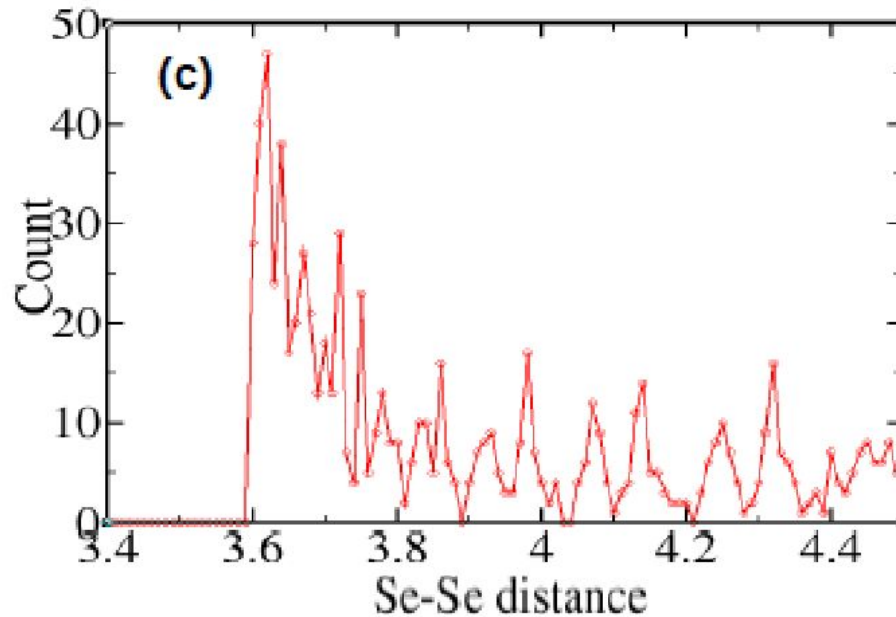
# Interlayer Se-Se distances



19.03°



3.48° at fixed interlayer separation

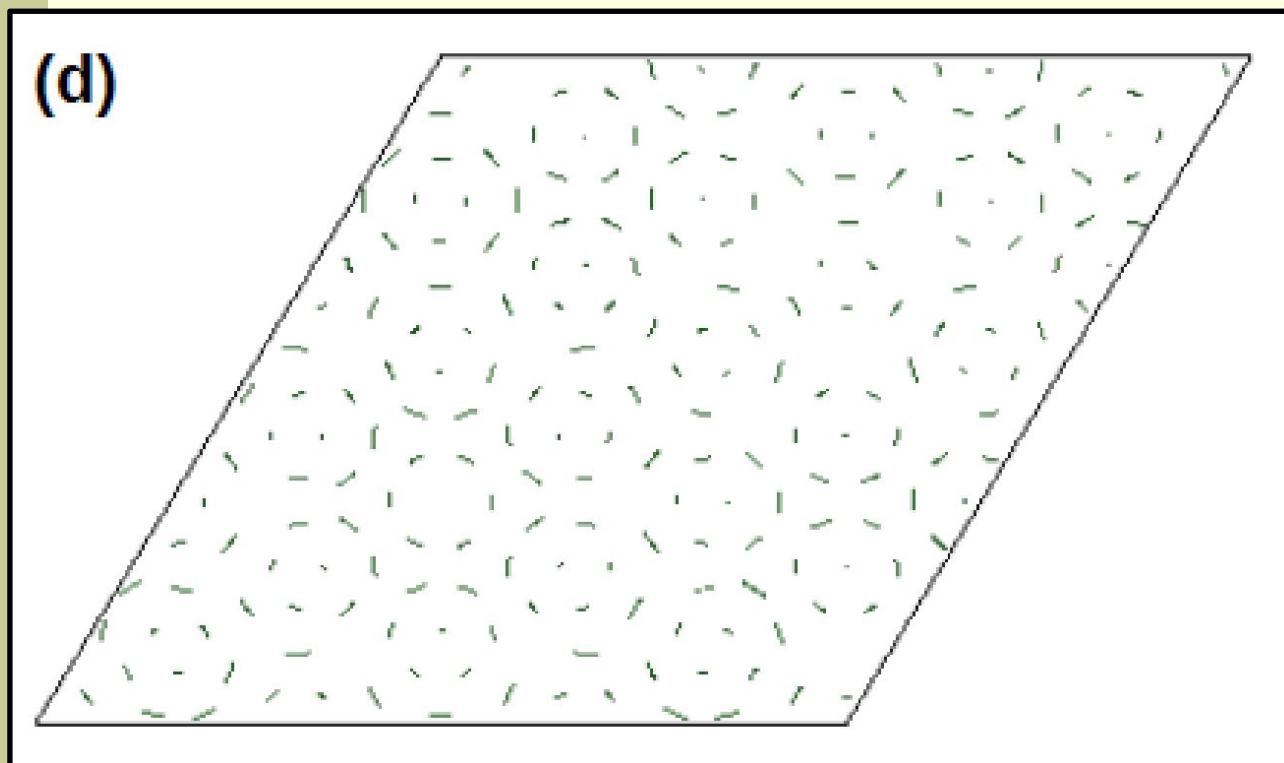


3.48° with interlayer separation optimised

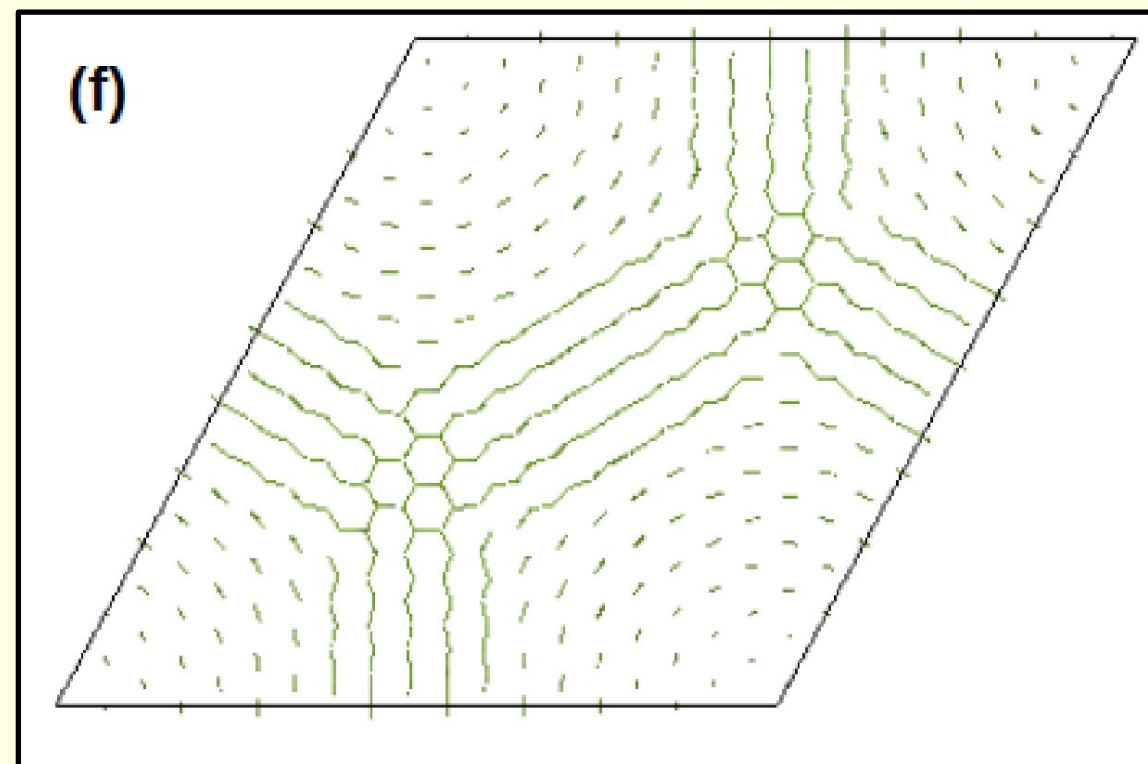


## Shortest set of Se-Se distances $< 3.8 \text{ \AA}$

At  $19.03^\circ$  with optimised structure

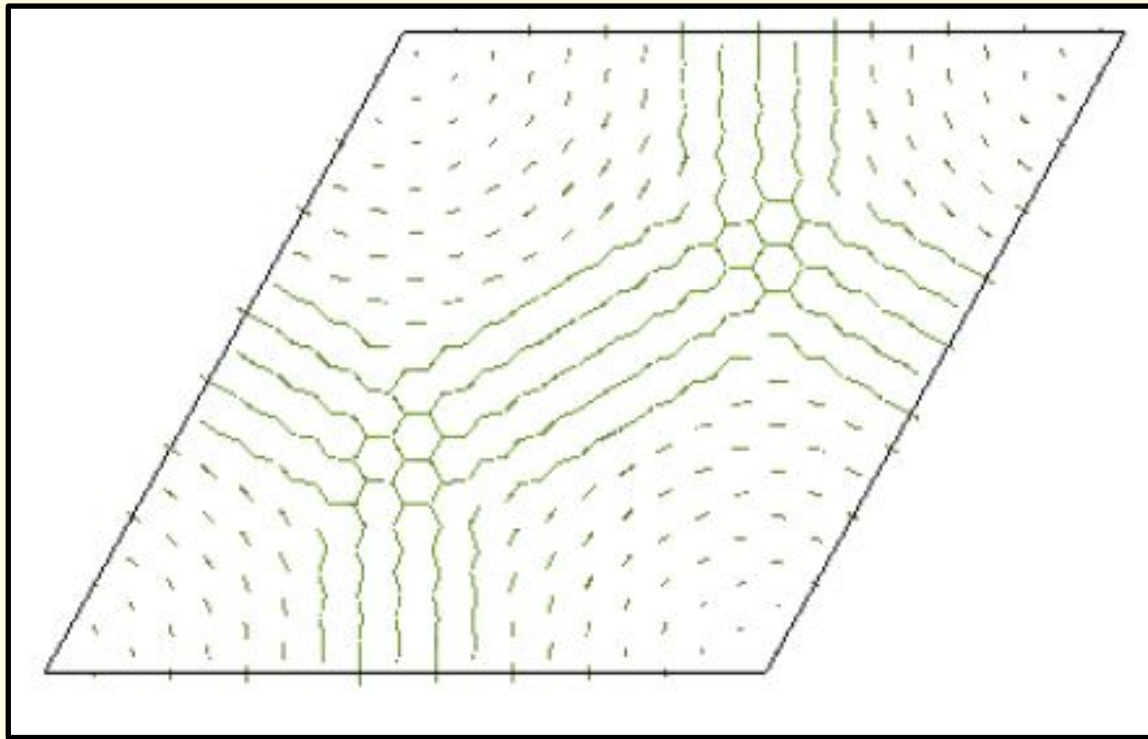


At  $3.48^\circ$  with optimised structure

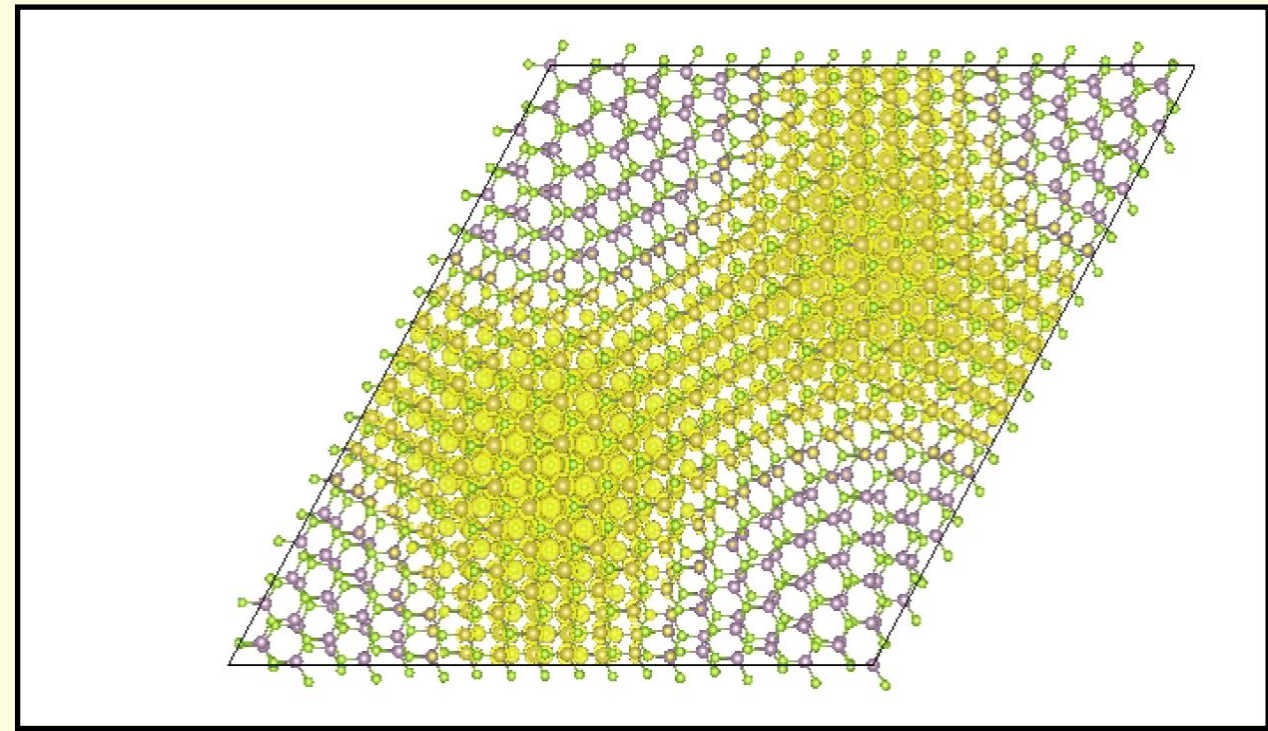


The sub-band formation emerges from concentrated regions of enhanced inter-layer interaction strengths.

At  $3.48^\circ$  with optimised structure.



Shortest set of  
Se-Se distances  $< 3.8 \text{ \AA}$



Charge density of the split off band  
at Gamma.

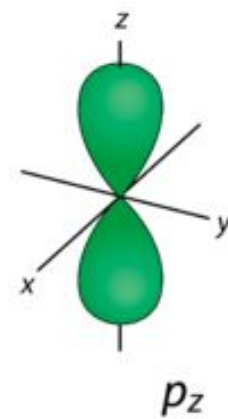
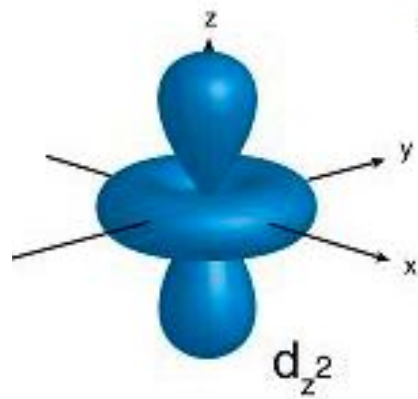
Concentrated regions of enhanced inter-layer interaction strengths lead to sub-band formation for twisted bilayers.

# Gamma

$(\text{VBM})_{\Gamma}$

$d_{z^2}, p_z$

Out of plane orbitals



**Large Interlayer coupling**

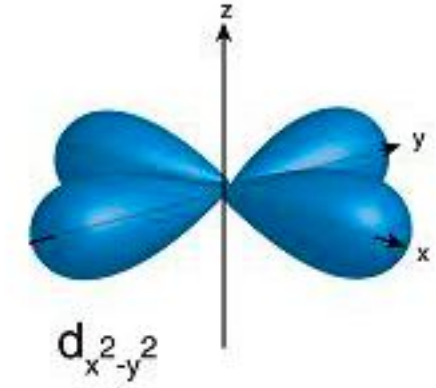
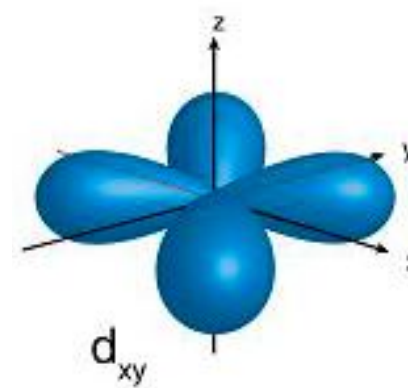
**Small Spin orbit coupling**

# K-valley

$(\text{VBM})_{\text{K}}$

$d_{x^2-y^2}, d_{xy}$

In plane orbitals

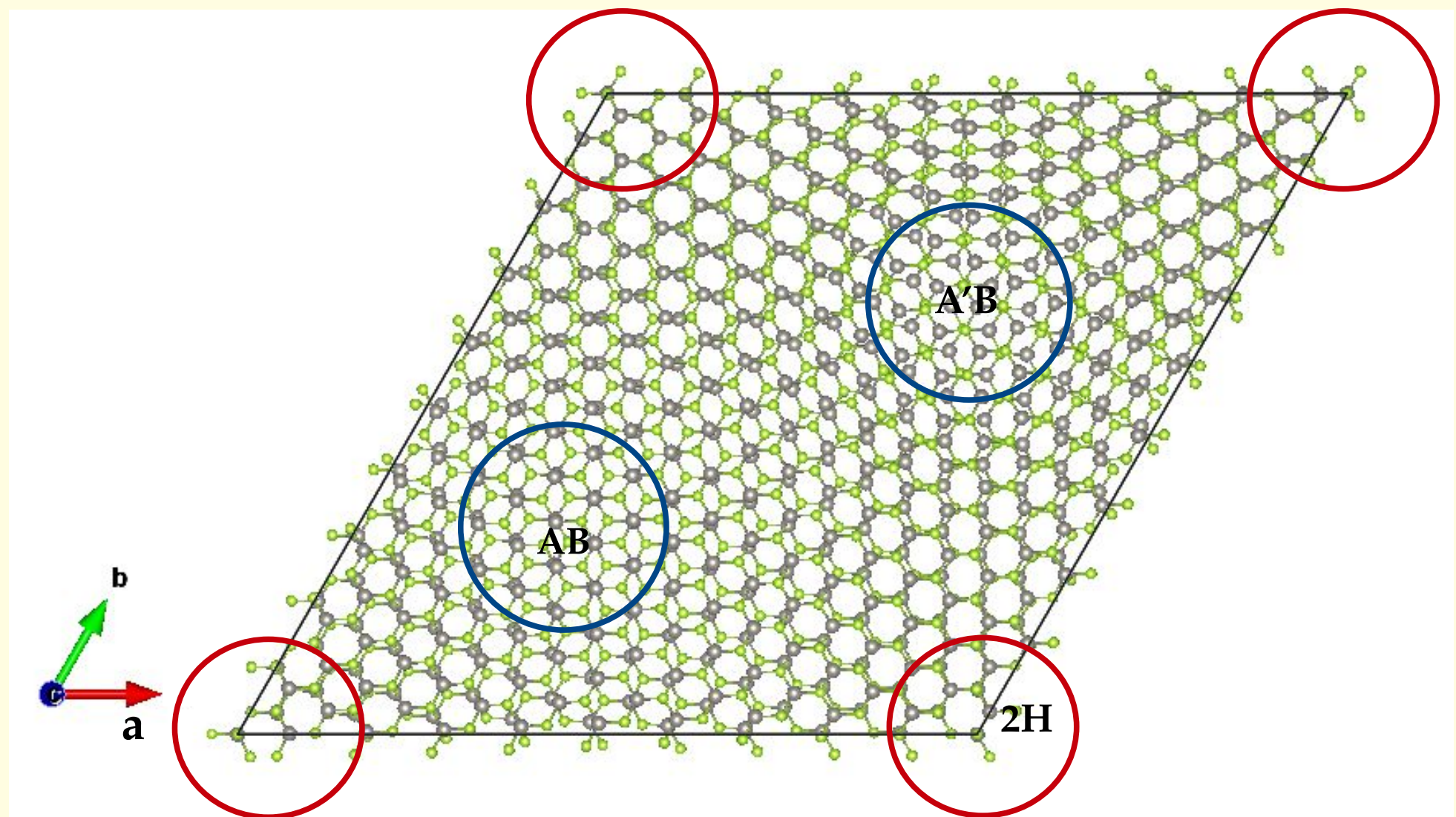


**Small Interlayer coupling**

**Large Spin orbit coupling**



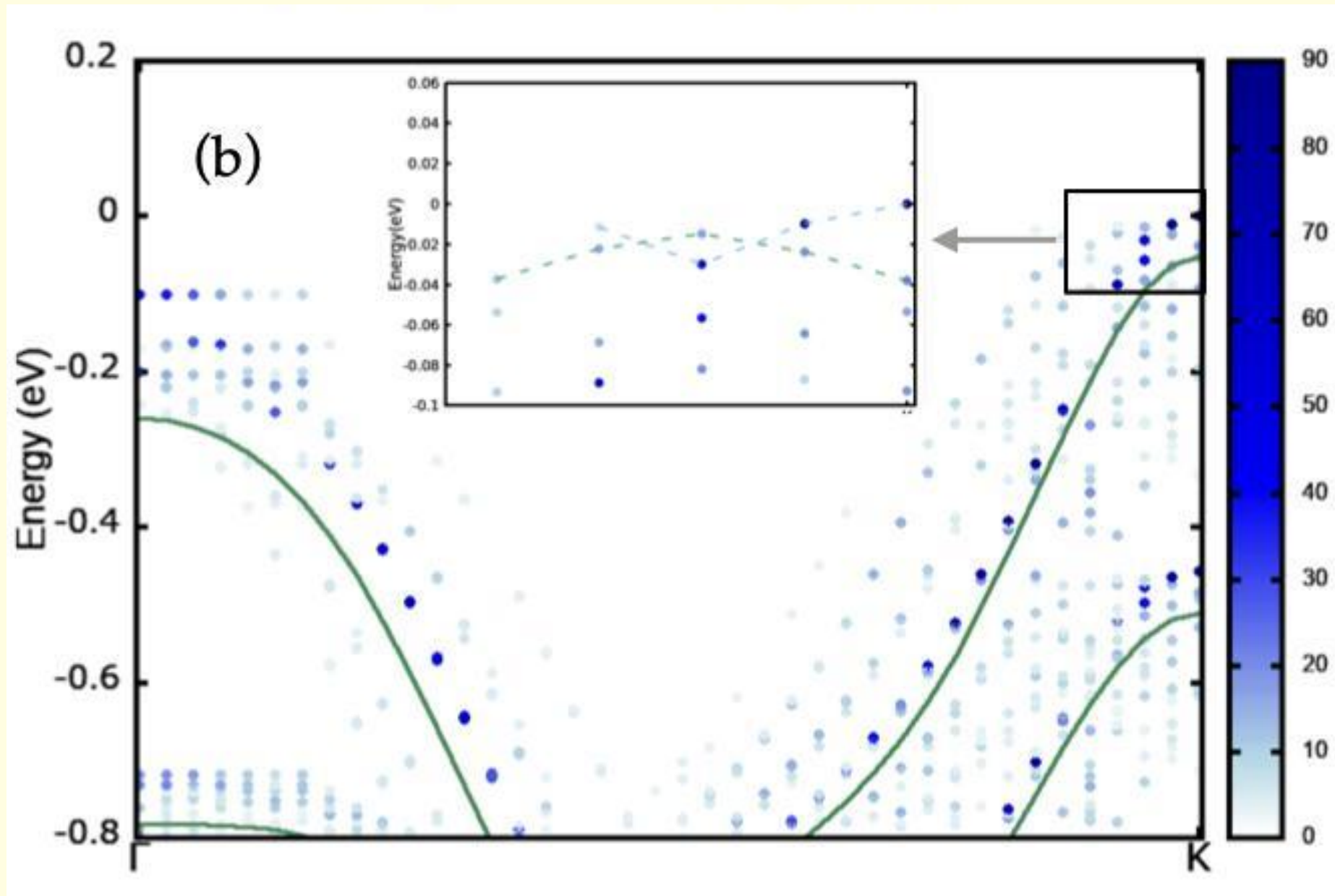
# Twisted bilayer $\text{WSe}_2$ at $3.48^\circ$



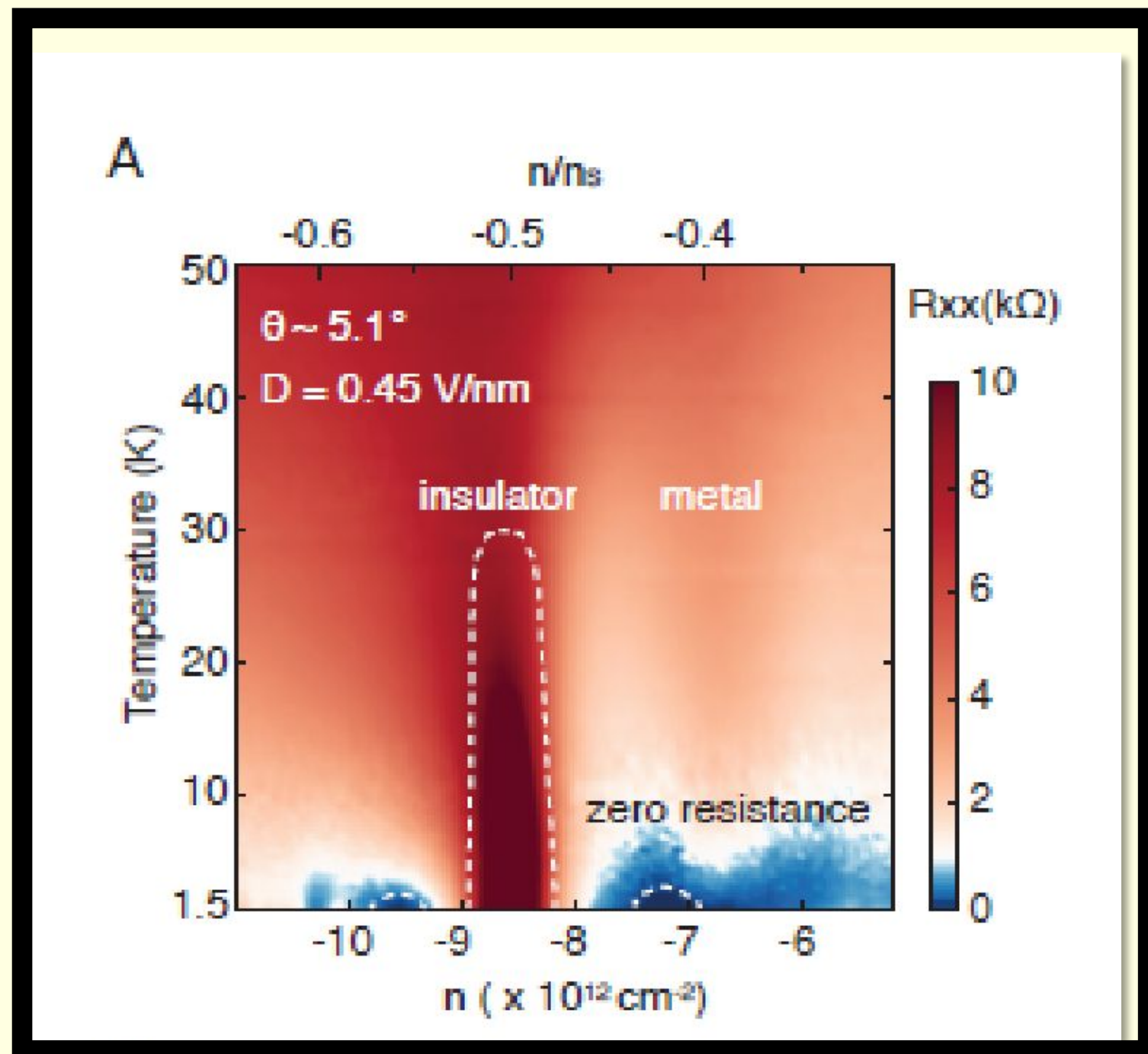
No of atoms=1626

Unit cell dimensions ~ 54.03 Å

# Twisted bilayer $\text{WSe}_2$ at $3.48^\circ$



# For twisted $\text{WSe}_2$

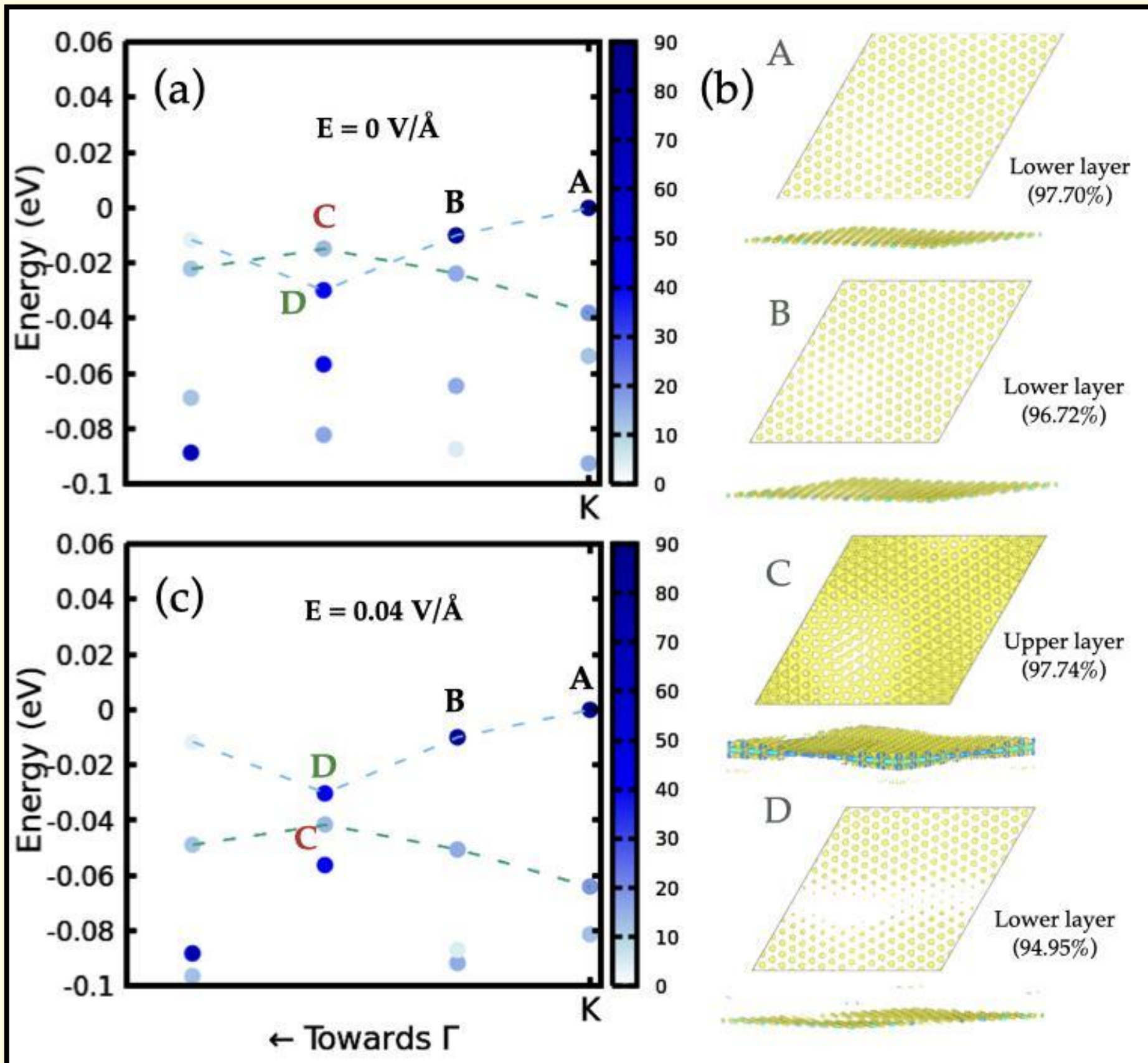


L. Wang et al., Nat.

Materials 19, 861 (2020).

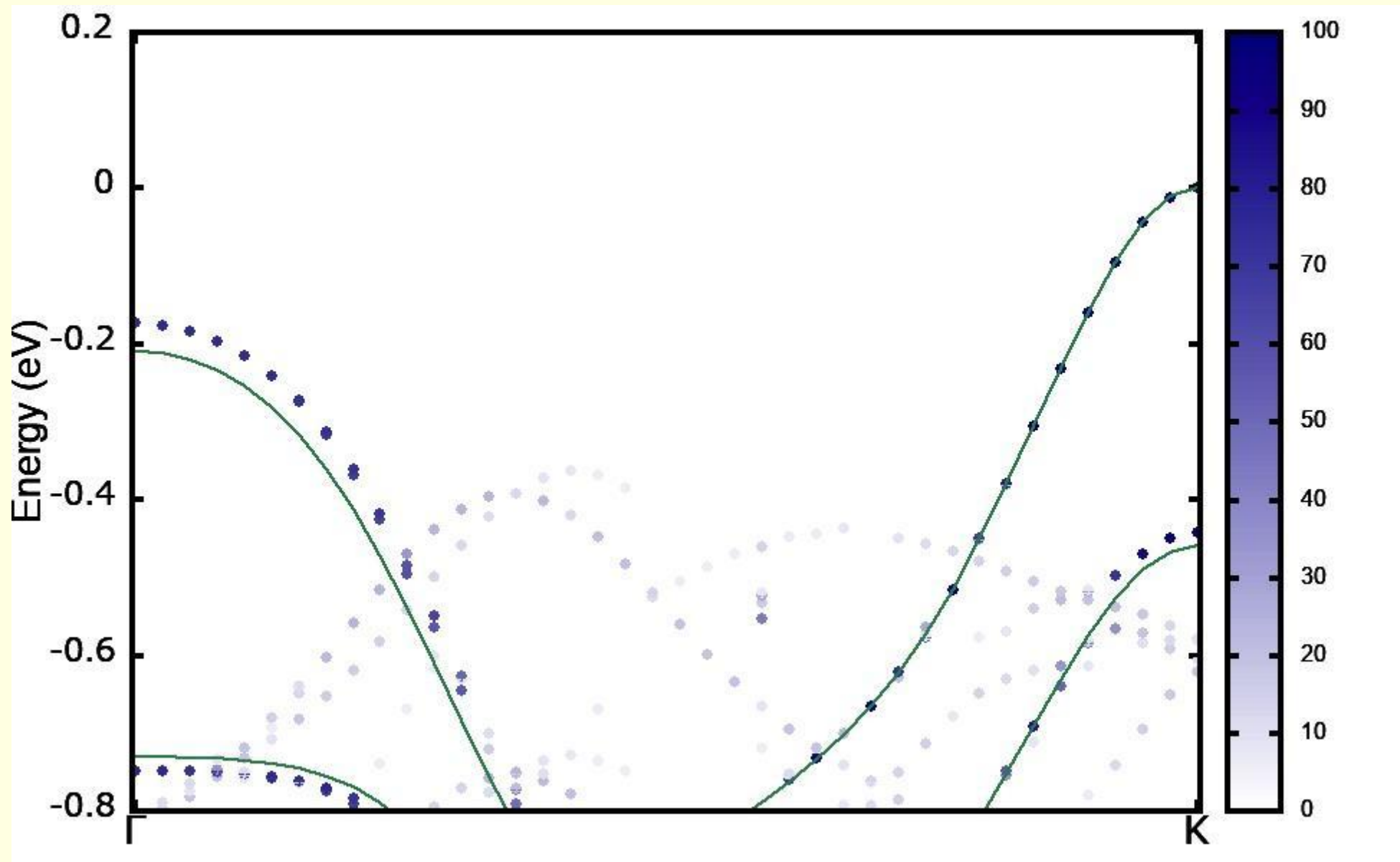


# Reconstructing the band





Considering a similar sized Moire cell :  $\text{WSe}_2$  at  $19.03^\circ$



Why do we have flat bands at K: what is the perturbation?

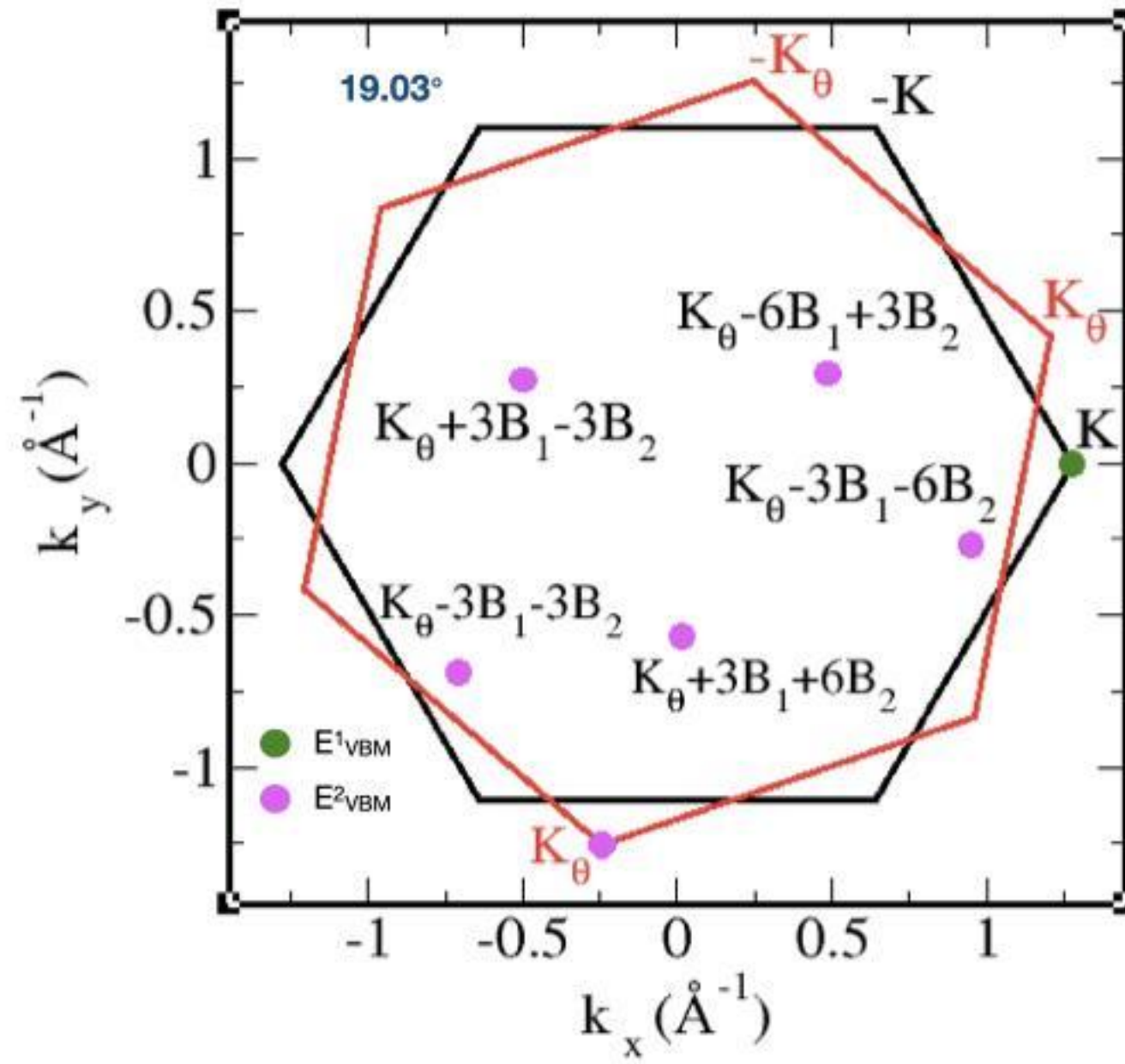
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- $3.48^\circ$  : unit cell length  $\sim 54 \text{ \AA}$
- $19.03^\circ$  : unit cell length  $\sim 52 \text{ \AA}$

**Shouldn't the Moire potentials be similar?**

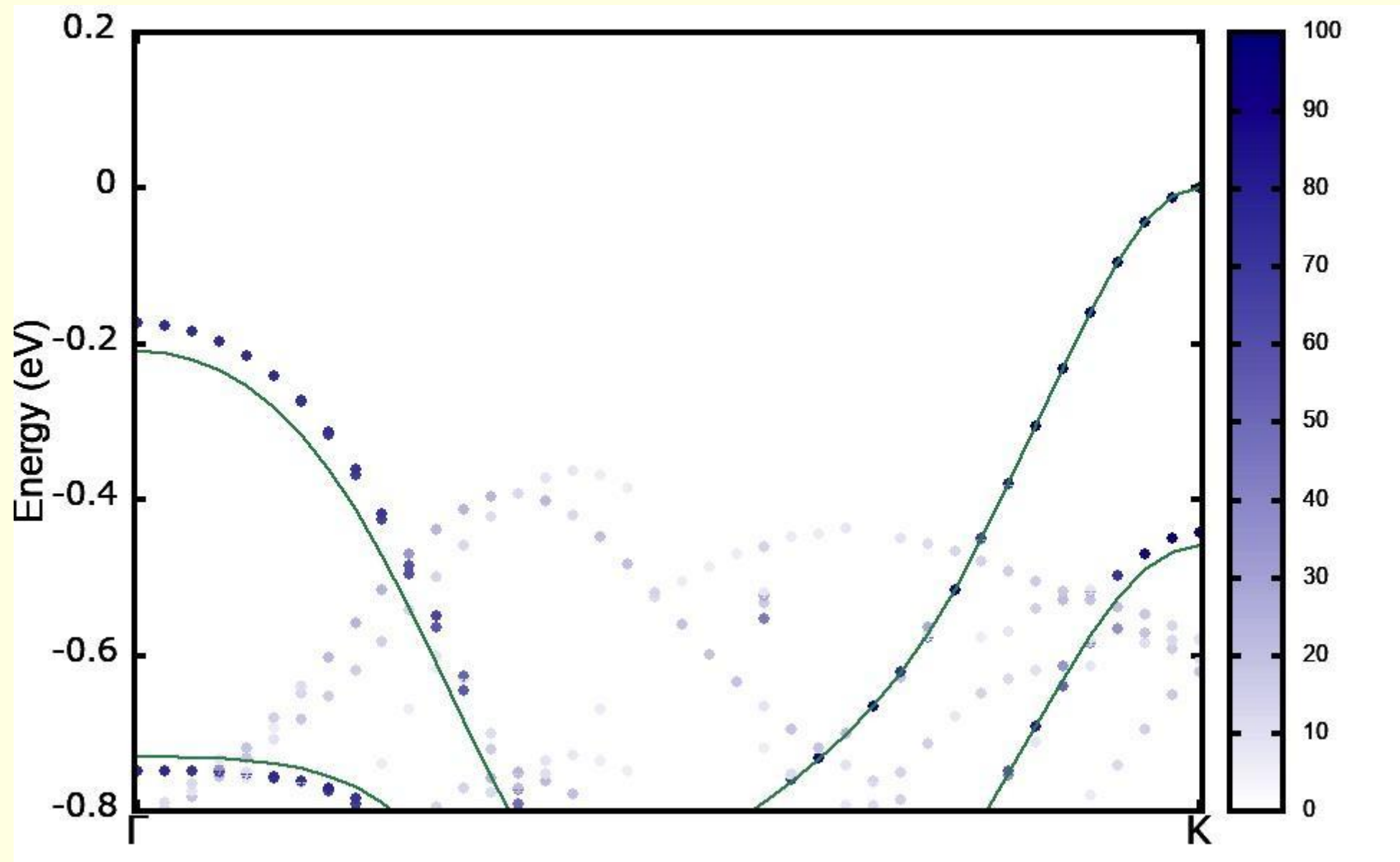
- **Fourier components of the Moire potential are associated with only the reciprocal lattice vectors of the primitive cell.**

**So we need to consider only scattering at the Brillouin zone of the primitive cell.**

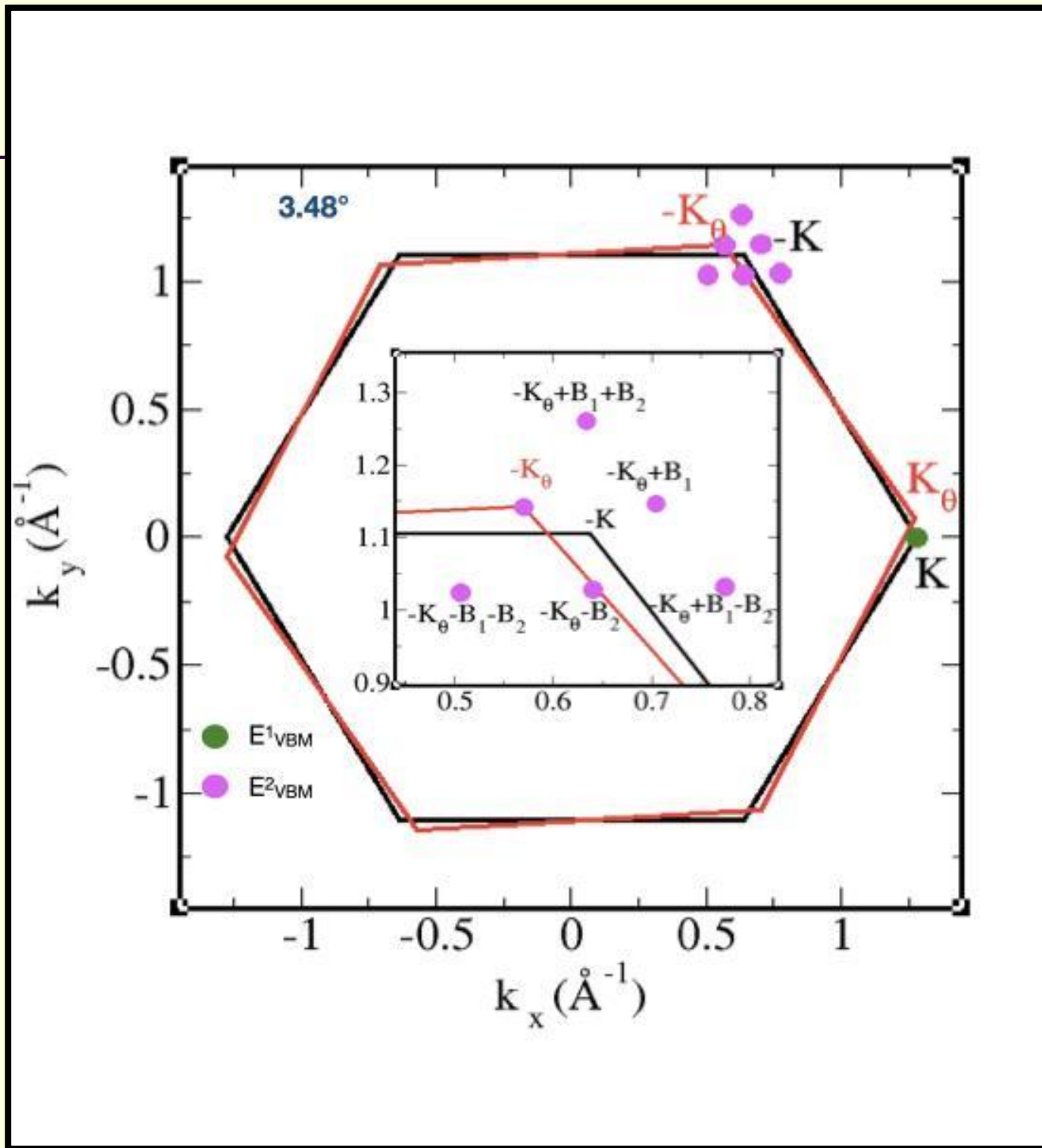


$$\mathbf{K}_{\text{sc}} + \mathbf{G} = \mathbf{k}$$

This is why the perturbation is weak at K at  $19.03^\circ$

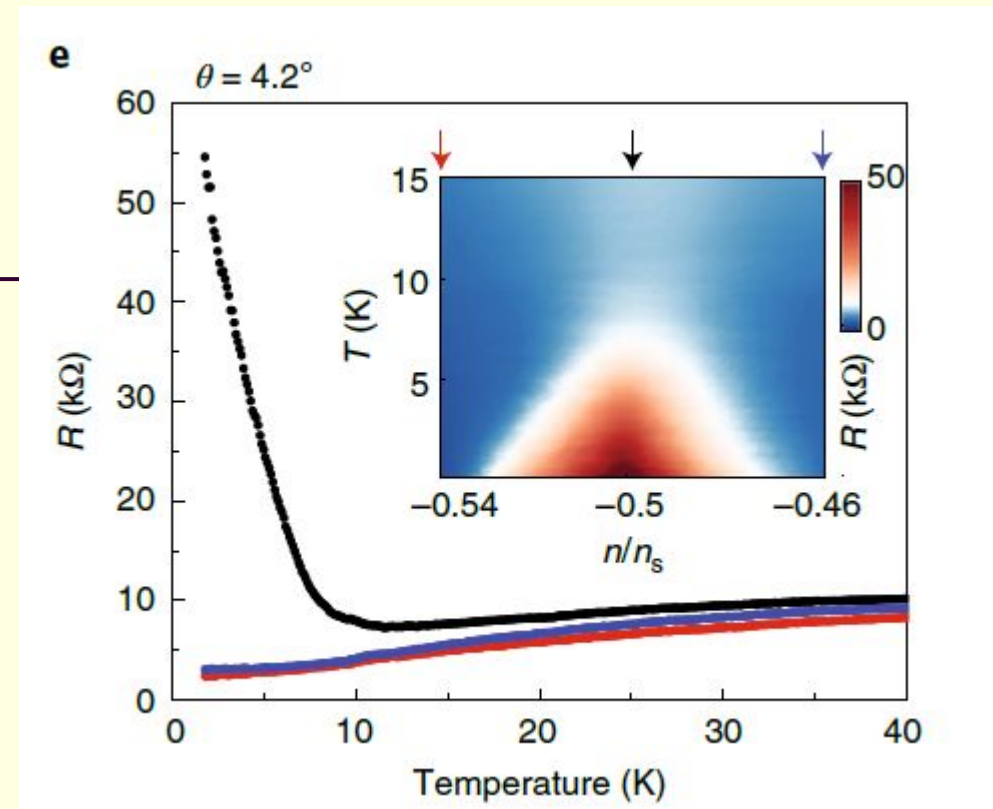
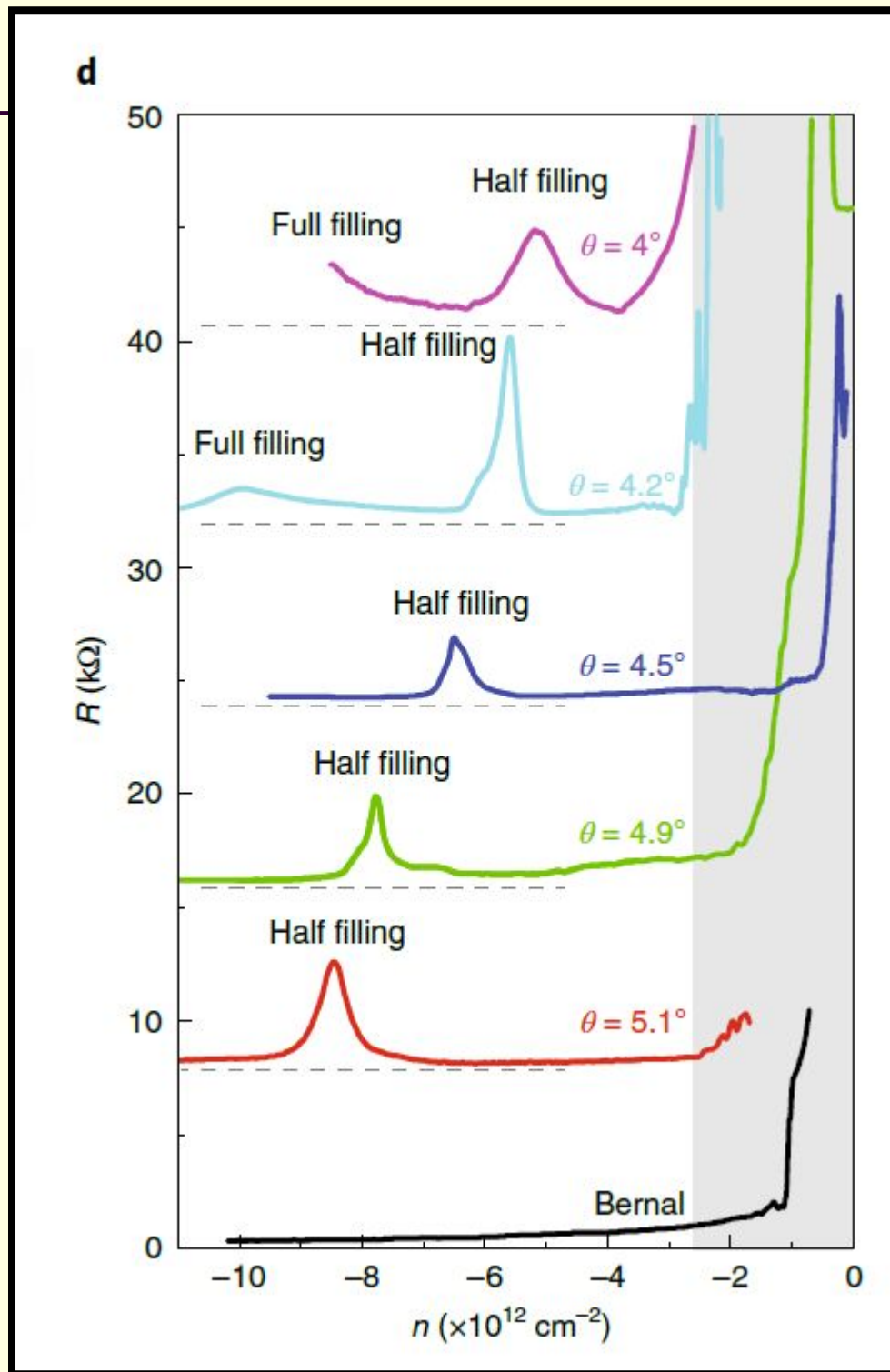






$$K_{\text{SC}} + G = k$$

For twisted  $\text{WSe}_2$



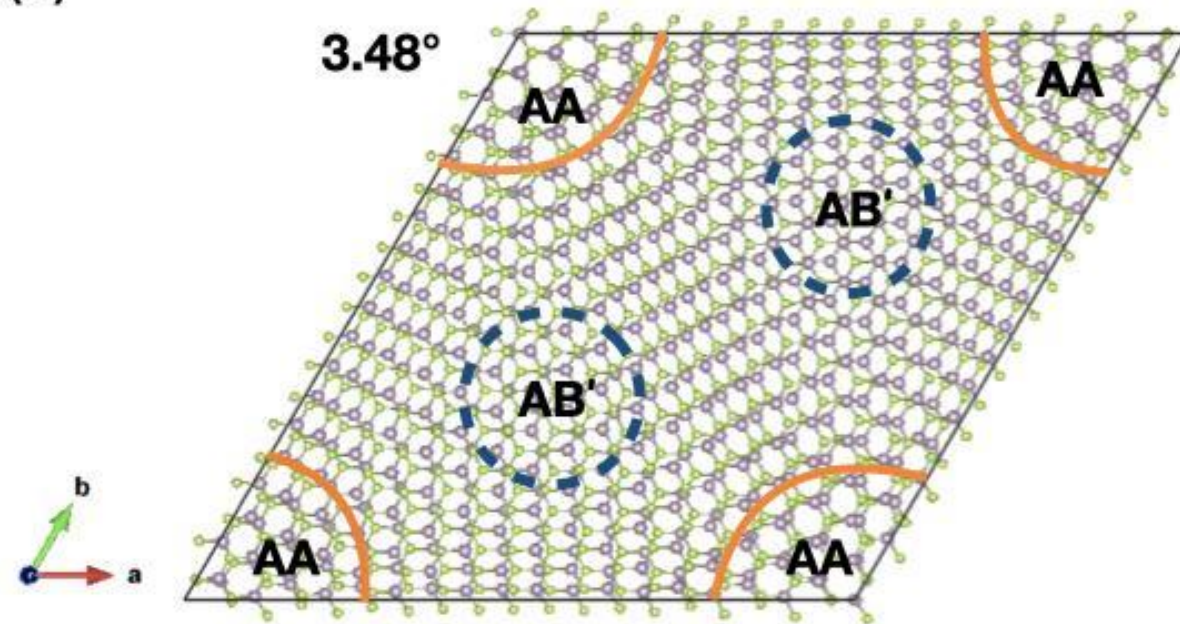
The zone boundary scattering at small angles, reduces the degeneracy of the valence band maximum to 1.

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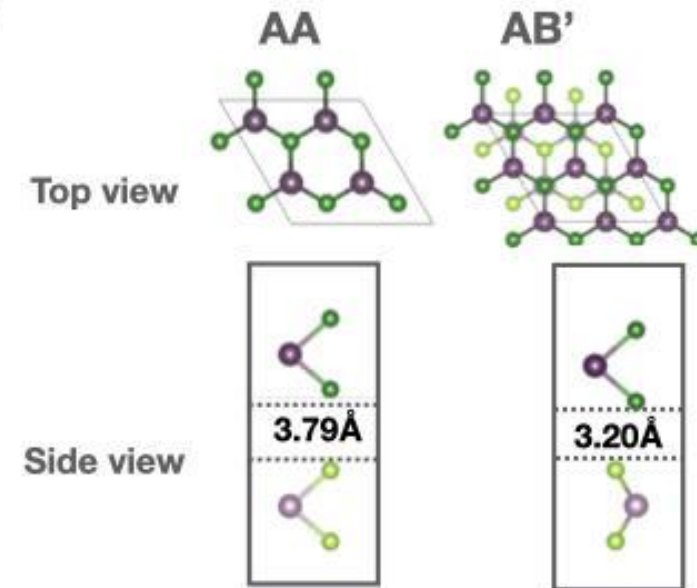
**How do we change the number of flat bands?**

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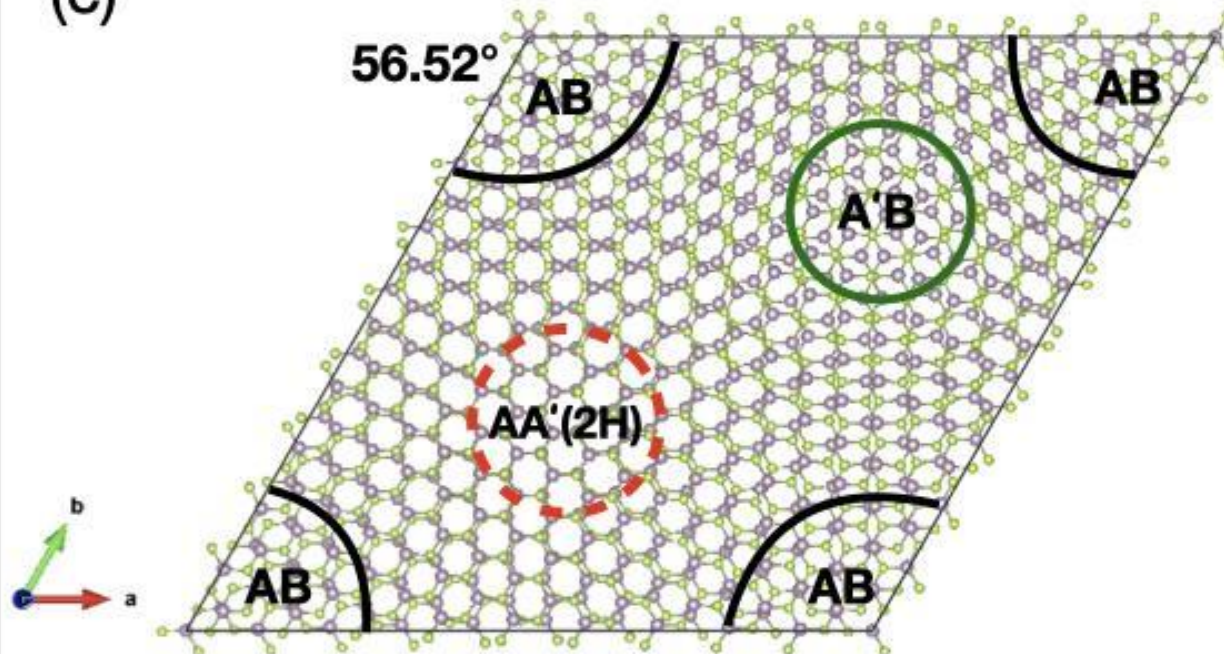
(a)



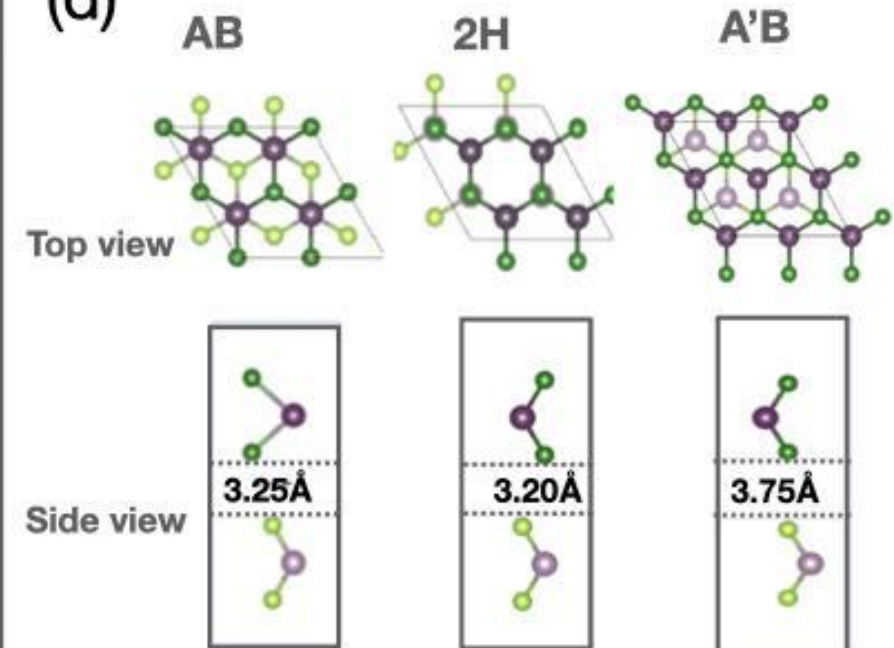
(b)



(c)

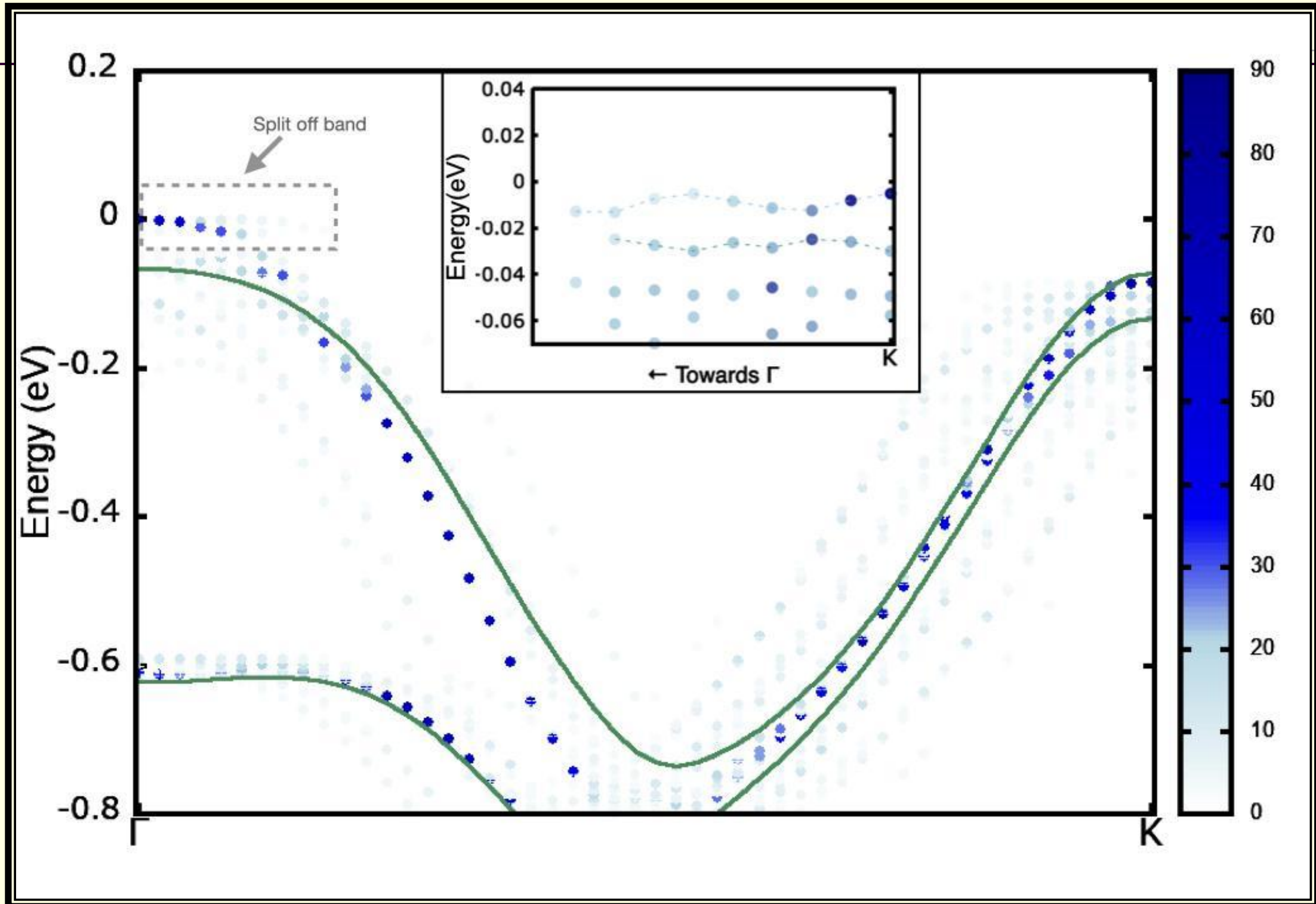


(d)

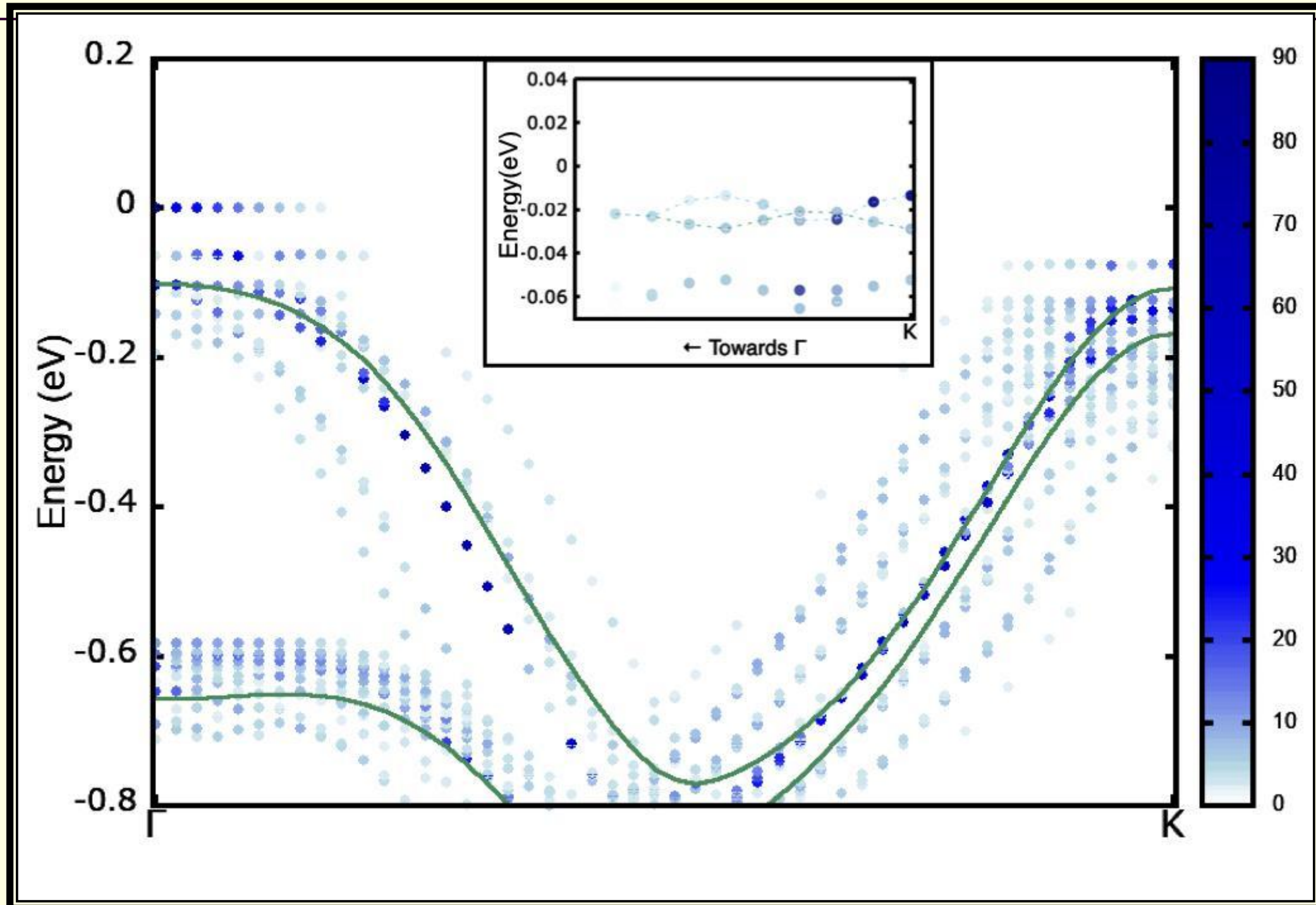


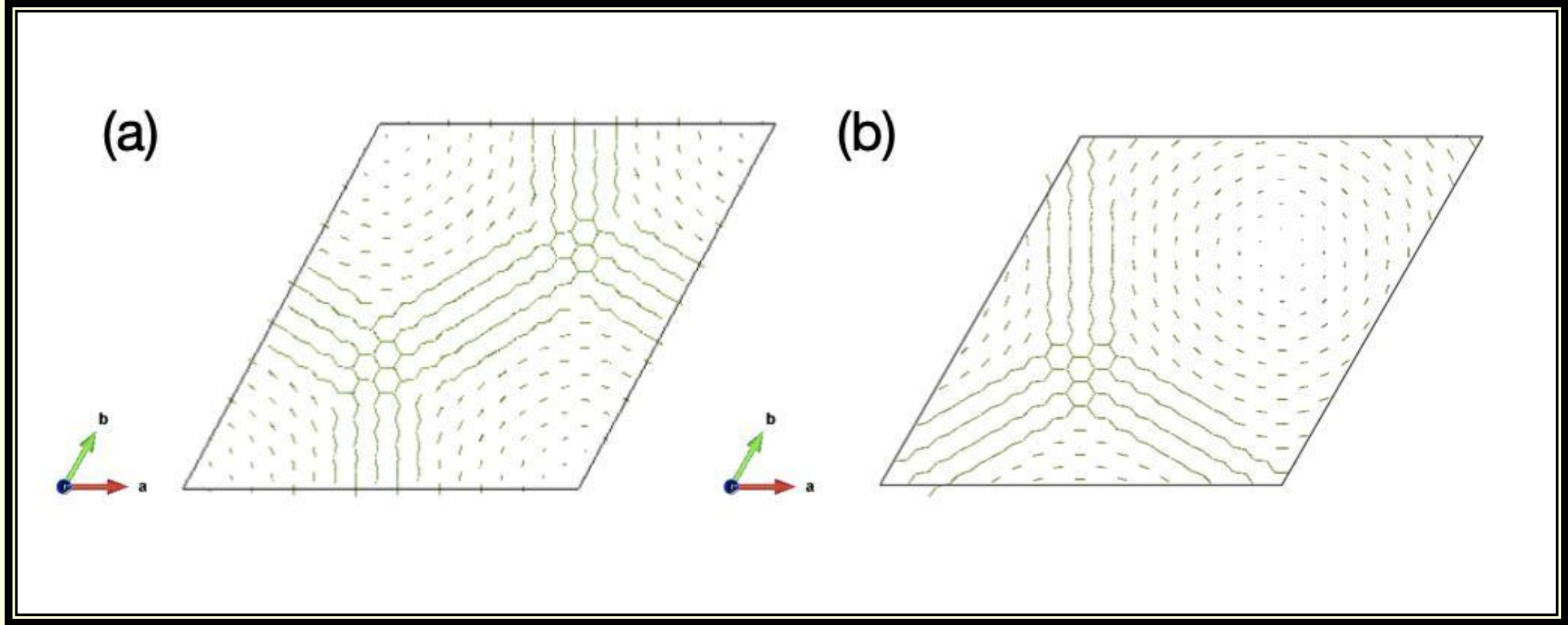


At  $3.48^\circ$

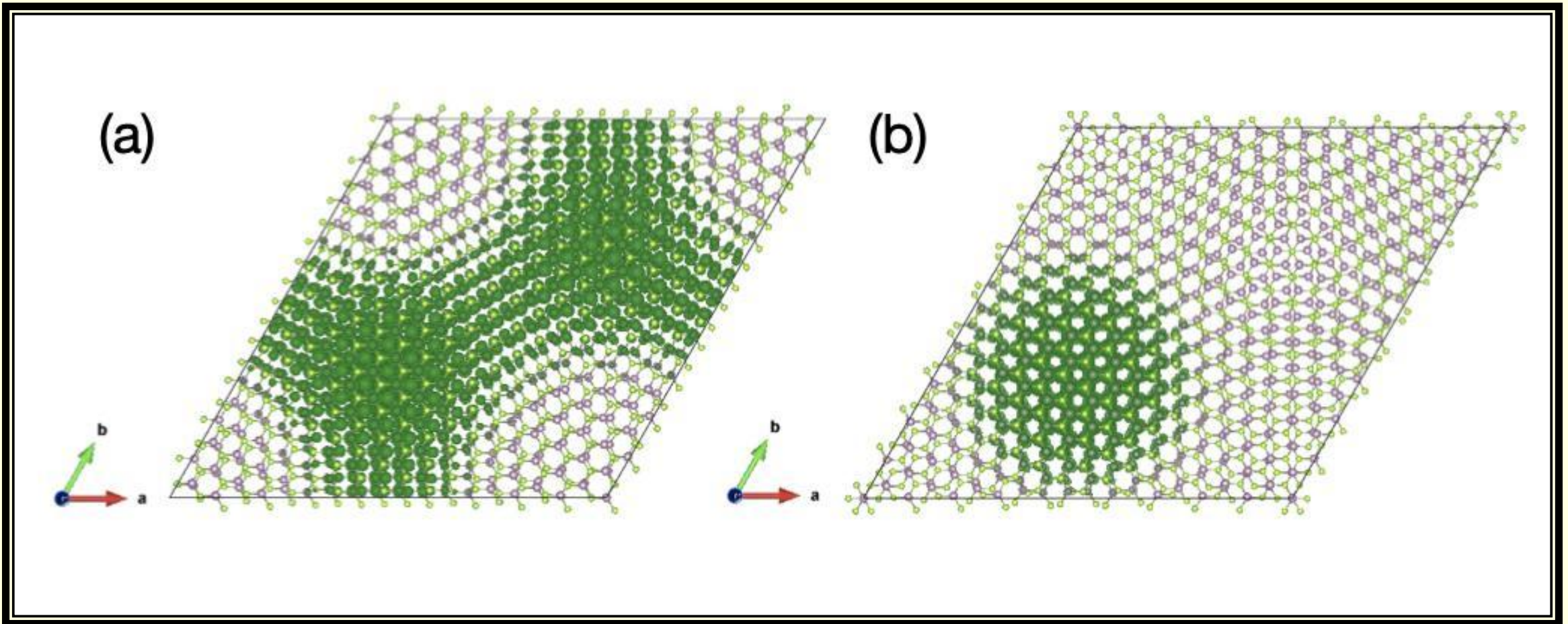


At  $56.52^\circ$

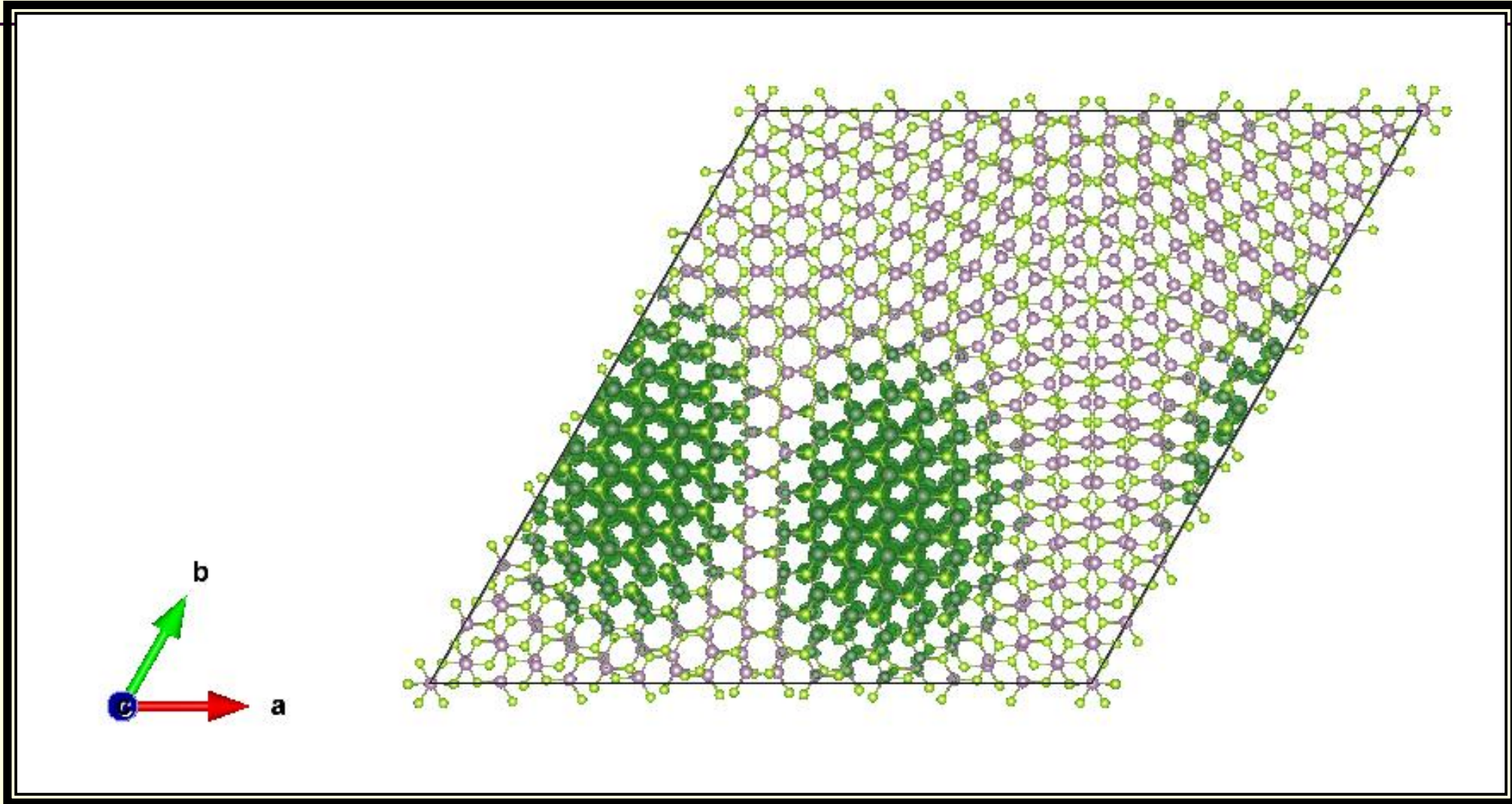












Concentrated regions of enhanced inter-layer interaction strengths lead to sub-band formation for twisted bilayers of  $\text{MoSe}_2$ .

In  $\text{WSe}_2$  we are able to explain the electric field induced MIT. The flat band formation here is traced back to the zone boundary scattering.

Sumanti Patra



Prasun Boyal



Madhurita Das  
Poonam Kumari  
Joydeep Chatterjee  
Shishir Kumar Pandey  
Ruma Das

Sumanti Patra, Poonam Kumari and PM, Phys. Rev. B (2020).

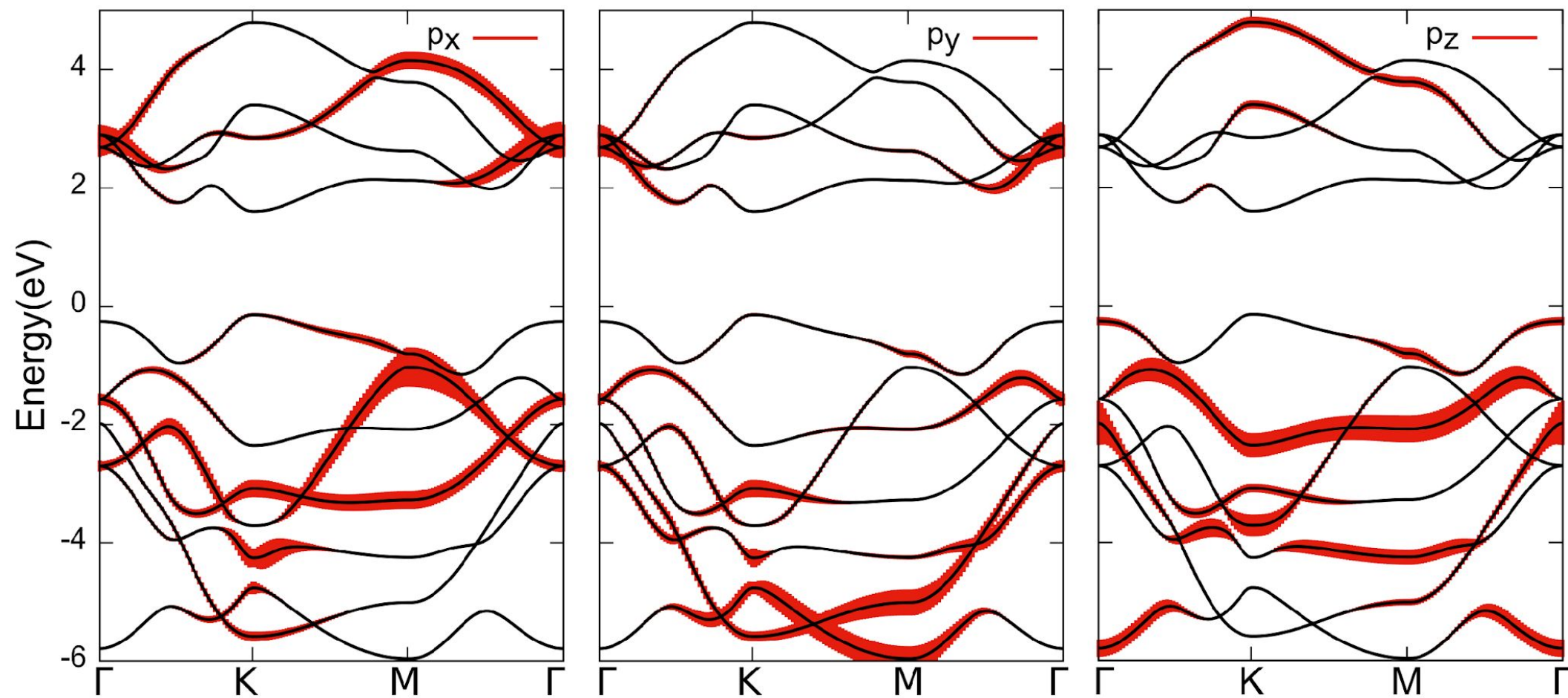
Sumanti Patra, Prasun Boyal and Priya Mahadevan, Phys. Rev. B (Lett.) **107**, L041104 (2023); Sumanti Patra, Madhurita Das and Priya Mahadevan, J. Phys. Mat. **7**, 014001 (2023).

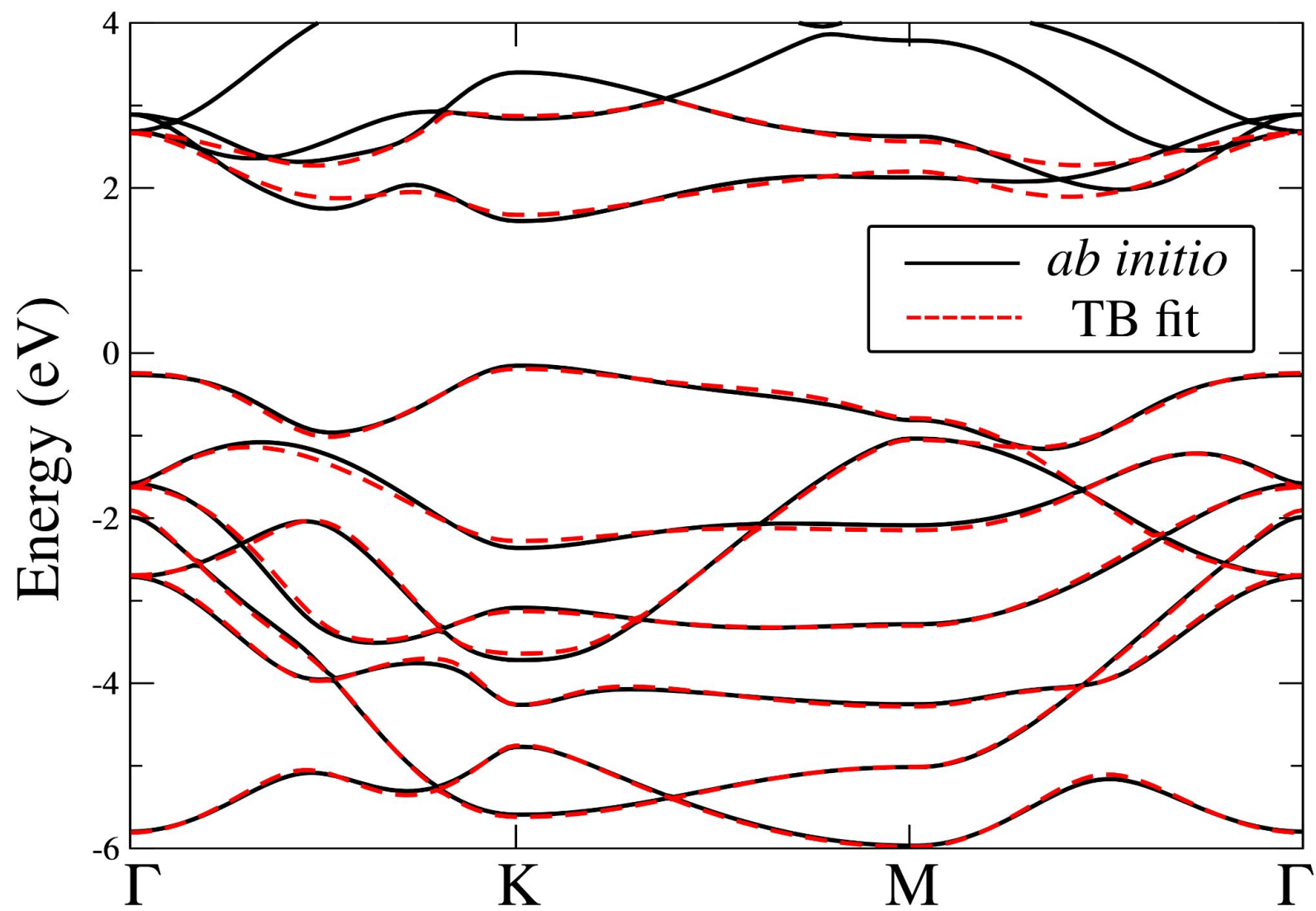
Funding acknowledged from DST Nanomission ; SERB-IRPHA.



# Where are the anion p levels?

p levels of Sulfur





TB fit with all d and p  
bands of Mo and S



Effective Hamiltonian at  $\Gamma$  point

-0.21    0.00    0.00

0.00    -0.21    0.00

0.00    0.00    -2.51

Basis :  $\{d_{xy}, d_{x^2-y^2}, d_{z^2}\}$

Effective Hamiltonian at mid-point along  $\Gamma$ -K direction

$$\begin{array}{ccc} -0.48 & 0.15-0.03i & -0.22-0.03i \\ & & i \end{array}$$

Basis :  $\{d_{xy}, d_{x^2-y^2}, d_{z^2}\}$

$$\begin{array}{ccc} 0.15+0.03i & -0.65 & -0.13+0.04i \\ & & i \end{array}$$

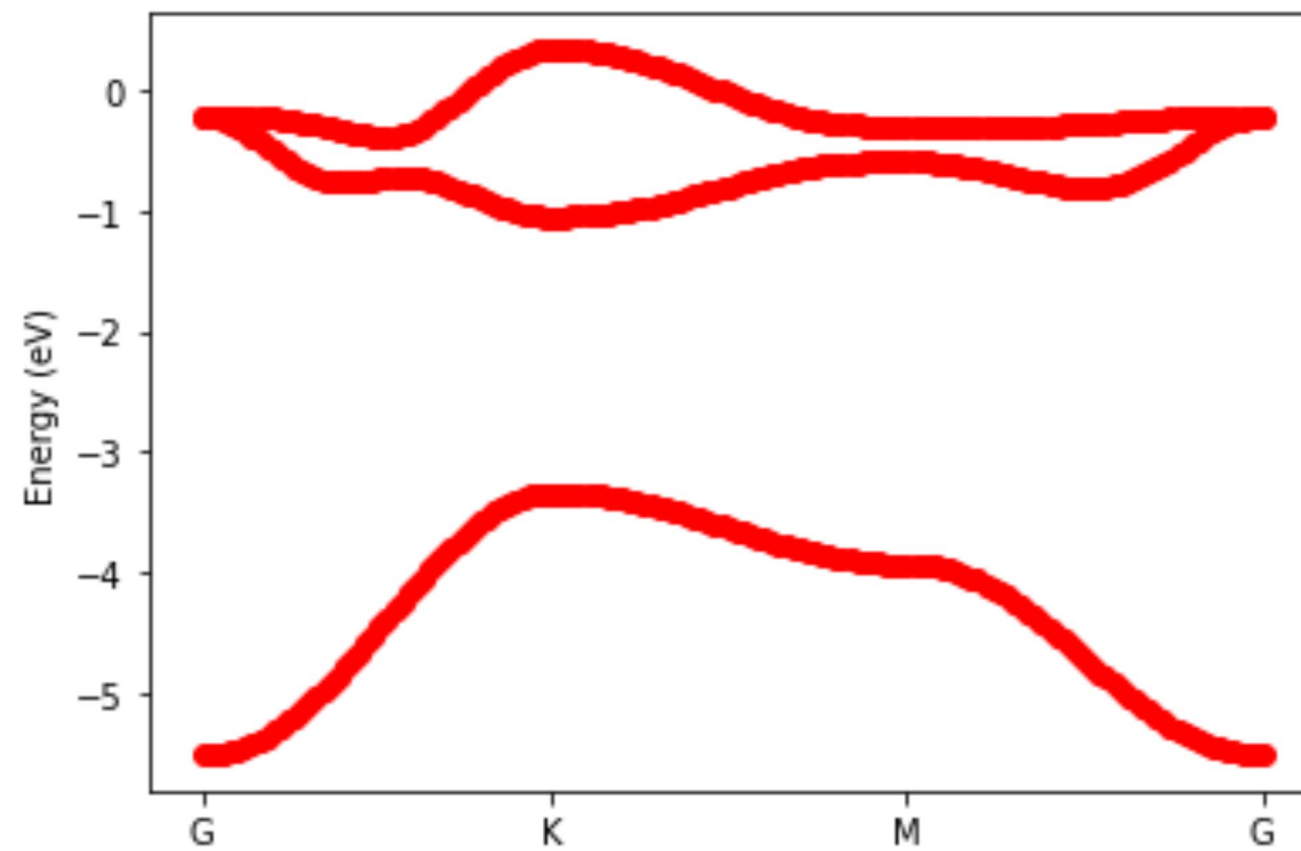
$$\begin{array}{ccc} -0.22+0.03i & 0.13-0.04i & -1.15 \\ i & & \end{array}$$

Effective Hamiltonian at K point

$$\begin{array}{ccc} -0.35 & -0.69i & 0.00 \\ 0.69i & -0.35 & 0.00 \\ 0.00 & 0.00 & -0.48 \end{array}$$

Basis :  $\{d_{xy}, d_{x^2-y^2}, d_{z^2}\}$

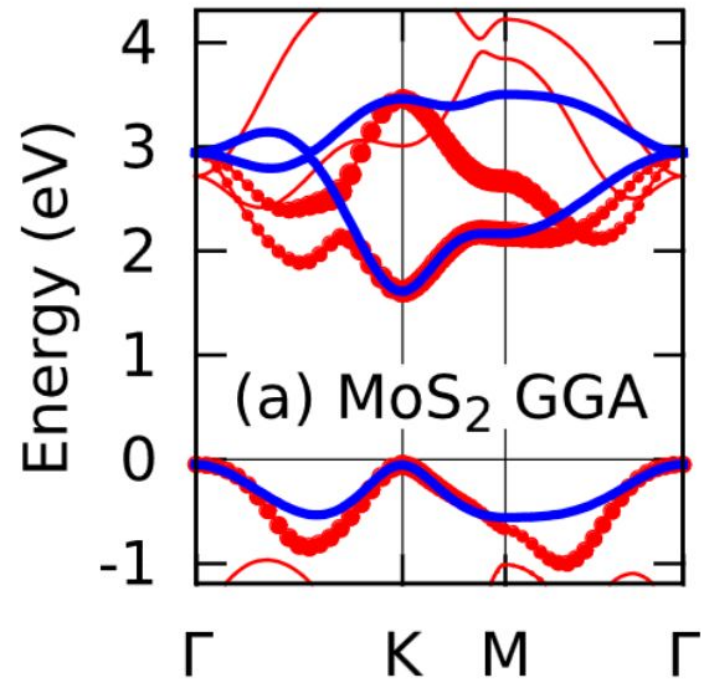
Band structure obtained from  
effective  $d$  only model (downfolded from full Hamiltonian)





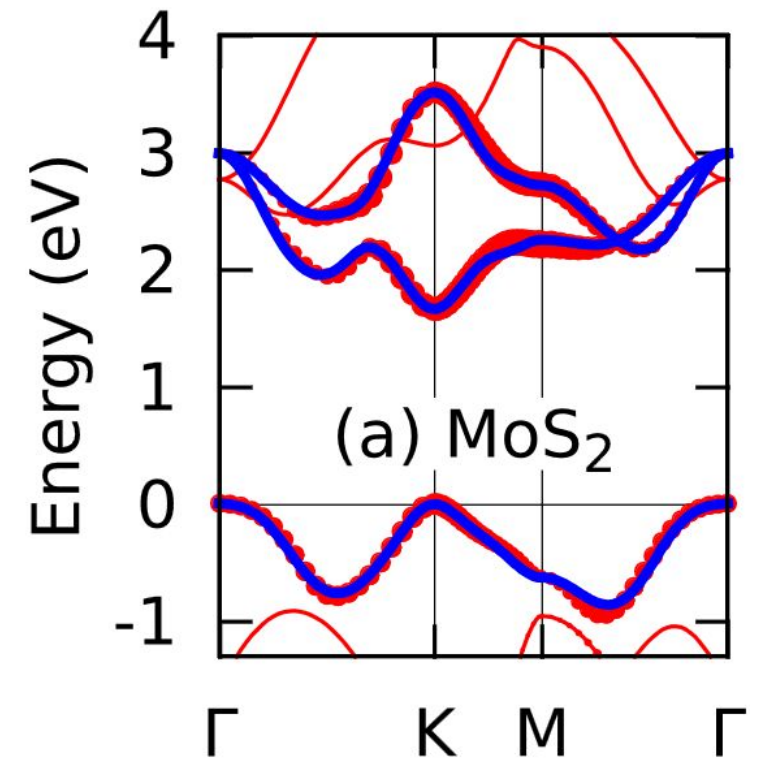
# Attempts of d-only model for MoS<sub>2</sub>

G. B. Liu et al., PRB **88**, 085433 (2013)

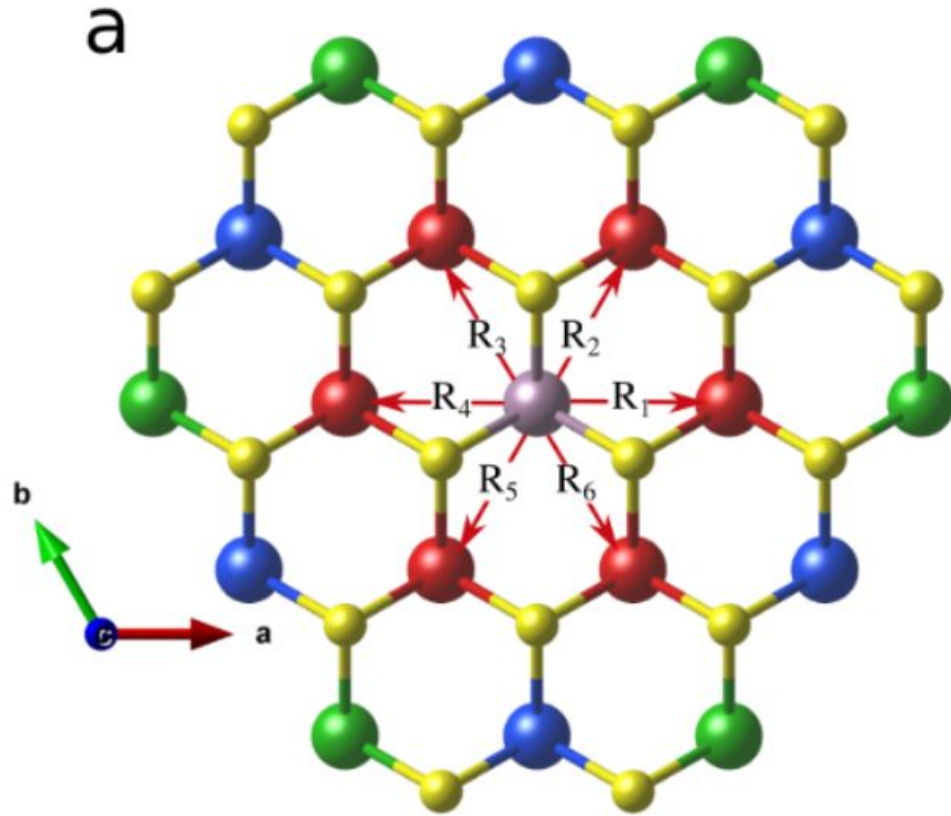


Nearest neighbor model  
(8 independent parameter)

Third neighbor model  
(17 independent parameter)



## Construction of a $d$ -only tight binding model



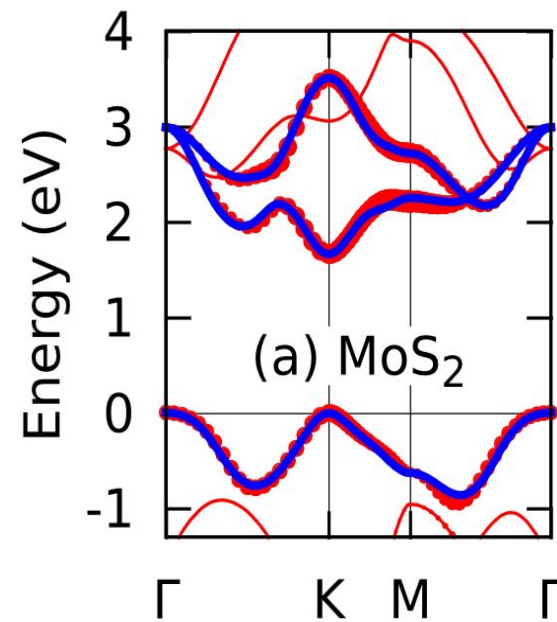
$$\{|1\rangle = |d_{xy}\rangle, |2\rangle = |d_{x^2-y^2}\rangle, |3\rangle = |d_{z^2}\rangle\}$$

Atom number	Lattice vector	Direction cosine (l,m,n)
1	$\mathbf{R}_1 = \langle a, 0, 0 \rangle$	(1, 0, 0)
2	$\mathbf{R}_2 = \langle \frac{a}{2}, \frac{\sqrt{3}a}{2}, 0 \rangle$	$(\frac{1}{2}, \frac{\sqrt{3}}{2}, 0)$
3	$\mathbf{R}_3 = \langle -\frac{a}{2}, \frac{\sqrt{3}a}{2}, 0 \rangle$	$(-\frac{1}{2}, \frac{\sqrt{3}}{2}, 0)$
4	$\mathbf{R}_4 = \langle -a, 0, 0 \rangle$	(-1, 0, 0)
5	$\mathbf{R}_5 = \langle -\frac{a}{2}, -\frac{\sqrt{3}a}{2}, 0 \rangle$	$(-\frac{1}{2}, -\frac{\sqrt{3}}{2}, 0)$
6	$\mathbf{R}_6 = \langle \frac{a}{2}, -\frac{\sqrt{3}a}{2}, 0 \rangle$	$(\frac{1}{2}, -\frac{\sqrt{3}}{2}, 0)$

$$H_{ij}(\mathbf{k}) = \sum_{\mathbf{R}} e^{i\mathbf{k}\cdot\mathbf{R}} E_{ij}(\mathbf{R})$$

Where,  $E_{ij}(\mathbf{R}) = \langle i(\mathbf{r}) | \hat{H} | j(\mathbf{r} - \mathbf{R}) \rangle$

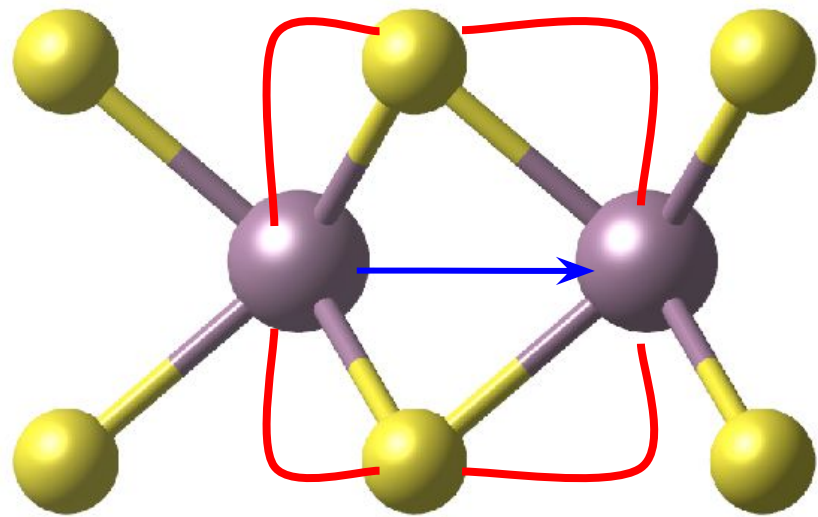
The model fits the bands at the cost of physical meaning!!



G. B. Liu et al., PRB **88**, 085433 (2013)

SK parameter	1 <sup>st</sup> neighbor	2 <sup>nd</sup> neighbor	3 <sup>rd</sup> neighbor
$V_{dd\sigma}$	$1.680 \pm 0.16$	$-0.159 \pm 0.03$	$-0.290 \pm 0.01$
$V_{dd\pi}$	$0.085 \pm 0.16$	$-0.040 \pm 0.03$	$0.266 \pm 0.01$
$V_{dd\delta}$	$-1.310 \pm 0.16$	$0.190 \pm 0.03$	$0.147 \pm 0.01$

Another hopping pathway provided by the S-p states



Two Hopping pathways possible  
between d states of adjacent Mo atoms!



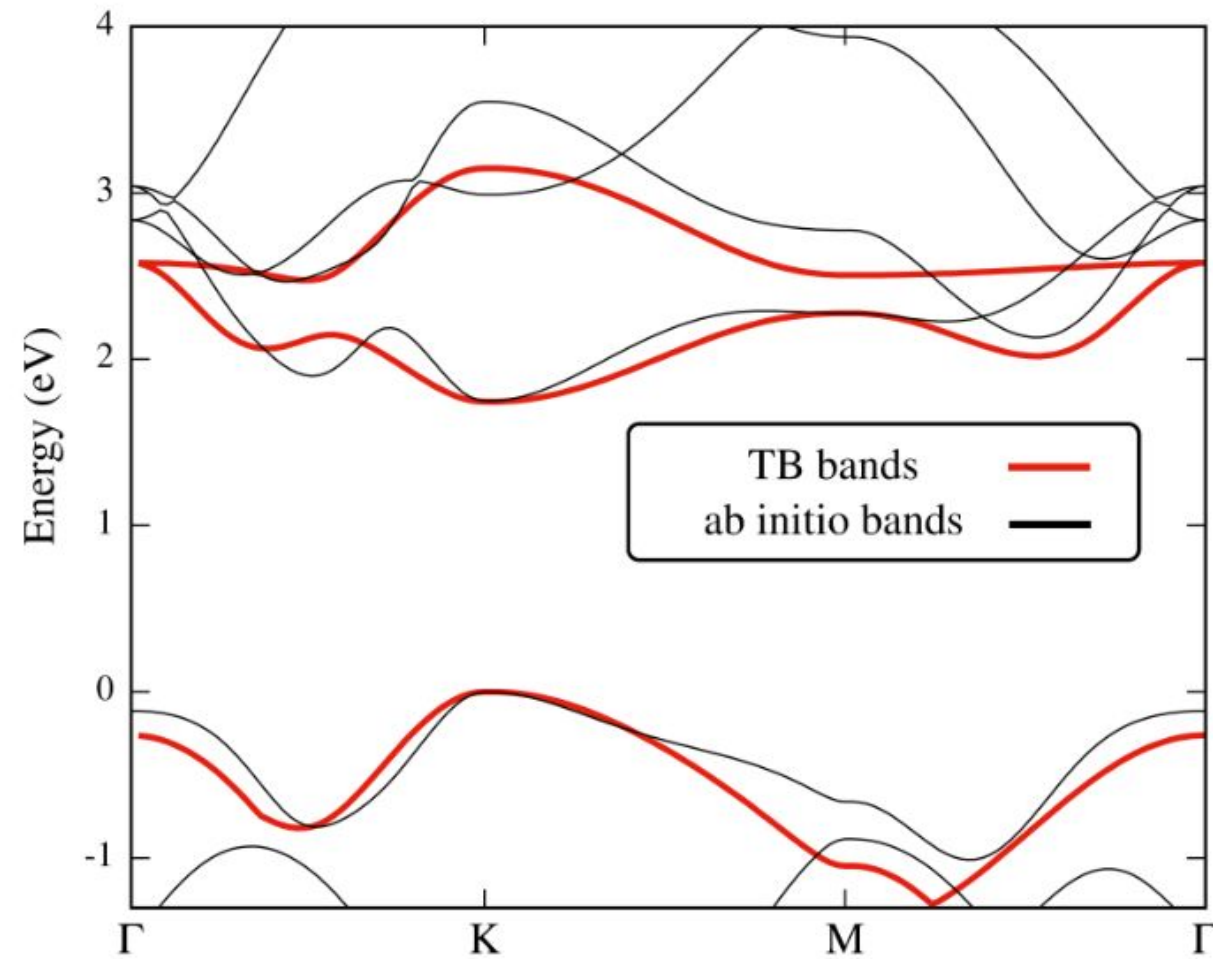
## Including in plane p orbitals in the tight binding model

- A 7-band model with in plane  $p$  orbitals
- Indirect hopping pathways between d electrons via S-p states are also allowed.

Basis:  $\{d_{xy}, d_{x^2-y^2}, d_{z^2}, p_x^t, p_y^t, p_x^b, p_y^b\}$

$$\mathcal{H}_{7\text{-band}} = \begin{pmatrix} h_{dd} & h_{dp} \\ h_{dp}^* & h_{pp} \end{pmatrix}$$

## Tight binding fit within the 7-band model



$\epsilon_1$	$\epsilon_2$	$\epsilon_3$	$V_{dd\sigma}$	$V_{dd\pi}$	$V_{dd\delta}$	$V_{dp\sigma}$	$V_{dp\pi}$	$V_{pp\sigma}$	$V_{pp\pi}$
-0.84	-4.44	-4.72	-0.04	0.22	-0.19	0.01	-0.58	0.86	-0.03

## Effective d-d Hamiltonian

$$\mathcal{H}_{7\text{-band}} = \begin{pmatrix} h_{dd} & h_{dp} \\ h_{dp}^* & h_{pp} \end{pmatrix}$$

## Effective Downfolded Hamiltonian

$$\mathcal{H}_{eff} = \mathcal{H}_A + \mathcal{V}(\mathbb{I} - \epsilon\mathcal{H}_B)\mathcal{V}^\dagger$$

## The Effective Hamiltonian

At  $\Gamma$

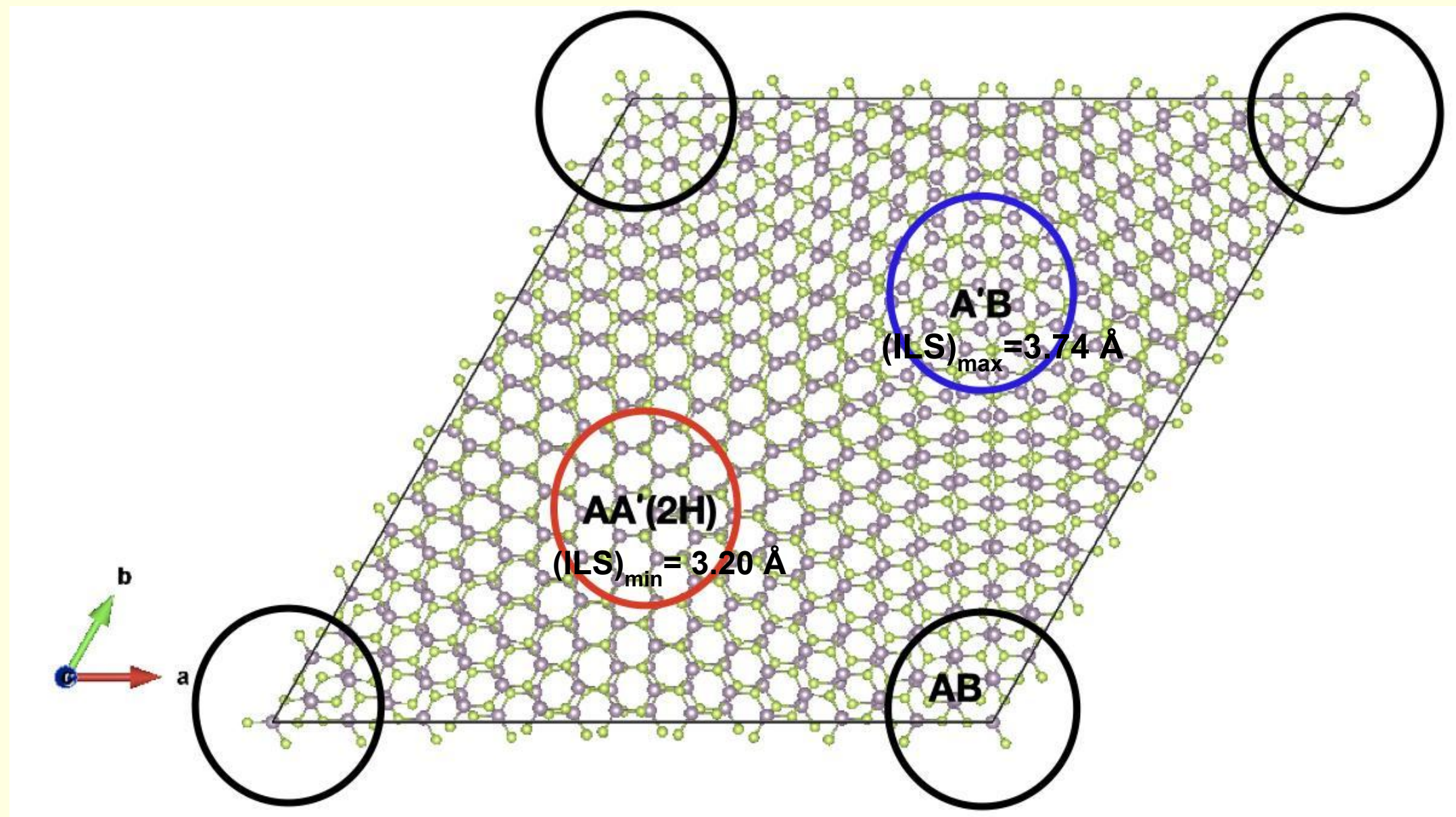
$$\begin{pmatrix} -0.4 & 0.00 & 0.00 \\ 0.00 & -0.4 & 0.00 \\ 0.00 & 0.00 & -5.51 \end{pmatrix} \xrightarrow[\substack{\text{Downfolding} \\ p \text{ block onto } d \text{ block}}]{\text{Downfolding}} \begin{pmatrix} -0.21 & 0.00 & 0.00 \\ 0.00 & -0.21 & 0.00 \\ 0.00 & 0.00 & -5.51 \end{pmatrix}$$

At K

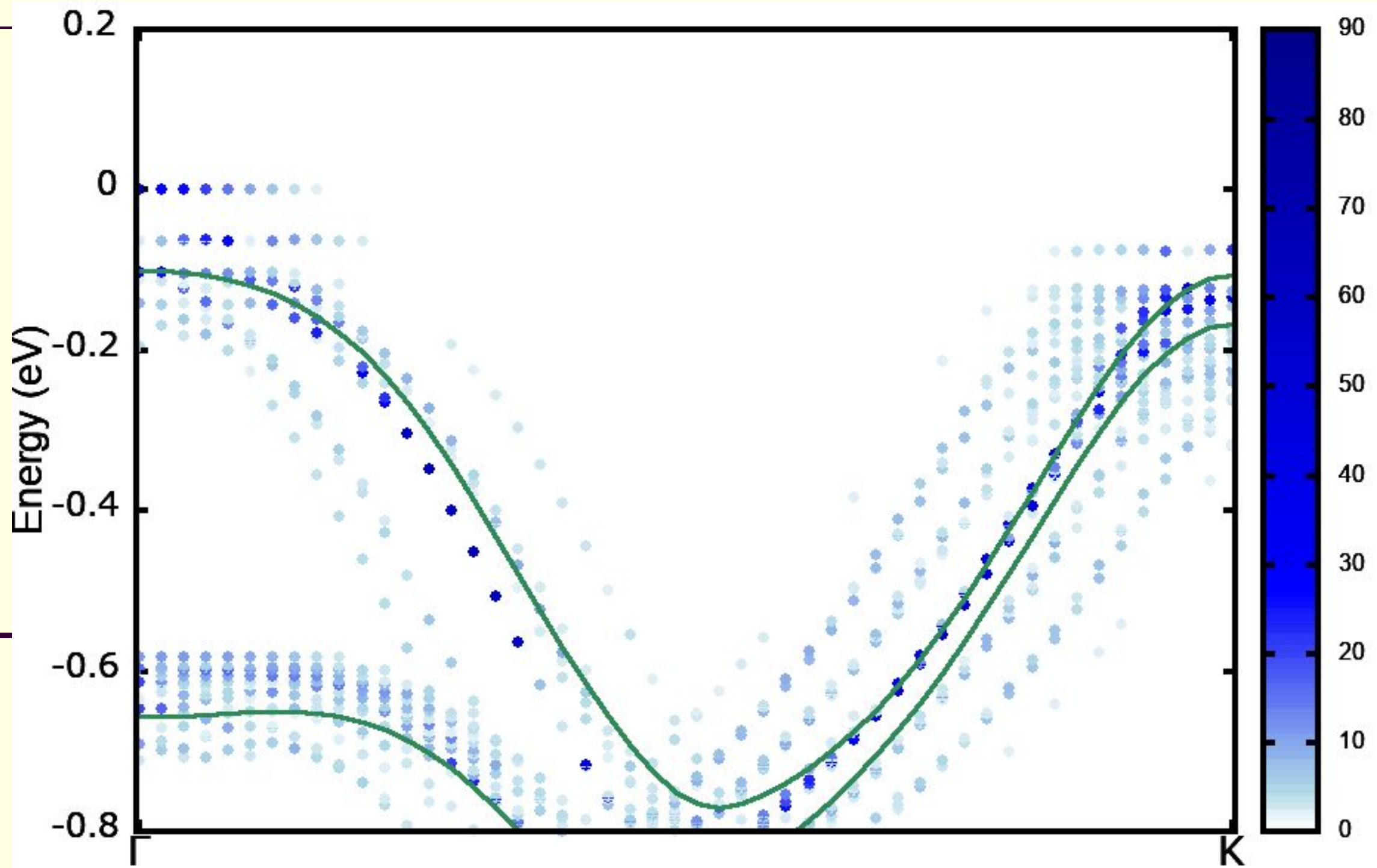
$$\begin{pmatrix} -1.05 & 0.00 & 0.00 \\ 0.00 & -1.05 & 0.00 \\ 0.00 & 0.00 & -3.9 \end{pmatrix} \xrightarrow[\substack{\text{Downfolding} \\ p \text{ block onto } d \text{ block}}]{\text{Downfolding}} \begin{pmatrix} -0.4 & -0.69i & 0.00 \\ 0.69i & -0.4 & 0.00 \\ 0.00 & 0.00 & -0.5 \end{pmatrix}$$



# MoSe<sub>2</sub> at a twist angle of 56.52°

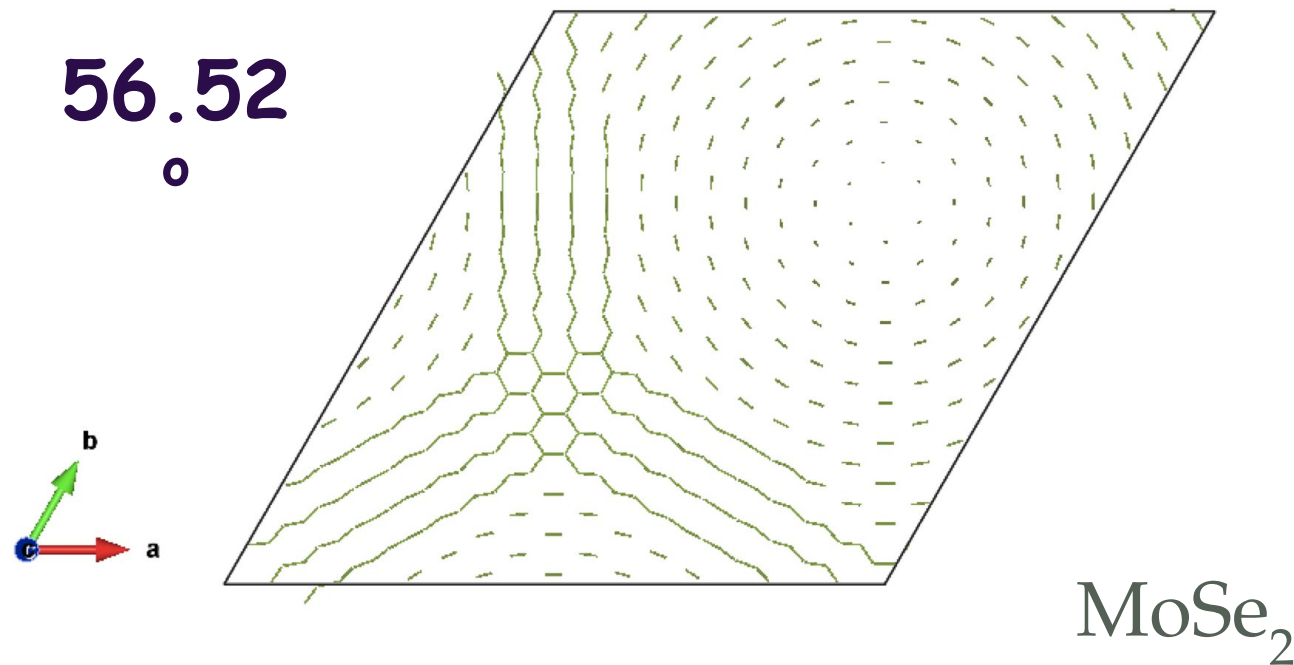


# Unfolded band structure (along the primitive cell Gamma to K direction) for twist angle $56.52^\circ$

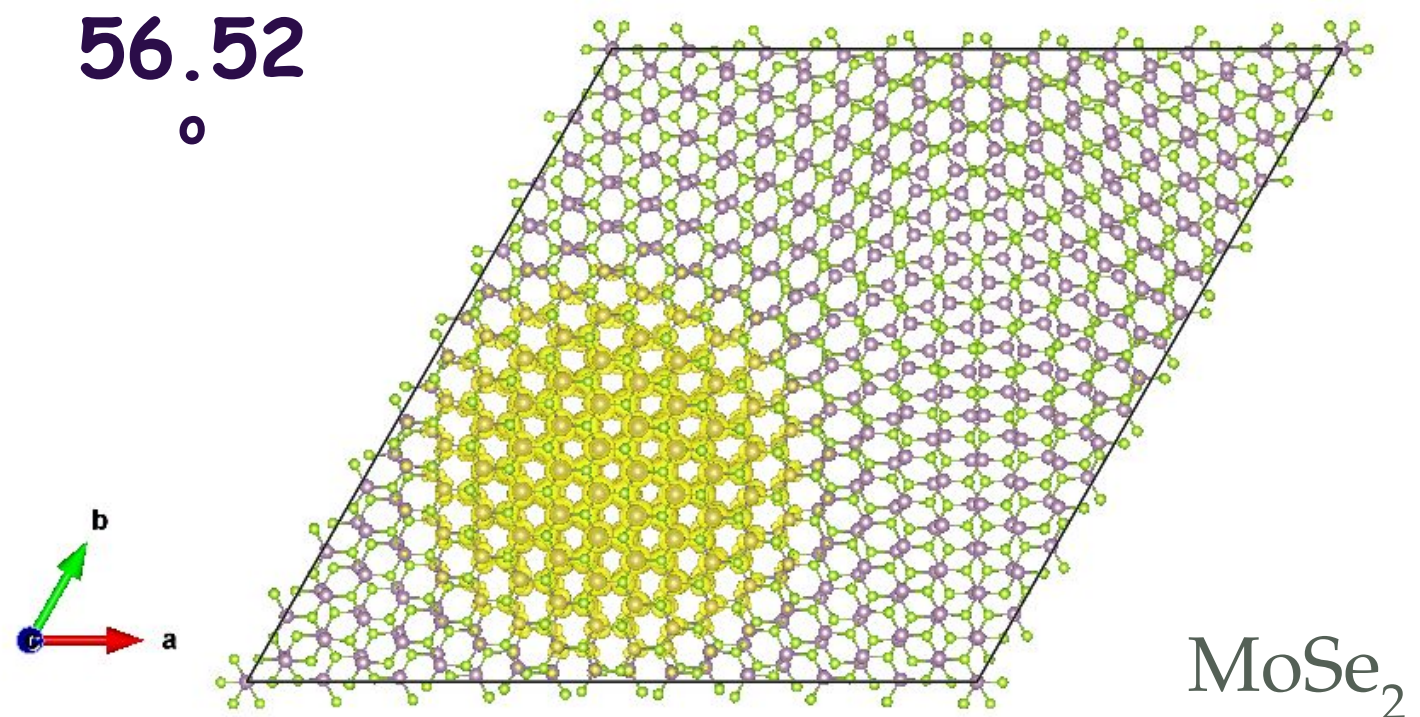




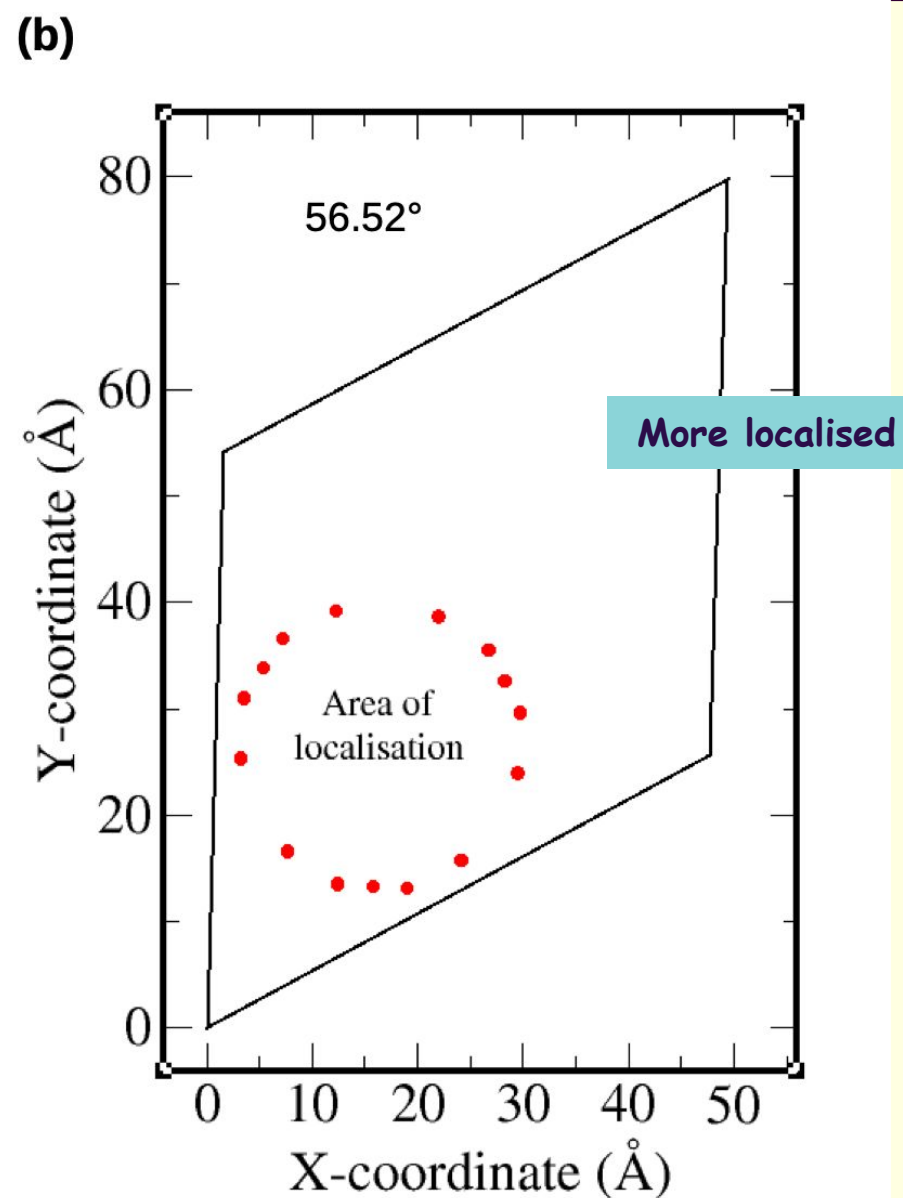
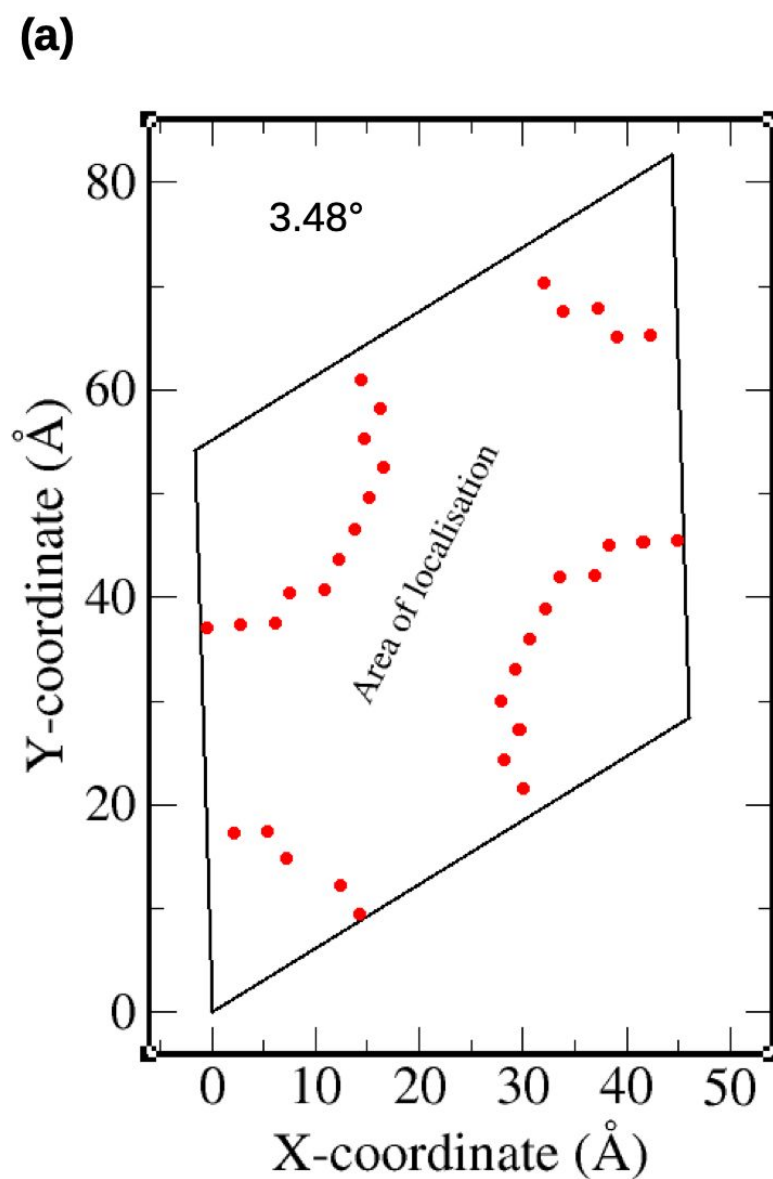
Shortest set of Se-Se distances < 3.8 Å



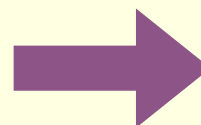
Charge density of the highest occupied band at  
Gamma



The area of charge density localisation of the split off band up to where the integrated charge density over a sphere of radius 1.262 Å (half the Mo-Se bond length) around each Mo atom reaches 10% of its maximum value.



Stronger localisation

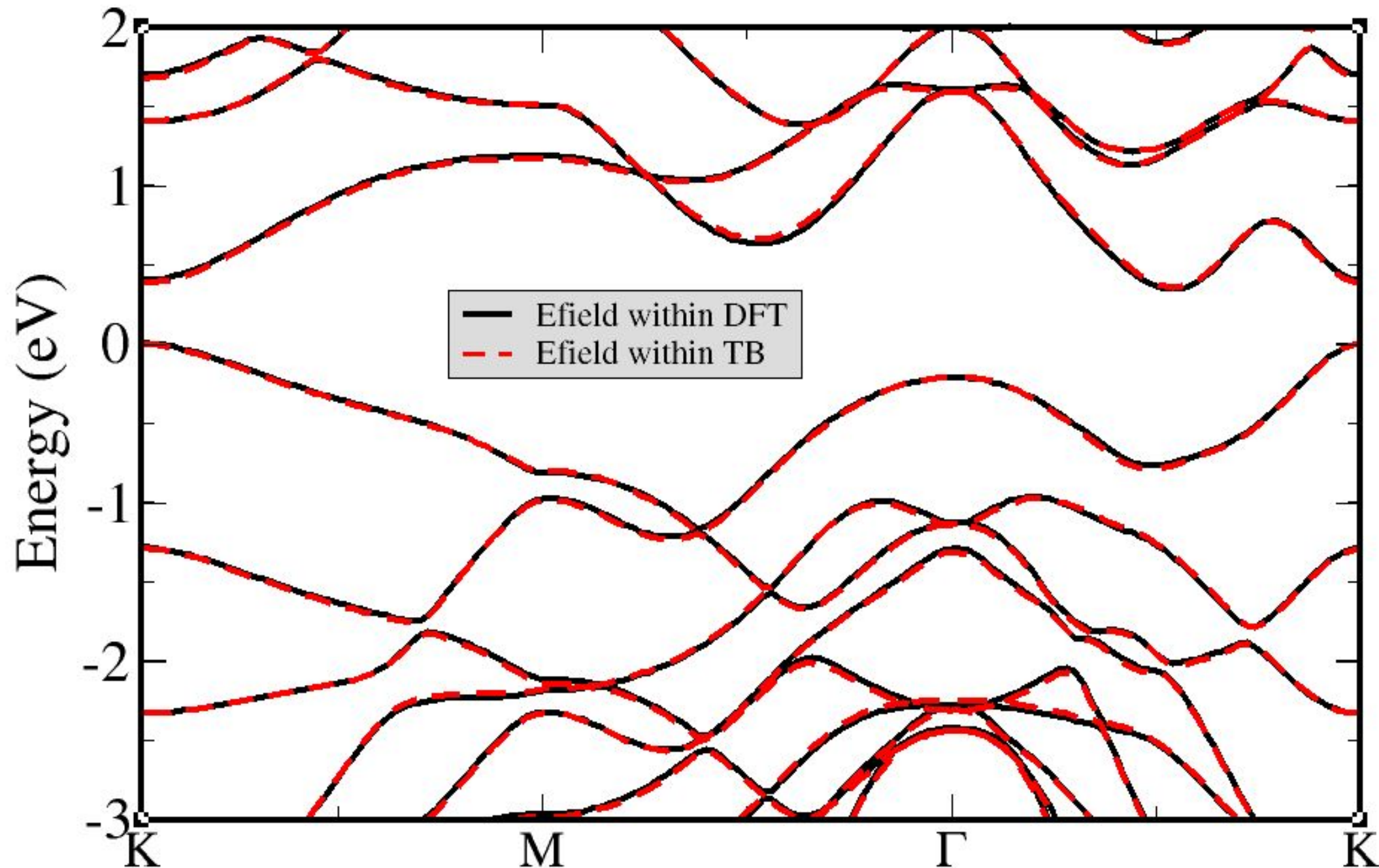


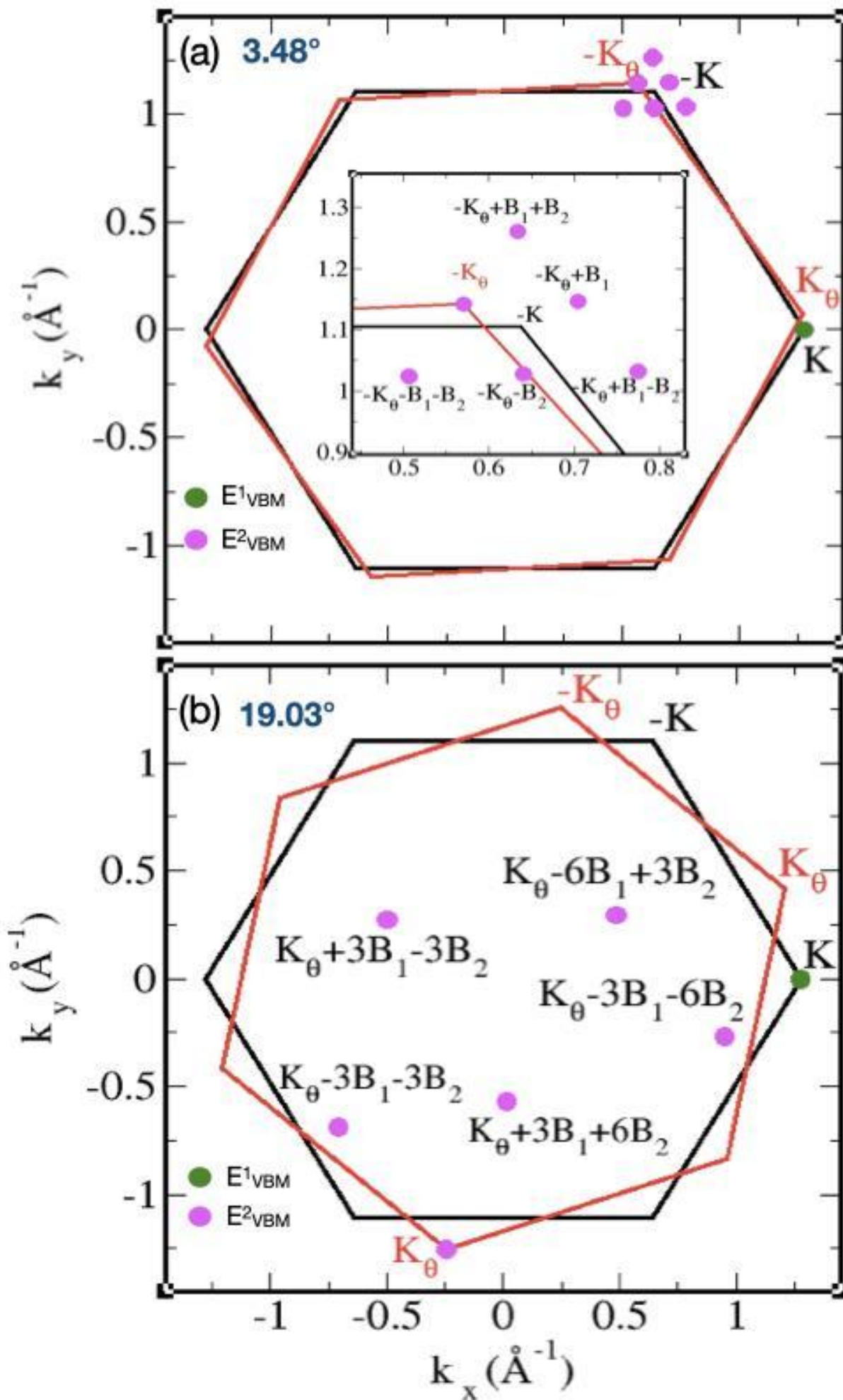
Vanishingly small bandwidth



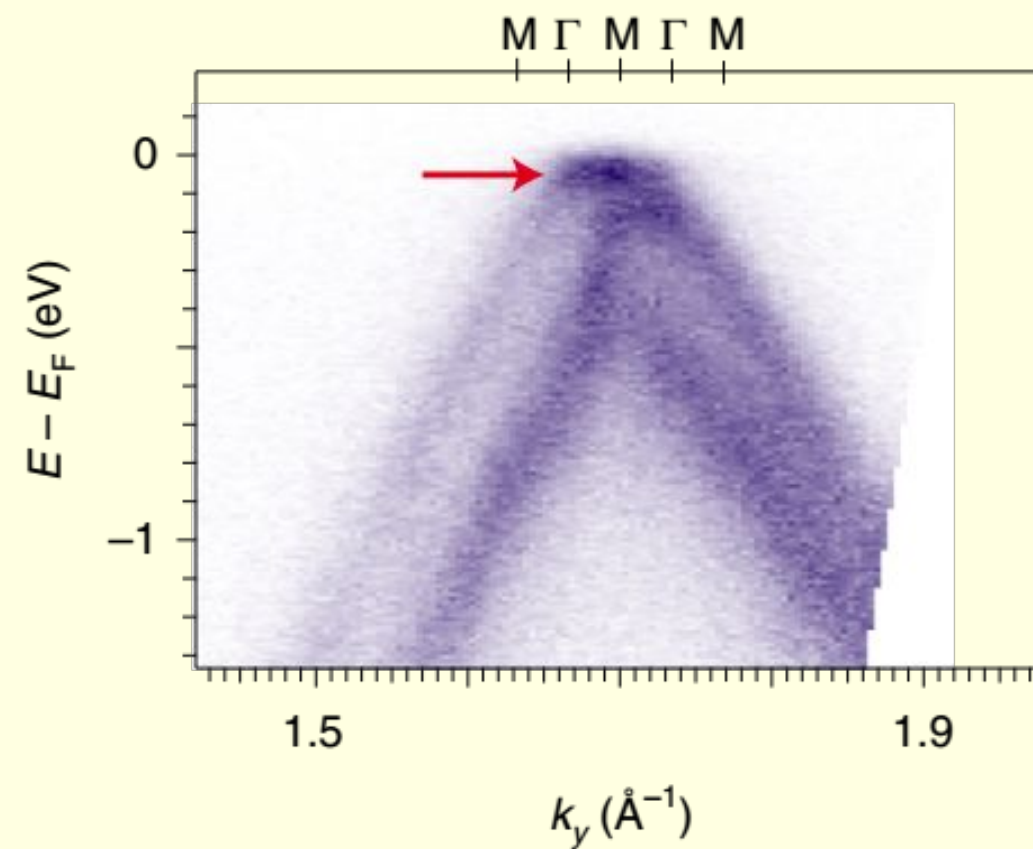
# Understanding the effect of vertical electric field on primitive cell bilayer $\text{WSe}_2$

**E.z** term added to the onsite energies.





$$K + G = k$$



Simone Lisi et al., Nat. Phys. 17, 189 (2021).

Recent results in twisted bilayer graphene support this viewpoint.